# simetrix

# SIMETRIX SIMULATOR REFERENCE MANUAL

VERSION 9.2

OCTOBER 2024

## SIMETRIX SIMULATOR REFERENCE MANAUL

COPYRIGHT © SIMETRIX TECHNOLOGIES LTD. 1992-2024

Trademarks: PSpice is a trademark of Cadence Design Systems Inc. Hspice is a trademark of Synopsys Inc.

SIMetrix Technologies Ltd., 78 Chapel Street, Thatcham, Berkshire RG18 4QN United Kingdom

Tel: +44 1635 866395 Fax: +44 1635 868322 Email: [support@simetrix.co.uk](mailto:support@simetrix.co.uk) Web:<http://www.simetrix.co.uk>



























[9 Convergence, Accuracy and Performance](#page-318-0) 303





# <span id="page-16-0"></span>**Chapter 1**

# **Introduction**

## <span id="page-16-1"></span>**1.1 Overview**

This manual provides full reference documentation for the SIMetrix simulator. Essentially the simulator receives a netlist as its input and creates a binary data file and list file as its output. The netlist defines the circuit topology and also specifies the analyses to be performed by the simulator. The netlist may directly include any device models required or these may be automatically imported from a device model library.

The simulator may be operated in GUI mode or non-GUI mode. GUI mode is the normal method of operation and requires the SIMetrix front end. In non-GUI mode the simulator runs stand alone in a non-interactive fashion and may be set to run at low priority in the background.

# <span id="page-16-2"></span>**1.2 The SIMetrix Simulator - What is it?**

The SIMetrix simulator core comprises a direct matrix analog simulator closely coupled with an event driven gate-level digital simulator. This combination is often described as *mixed-mode* or *mixed-signal* and has the ability to efficiently simulate both analog and digital circuits together.

The core algorithms employed by the SIMetrix analog simulator are based on the SPICE program developed by the CAD/IC group at the department of Electrical Engineering and Computer Sciences, University of California at Berkeley. The digital event driven simulator is derived from XSPICE developed by the Computer Science and Information Technology Laboratory, Georgia Tech. Research Institute, Georgia Institute of Technology.

# <span id="page-16-3"></span>**1.3 What is in This Manual**

This reference manual contains detailed descriptions of all simulator analysis modes and supported devices.

# <span id="page-17-0"></span>**Chapter 2**

# **Running the Simulator**

# <span id="page-17-1"></span>**2.1 Using the Simulator with the Schematic Editor**

Full documentation on using the SIMetrix schematic editor for simulation is described in the SIMetrix User's manual. However, just a few features of the schematic editor are of particular importance for running the simulator and for convenience their description is repeated here.

#### <span id="page-17-2"></span>**2.1.1 Adding Extra Netlist Lines**

The analysis mode selected using the schematic editor's **Simulator | Choose Analysis...** menu is stored in text form in the schematic's simulator command window. If you wish, it is possible to edit this directly. Sometimes this is quicker and easier than using the GUI especially for users who are familiar with the command syntax.

Note that the text entered in the simulator command window and the Choose Analysis dialog settings remain synchronised so you can freely switch between the two methods.

To open the simulator command window, select the schematic then press the F11 key. It has a toggle action, pressing it again will hide it. If you have already selected an analysis mode using the Choose Analysis dialog, you will see the simulator statements already present.

The window has a popup menu selected with the right key. The top item **Edit file at cursor** will open a text editor with the file name pointed to by the cursor or selected text item if there is one.

The simulator command window can be resized using the splitter bar between it and the schematic drawing area.

You can add anything you like to this window not just simulator commands. The contents are simply appended to the netlist before being presented to the simulator. So, you can place .PARAM statements, device models, inductor coupling specifications, .OPTIONS statements or simply comments. The Choose Analysis dialog will parse and possibly modify analysis statements and some .OPTIONS settings but will leave everything else intact.

#### <span id="page-17-3"></span>**2.1.2 Displaying Net and Pin Names**

It is sometimes necessary to know the name used for a particular net on the schematic to be referenced in a simulator statement (such as .NOISE) or for an arbitrary source input. There are two approaches:

• Find out the default name generated by the schematic editor's netlist generator. To do this, move the mouse cursor over the net of interest then observe the netname in the status bar in the form "NET=???".

• Force a net name of your choice. For this, use a terminal or small terminal symbol. These can be found under the **Place | Connectors** menu. After placing on the schematic, select it then press F7 to edit its name. This name will be used to name the net to which it is connected.

## <span id="page-18-0"></span>**2.1.3 Editing Device Parameters**

To use any of the additional parameters in a schematic, use the *Parameters* button in the dialog box opened by F7 or the equivalent menu. For example you see this box when editing a resistor:



Pressing the Parameters button will open another dialog from which you can edit parameter values:



You can also bring up this box directly using the right click menu Edit Additional Parameters....

## <span id="page-18-1"></span>**2.1.4 Editing Literal Values - Using shift-F7**

The above method is not infallible as it requires the schematic editor to know about the device being edited. In some circumstances, this will require special properties to be present on the symbol and these may have not been defined (for example something to tell the schematic what level a MOSFET is).

Another situation where the usual device editing methods may be unsuitable is when you need to define a parameter as an expression.

In these situations you can use shift-F7. This will edit the device's literal value including any model names exactly as it will be placed in the netlist. shift-F7 bypasses all smart algorithms and presents you with the raw values and you must also supply raw values. For example, here is what you might enter for a MOSFET referencing a model called N1

 $N1 L = \{LL-2*EDGE\} W = \{WW-2*EDGE\}$ 

Note the model name must be included.

## <span id="page-19-0"></span>**2.2 Running in non-GUI Mode**

#### <span id="page-19-1"></span>**2.2.1 Overview**

The simulator can be run in a non-interactive non-GUI mode independently of the front end. This is useful for running simulation 'batches' controlled by a proprietary script or language or DOS batch files.

Under Windows, the simulator will run as a 'console mode' application and no GUI elements will be created.

When run in this mode, the simulator will read in the specified netlist, run the simulation then close and return control to the calling program. It will generate a binary data file and a list file.

#### <span id="page-19-2"></span>**2.2.2 Important Licensing Information**

Non-GUI mode is only possible if you are using network licensing. This feature is not available if you are using a portable (i.e. dongled) license.

This mode of operation is 'counted' for licensing purposes. This means you can only run one non-GUI simulation process for each license issued even if all are run by a single user on a single machine. By contrast, regular simulation initiated manually through the GUI are not counted and any number of runs may be initiated on the same machine by the same user for this purpose.

These restrictions have been made to limit exploitation of multiple core machines for simulations run from non-SIMetrix environments.

#### <span id="page-19-3"></span>**2.2.3 Syntax**

The command syntax is as follows:

```
SIM [/config "config_location"] [/gui mode] [/check] [/an "analysis_line"]
  [/list list filename] [/options "options"] [/nolist] [/lowPriority]
  [/nodata] [/k] [/extraline extra_line] netlist_file [data_file]
```




#### <span id="page-21-0"></span>**2.2.4 Aborting**

Press cntrl-C - you will be asked to confirm. The simulation will be paused while waiting for your response and will continue if you enter 'No'. This is an effective means of pausing the run if you need CPU cycles for another task, or you wish to copy the data file. See [Reading Data.](#page-21-1)

#### <span id="page-21-1"></span>**2.2.5 Reading Data**

A data file will be created for the simulation results as normal (see [The Binary Data File\)](#page-27-0). You can read this file after the simulation is complete use the SIMetrix menu **File | Data | Load...** . You may also read this data file while the simulation is running but you must pause the simulation first using cntrl-C.

Important: if you read the data file before the simulation is complete or aborted, the file entries that provide the size of each vector will not have been filled. This means that the waveform viewer will have to scan the whole file in order to establish the size of the vectors. This could take a considerable time if the data file is large.

# <span id="page-21-2"></span>**2.3 Configuration Settings**

Configuration settings consist of a number of persistent global options as well as the locations for installed model libraries.

When the simulator is run in GUI mode, its configuration settings are controlled by the front end and stored wherever the front end's settings are stored. See the *User's Manual* for more details.

The settings when run in non-GUI mode are stored in a configuration file which in fact defaults to the same location as the default location for the front end's settings. You can change this location using the /config switch detailed in [Running in non-GUI Mode.](#page-19-0)

The format of the configuration file is:

```
[Options]
option_settings
[Models]
model_libraries
```
Where:

```
option settings These are of the form name=value and specify a number of global settings.
                       Boolean values are of the form name= without a value. If the entry is
                       present it is TRUE if absent it is FALSE. Available global settings are
                       detailed below.
```
model\_libraries A list of entries specifying search locations for model libraries. These are of the form *name*=*value* where *name* is a string and value is a search location. The string used for *name* is arbitrary but must be unique. Entries are sorted alphabetically according to the name and used to determine the search order. *value* is a path name and may contain wildcards (i.e. '\*' and '?').

#### <span id="page-22-0"></span>**2.3.1 Global Settings**



#### <span id="page-22-1"></span>**2.3.2 Data Buffering**

The simulator buffers data before writing it to disk. By doing so the binary data file can be organised more efficiently allowing data to be recovered from it quickly.

By default, the simulator won't allocate more than 10% of your system RAM to vector buffers. Clearly if you are running a large circuit and saving many vectors, the buffer sizes could reduce to levels that would make data retrieval very slow. In this case you may wish to consider increasing the memory that is allowed for these buffers. Two configuration settings control the vector buffering. These are:

- MaxVectorBufferSize. This sets the maximum size that will be used for any individual vector. The default is 32768 bytes. If you have a high performance SCSI disk system, you may benefit from increasing this value
- TotalVectorBufferSize. This sets the maximum amount of memory in bytes used for all buffers. It defaults to a value equal to 10% of your system RAM. This is usually sufficient for most

applications but if you are simulating a very large circuit and have sufficient RAM you may like to increase this value

The disk will not be written to until the buffers are full. With an all analog circuit all the buffers reach their full state at the same time so they all get written to disk at the same time. If you have 2G of RAM and are simulating a large circuit, approximately 200M of data will be written to the disk at regular intervals. This will result in a pause in the simulation coupled with a great deal of disk activity.

Note that both MaxVectorBufferSize and TotalVectorBufferSize may be set from the front end using the Set command. See *User's Manual/Sundry Topics/Using the Set and Unset Commands* for details.

## <span id="page-23-0"></span>**2.4 Netlist Format**

The SIMetrix netlist format follows the general format used for all SPICE and SPICE compatible simulators. However, with so many SPICE derivatives and with two significantly different versions of SPICE itself (SPICE 2 and SPICE 3) it is not possible to define a standard SPICE format. SIMetrix has been developed to be as compatible as possible with model libraries that can be obtained from external sources. For discrete devices, models are usually SPICE 2 compatible but some use extensions originally developed for PSpice®. IC designers usually receive model files from fabrication companies and these are available for a variety of simulators usually including Hspice®. SIMetrix is compatible with all of these but simultaneous compatibility with all formats is not technically possible due to a small number of syntax details - such as the character used for in line comments. To overcome these minor difficulties, a language declaration can be placed at the top of the netlist and any file included using [.INC](#page-234-0) or the Hspice® variant of [.LIB.](#page-238-0) This is described in the following sections.

#### <span id="page-23-1"></span>**2.4.1 File Format**

A complete netlist consists of:

- A title line
- Optional language declaration
- Device lines
- Statement lines
- Comment lines

The title line must be the first line of the file and may be empty. The remaining lines - with some exceptions - may be placed in any order

All other lines are defined by their first non-whitespace character as follows.

- Statement lines begin with a period: '.'
- Comment lines begin with an asterix: '\*'
- Device lines begin with a letter

A line is usually terminated with a new line character but may be continued using the '+' continuation character. So if the first non-whitespace character is a '+' the line will be considered to be an extension of the previous line. SPICE requires the '+' to be the first character, SIMetrix allows whitespace (space or tab) to precede it.

#### <span id="page-23-2"></span>**2.4.2 Encoding and International Characters**

Netlists may be encoded as ANSI or UTF-8. Currently wide-character encoding is not supported. If ANSI encoded, the character set employed will be the default for the locale.

Characters from all character sets may be used in netlists for naming items that do not specifically require western characters. For example, node names may use Japanese characters as long as they do not contain any spaces.

#### <span id="page-24-0"></span>**2.4.3 Language Declaration**

SIMetrix is able to read PSpice®, Hspice® and native SIMetrix netlists, but in some cases needs to be instructed what format netlist it is reading. Currently there are three areas where simultaneous compatibility has not been possible. These are:

- Inline comment character.
- Unlabelled device parameters
- The meaning of LOG() and PWR() functions

SIMetrix can be instructed to use any of the three languages by using the language declaration. This is one of:

#### \*#SIMETRIX \*#HSPICE \*#PSPICE

The language declaration must be placed at the top of the file immediately below the title line. It can also be placed in files referenced using .INC or the HSPICE® version of .LIB in which case it will apply only to that file and any others that it calls. A language declaration placed anywhere else in a file will be ignored.

For details see [Language Differences.](#page-50-0)

The \*#SIMETRIX language declaration can also be supplied with a parameter to specify the separator letter used for devices. See [Device Lines](#page-24-2) section for details.

#### <span id="page-24-1"></span>**2.4.4 Comments**

Any line other than a language declaration beginning with a '\*' is defined as a comment and will be ignored. Also anything between a semi-colon ';' ('\$' in HSPICE mode) and the end of the line will be treated as comment and will also be ignored. Some SPICE simulators require the '\*' character to be the first character of the line. SIMetrix allows it to be preceded by white space (spaces and tabs).

#### <span id="page-24-2"></span>**2.4.5 Device Lines**

Device lines usually follow the following basic form but each type of device tends to have its own nuances:

Name nodelist value [parameters]

*value* may be an actual number e.g. in the case of passive components such as resistors, or it may be a model name in the case of semiconductor devices such as bipolar transistors. Models are defined using a .MODEL statement line.

*nodelist* is a list of netnames. The number and order of these is device dependent. The netname itself may consist of any collection of non-control ASCII characters except whitespace and '.'. All other ASCII characters are accepted although it is suggested that the following characters are avoided if possible:

 $\left[\begin{array}{cc} 0 & \frac{1}{2} \\ 0 & \frac{1}{2} \end{array}\right]$  ,  $\left[\begin{array}{cc} 0 & \frac{1}{2} \\ 0 & \frac{1}{2} \end{array}\right]$  ,  $\left[\begin{array}{cc} 0 & \frac{1}{2} \\ 0 & \frac{1}{2} \end{array}\right]$  ,  $\left[\begin{array}{cc} 0 & \frac{1}{2} \\ 0 & \frac{1}{2} \end{array}\right]$ 

If any of these characters are used in a netname, a special syntax will be needed to plot any signal voltage on that net. This is explained in [Output Data Names.](#page-27-1) In addition the characters '[', ']', '%', '!' and ' ' have a special meaning when used with XSPICE devices and therefore should be avoided at all times.

The *name* is the circuit reference of the device. The first letter of this name determines the type of device as shown in the table below.





To remove the naming restriction that this system imposes, SIMetrix supports an extension to the above to allow the user to use any name for all devices. If the device letter is followed by a dollar '\$' symbol (by default but can be changed - see below), the remainder of the name following the '\$' will be used as the device name. E.g.:

#### Q\$TR23

will define a bipolar transistor with the name TR23. All output generated by the simulator will refer to TR23 not Q\$TR23.

The above mechanism can be disabled and also the character can be changed by adding a parameter to the language declaration (see [Language Declaration\)](#page-24-0). To disable, add this to the top of the netlist:

\*#SIMETRIX sep=none

To change the character use:

\*#SIMETRIX sep=character

*character* must be a single letter, anything else will be ignored. Although any character will be accepted it should clearly not be alpha-numeric.

The above mechanism will also be disabled if HSPICE or PSPICE languages are specified.

#### <span id="page-26-0"></span>**2.4.6 Simulator Statements**

Instructions to the simulator other than device definitions and comments are referred to as *statements* and always begin with a period '.'.

Full documentation for SIMetrix statements see [Command Reference.](#page-214-0)

# <span id="page-26-1"></span>**2.5 Simulator Output**

#### <span id="page-26-2"></span>**2.5.1 The List File**

SIMetrix produces a list file by default. This receives all text output except for the Monte Carlo log. This includes operating point results, model parameters, noise analysis results, sensitivity analysis results, pole-zero analysis results and tabulated vectors specified by .PRINT.

The list file is generated in the same directory as the netlist. It has the same name as the netlist but with the extension .OUT.

There are a number of options that control the list file output.



#### <span id="page-27-0"></span>**2.5.2 The Binary Data File**

The simulation data is stored in a binary data file. The format is proprietary to SIMetrix and is not compatible with SPICE 'raw' files.

The name and location of the binary file depends on configuration settings and in what mode the simulator is run. Usually, the file is located in the directory specified by the TEMPDATADIR configuration setting (see [Configuration Settings\)](#page-21-2) and is named according to the analysis type and appended with the extension .sxdat. E.g.tran1.sxdat, ac2.sxdat, dc3.sxdat etc. The name and location can be overridden at the program command line if operated in non-GUI mode or at the front end Run command line if run in GUI mode.

Only the SIMetrix front end can read the simulator's binary data file. When run in GUI mode, the file is automatically loaded and in fact it is not usually necessary to know anything about it except perhaps when it grows very large and fills up your disk. If the simulator is run in non-GUI mode, it becomes necessary to explicitly load the data into the front end when the run is complete. This can be done with the command shell menu **File | Data | Load...**. After the data is loaded, the results can be plotted in the usual manner. See *User's Manual/Graphs,Probes and Data Analysis/Saving Data/Restoring Simulation Data* for further details.

#### <span id="page-27-1"></span>**2.5.3 Output Data Names**

For transient, DC and AC analyses, SIMetrix calculates and stores the circuit's node voltages and device pin currents and these are all given unique names. If using probing techniques with the front end's schematic editor you don't usually need to know anything about the names used. However there are situations where it is necessary or helpful to know how these names are derived. An example is when compiling an expression relating voltages and currents to be used in a .PRINT statement. Another is when plotting results created by simulating a netlist that was not generated using the schematic editor. The names used are documented in the following notes.

#### **Top Level Node Voltages**

The vector names used for node voltages at the top level (i.e. not in a subcircuit) are simply the name of the node used in the netlist. If using the schematic editor the name of any node can be fixed using a Terminal symbol. See menu **Place | Connectors | Terminal**.

#### **Subcircuit Node Voltages**

For nodes within a subcircuit, the name is prefixed with the subcircuit reference and a '.'. For example:

```
X1 N1 N2 N3 SubName
X2 N4 N5 N6 SubName
.SUBCKT 1 2 3 SubName
X3 N1 2 N3 SubName2
R1 VIN 0 1k
...
.ENDS
.SUBCKT 1 2 3 SubName2
V1 VCC 0 5
...
.ENDS
```
The internal node VIN in definition SubName referenced by X1 would be called X1.VIN. The same node referenced by X2 would be called X2.VIN. The node VCC defined in subcircuit SubName2 would be named X1.X3.VCC and X2.X3.VCC for X1 and X2 respectively.

#### **Nodes with Non-standard Names**

A non-standard node name is one that begins with a digit or which contains one or more of the characters:

 $\langle \begin{array}{c} \n\mathbf{u} \end{array} \rangle$   $\begin{array}{c} \n\mathbf{v} \end{array}$  + - \* / ^ < > [ ] ' @ { }

These are legal but introduce problems when accessing the voltage data that they carry. The above characters can be used in arithmetic expressions so cause a conflict if used as a node name. In order to access the voltage data on a node so named, use the Vec() function:

Vec('node\_name')

Example with .PRINT and node called V+

**.PRINT** TRAN {Vec('V+')}

A similar syntax is required when using the front end plotting commands.

#### **Device Pin Currents**

Device pin currents are named in the following form:

device\_name#pin\_name

For primitive devices (i.e. not sub-circuits) pin\_name must comply with the table in [Device Lines.](#page-24-2) For example the current into the collector of Q23 would be Q23#c.

The pin names for sub-circuits depend on whether the *pinnames:* specifier (see [Subcircuit Instance\)](#page-129-3) is included in the netlist entry for the device. If it is the pin current name will be the name listed after *pinnames:*. If it isn't then they are numbered in sequence starting from 1. The order is the same as the order they appear in the netlist device line. For example, if the subcircuit line is:

X\$U10 N1 N2 N3 N4 N5 LM324 pinnames: VINP VINN VP VN VOUT

The current into the last pin (connected to N5) would be U10#VOUT

(Note that 'X\$' is stripped off as explained above in [Device Lines\)](#page-24-2).

If the netlist line is:

X\$U10 N1 N2 N3 N4 N5 LM324

The same current would be U10#5

#### **Internal Device Values**

Some devices have internal nodes or sources and the voltages or currents associated with these may be output by the simulator. These are named in a similar manner to pin currents i.e.

device\_name#internal\_name

The *internal\_name* depends on the device. For example, bipolar transistors create an internal node for each terminal that specifies a corresponding resistance parameter. So if the RE parameter is specified an internal node will be created called emitter.

Note that internal device values are only output if explicitly enabled using the ".KEEP /INTERNAL" statement. See [.KEEP.](#page-234-1)

# <span id="page-29-0"></span>**2.6 Data Handling - Controlling Data Saved**

As explained in [The Binary Data File,](#page-27-0) all data is saved to a binary disk file. By default, all signals visible in a schematic are saved. That is all signals at the top level of a hierarchy and in all child schematics are saved. Signals inside subcircuits that were not generated by a hierarchical schematic are *not* saved.

SIMetrix has comprehensive features for changing exactly what data is saved. Some simulations can generate huge amounts of data and with multi-core multi-step simulations, the rate at which the data is created can exceed the performance of the disk system. It is therefore desirable in some cases to reduce the amount of data saved.

For simulations run from the user interface, some of the data handling features are available through the GUI. See *User's Manual/Analysis Modes/Data Handling and Keeps*.

More comprehensive features are available using [.KEEP](#page-234-1) and .OPTIONS. See .KEEP for full details.

# <span id="page-30-0"></span>**Chapter 3**

# **Simulator Devices**

## <span id="page-30-1"></span>**3.1 Overview**

This chapter is an introduction to the [Analog Deivce reference](#page-55-0) and the [Digital/Mixed Signal Device](#page-159-0) [Reference.](#page-159-0)

The device reference chapters describe all simulator devices at the netlist level. The netlist consists of a list of component definitions, along with simulator commands, which the simulator can understand. Simple components, such as resistors just need a value to define them. Other more complicated devices such as transistors need a number of parameters to describe their characteristics.

The device references includes details of all device and model parameters. Using the schematic editor and model library you may not often need to read this section. Some of the devices, however, have advanced options not directly supported by the user interface. For example, many devices allow a local temperature to be specified. This requires the component value to be appended with TEMP=.... This device parameter and others are documented here.

Note that many parts either supplied with SIMetrix or available from component manufacturers are implemented as subcircuits. These are circuit designs to simulate the behaviour of high level devices such as opamps. SIMetrix (and all other SPICE simulators) do not have an opamp device built in but use these *macro models* instead. Full documentation for these devices is beyond the scope of this manual but can sometimes be obtained from their suppliers.

# <span id="page-30-2"></span>**3.2 Using XSPICE Devices**

Some devices are implemented as part of the XSPICE 'code modelling' framework. This framework introduces some new features at the netlist level not supported by standard SPICE devices. These new features are described in this section.

All but one of these devices that use this framework are digital or mixed signal devices and the reference for these can be found at [Digital/Mixed Signal Device Reference.](#page-159-0)

The exception is the [S-domain Transfer Function Block](#page-94-0) which is a pure analog part.

#### <span id="page-30-3"></span>**3.2.1 Vector Connections**

Some models feature an arbitrary number of inputs or/and outputs. For example, an AND gate can have any number of inputs. It would be inflexible to have a separate model for every configuration of AND gate so a method of grouping connections together has been devised. These are known as *vector connections*. Vector connections are enclosed in square brackets. E.g. the netlist entry for an AND gate is:

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

The pins in  $\alpha$  in  $\alpha$  is in  $\alpha$  in form a single vector connection. Any number of pins may be placed inside the square brackets, in fact the same model may be used for devices with different numbers of inputs.

Some devices have a minimum and/or maximum number of pins that may be used in a vector connection. This is known as *vector bounds* and if they apply will be listed in the vector bounds column of the Connection Details table provided with every device definition.

#### <span id="page-31-0"></span>**3.2.2 Connection Types**

In the device references that follow, each has a table titled Connection Details. Each table has a "Type" column and some have an "Allowed types" column. The type referred to here is the type of electrical connection e.g. voltage, current, differential or single-ended. Some devices allow some or all of their connections to be specified with a range of types. For example, the [analog-digital converter](#page-197-3) has a single ended voltage input by default. However, using a simple modification to the netlist entry, an ADC can be specified with a differential voltage input or even a differential current. Changing the type of connection involves no changes to the .MODEL statement, only to the netlist entry.

The following table lists all the available types. The modifier is the text used to alter a connection type at the netlist level. This is explained below



With the models supplied with SIMetrix, only the first four in the above table are ever offered as options. The others are used but are always compulsory, and an understanding of their meaning is not necessary to make full use the system.

As well as type, all connections also have a *flow* referring to the direction of the signal flow. This can be *in, out or inout*. Voltage, current and digital connections may be in or out while the conductance and resistance connections may only be *inout*. Voltage inputs are always open circuit, current inputs are always short circuit, voltage outputs always have zero output impedance and current outputs always have infinite output impedance.

The conductance connections are a combined voltage input and current output connected in parallel. If the output is made to be proportional to the input, the connection would be a conductor with a constant of proportionality equal to its conductance, hence the name.

Similarly, the resistance connections are a combined current input and voltage output connected in series. If the output is made to be proportional to the input, the connection would be a resistor with a constant of proportionality equal to its resistance.

#### **Changing Connection Type**

If a model allows one or more of its connections to be given a different type, this can be done by preceding the connection entry with the appropriate modifier listed in the table above. For example if you wish to specify a 4 bit ADC with a differential voltage input, the netlist entry would be something like:

```
A1 %vd ANALOG_INP ANALOG_INN CLOCK_IN [ DATA_OUT_0 DATA_OUT_1 DATA_OUT_2
DATA_OUT_3 ] DATA_VALID ADC_4
```
## <span id="page-32-0"></span>**3.3 Using Expressions**

#### <span id="page-32-1"></span>**3.3.1 Overview**

Expressions consist of arithmetic operators, functions, variables and constants and may be employed in the following locations:

- As device parameters
- As model parameters
- To define a variable (see [.PARAM\)](#page-272-1) which can itself be used in an expression.
- As the governing expression used for [arbitrary sources.](#page-57-1)

They have a wide range of uses. For example:

- To define a number of device or model parameters that depend on some common characteristic. This could be a circuit specification such as the cut-off frequency of a filter or maybe a physical characteristic to define a device model.
- To define tolerances used in Monte Carlo analyses.
- Used with an arbitrary source, to define a non-linear device.

#### <span id="page-32-2"></span>**3.3.2 Using Expressions for Device Parameters**

Device or instance parameters are placed on the device line. For example the length parameter of a MOSFET, L, is a device parameter. A MOSFET line with constant parameters might be:

```
M1 1 2 3 4 MOS1 L=1u W=2u
```
L and W could be replaced by expressions. For example:

```
M1 1 2 3 4 MOS1 L={LL-2*EDGE} W={WW-2*EDGE}
```
Device parameter expressions must usually be enclosed with either single quotation marks ( ' ) double quotation marks (") or braces (" and "). The expression need not be so enclosed if it consists of a single variable. For example:

```
.PARAM LL=2u WW=1u
M1 1 2 3 4 MOS1 L=LL W=WW
```
#### <span id="page-32-3"></span>**3.3.3 Using Expressions for Model Parameters**

The rules for using expressions for device parameters also apply to model parameters. E.g.

```
.MODEL N1 NPN IS=is BF={beta*1.3}
```
#### <span id="page-33-0"></span>**3.3.4 Expression Syntax**

Expressions generally comprise the following elements:

- Circuit variables
- Parameters
- Constants.
- Operators
- Functions
- Look up tables

These are described in the following sections.

#### **Circuit Variables**

Circuit variables may only be used in expressions used to define [arbitrary sources](#page-57-1) and to define variables that themselves are accessed only in arbitrary source expressions.

Circuit variables allow an expression to reference voltages and currents in any part of the circuit being simulated.

Voltages are of the form:

V(node\_name1)

#### OR

V(node\_name1, node\_name2)

Where *node* name1 and node name2 are the name of the node carrying the voltage of interest. The second form above returns the difference between the voltages on node name1 and node name2. If using the schematic editor nodenames are normally allocated by the netlist generator. For information on how to display and edit the schematic's node names, refer to [Displaying Net and Pin Names.](#page-17-3)

Currents are of the form:

I(source\_name)

Where *source* name is the name of a device carrying the current of interest. The controlling device can be any native (i.e. non-subcircuit) device in the circuit. The current used will be the current flowing into its first terminal. The first terminal is the one that is first in the device's netlist entry. Note that if the device is not a voltage source or implemented as a voltage source, the current is sensed by placing a zero-volt voltage source in series with the sensing device. This is done automatically and no user action is required.

It is legal for an expression used in an arbitrary source to reference itself e.g.:

B1 n1 n2 V=100\*I(B1)

Implements a 100 ohm resistor.

A second argument can be provided:

I(source\_name, terminal)

where *(*terminal) is the name of the terminal of the device. For example:

 $I(Q3, c)$ 

will return the collector current of Q3. There is currently no documentation that lists terminal names for each simulator device type but the names can be obtained from the GetDevicePins script function. Refer to *Script Reference Manual/Function Reference/GetDevicePins*. Most semiconductor device pins are named with a single letter representing their familiar name: 'c', 'b', 'e', 'd', 'g', 's', 'b' and most two-terminal parts are 'p' and 'n'.

The function names ID, IG, IS, IC, IB and IE may also be used to access drain, gate, source, collector, base and emitter currents respectively. Note, however, that if a user function (defined using [.FUNC\)](#page-226-1) of the same name is defined, the user function will take precedence.

#### **Parameters**

These are defined using the [.PARAM](#page-272-1) statement. For example:

```
.PARAM res=100
B1 n1 n2 V=res*I(B1)
```
Also implements a 100 ohm resistor.

Circuit variables may be used .PARAM statements, for example:

**.PARAM** VMult = {  $V(a) * V(b)$  } B1 1 2 V = Vmult + V(c)

Parameters that use circuit variables may only be used in places where circuit variables themselves are allowed. So, they can be used in arbitrary sources and they may be used to define the resistance of an Hspice style resistor which allows voltage and current dependence. (See [Resistor - Hspice Compatible\)](#page-124-1). They may also of course be used to define further parameters as long as they too comply with the above condition.

#### **Built-in Parameters**

A number of parameter names are assigned by the simulator. These are:





#### **Constants**

Apart from simple numeric values, arbitrary expressions may also contain the following built-in constants:



If the simulator is run from the front end in GUI mode, it is also possible to access variables defined on the Command Shell command line or in a script. The variable must be global and enclosed in braces. E.g.

B1 n1 n2  $V = V(n3, n3)$  \* { global:amp\_gain }

amp\_gain could be defined in a script using the LET command. E.g. "Let global:amp\_gain = 100"

## **Operators**

These are listed below and are listed in order of precedence. Precedence controls the order of evaluation. So  $3*4 + 5*6 = (3*4) + (5*6) = 42$  and  $3+4*5+6 = 3 + (4*5) + 6 = 29$  as '\*' has higher precedence than '+'.




# **Comparison, Equality and Logical Operators**

These are Boolean in nature either accepting or returning Boolean values or both. A Boolean value is either TRUE or FALSE. FALSE is defined as equal to zero and TRUE is defined as not equal to zero. So, the comparison and equality operators return 1.0 if the result of the operation is true otherwise they return 0.0.

The arguments to equality operators should always be expressions that can be guaranteed to have an exact value e.g. a Boolean expression or the return value from functions such as SGN. The == operator, for example, will return TRUE only if both arguments are *exactly* equal. So the following should never be used:

 $v(n1) = 5.0$ 

v(n1) may not ever be exactly 5.0. It may be 4.9999999999 or 5.00000000001 but only by chance will it be 5.0.

These operators are intended to be used with the IF() function described in [Ternary Conditional](#page-36-0) [Expression.](#page-36-0)

# **Digital Operators**

These are now considered obsolete and should not be used in new model designs. They may be removed from future versions of SIMetrix.

These are the operators '&', '|' and ' $\sim$ '. These were introduced in old SIMetrix version as a simple means of implementing digital gates in the analog domain. Their function has largely been superseded by gates in the event driven simulator.

# <span id="page-36-0"></span>**Ternary Conditional Expression**

This is of the form:

test\_expression ? true\_expression : false\_expression

The value returned will be *true\_expression* if *test\_expression* resolves to a non-zero value, otherwise the return value will be *false expression*. This is functionally the same as the IF() function described in the functions table below.

# **Functions**





# <span id="page-38-0"></span>**The log() Function**

In versions 9.1 and earlier the log() function means log to the base 10 in native SIMetrix expressions. From 9.2 this changed to log to the base e in order to be compatible with other simulators and publicly available models.

If compatibility with older SIMetrix versions is required, an option setting can be used to revert to log to base 10. Add this line to the netlist:

**.OPTIONS** logFunctionBaseE=0

Note that the above affects the use of log() in native arbitrary source expressions and .PARAM statements. A native arbitrary source is one defined using the 'B' device as follows:

Bxxx  $n1 n2 v|i|q|$ flux = expression

See [Arbitrary Source](#page-57-0) for further details.

Arbitrary sources implemented using PSpice ABM syntax are also recognised by SIMetrix and, as PSpice interprets log() as log to base e, SIMetrix will do so too when used in a PSpice ABM expression regardless of the logFunctionBaseE option setting. For example:

E1 n1 n2 VALUE =  $\{log(1+exp(V(n3, n4)))\}$ 

In the above, log is interpreted as log to base e even if the  $logFunctionBaseE}$  option setting above is set to 0.

To avoid any confusion, we recommend avoid using log(). For log to base 10 use log10() and for log to base e use ln().

# **Monte Carlo Distribution Functions**

To specify Monte Carlo tolerance for a model parameter, use an expression containing one of the following functions:





A full discussion on the use of Monte Carlo distribution functions is given in [Specifying Tolerances.](#page-299-0)

# <span id="page-39-0"></span>**IF() Function**

IF(condition, true-value, false-value[, max-slew])

#### The result is:

if *condition* is non-zero, result is *true-value*, else result is *false-value*.

If *max-slew* is present and greater than zero, the result will be slew-rate limited in both positive and negative directions to the value of max-slew.

In some situations, for example if *true-value* and *false-value* are constants, the result of this function will be discontinuous when *condition* changes state. This can lead to non-convergence as there is no lower bound on the time-step. In these cases a *max-slew* parameter can be included. This will limit the slew rate so providing a controlled transition from the *true-value* to the *false-value* and vice-versa.

If the [option setting](#page-250-0) *DISCONTINUOUSIFSLEWRATE* is non-zero, SIMetrix will automatically apply a *max-slew* parameter to all occurrences of the IF() function if both true-value and false-value are constants. This provides a convenient way of resolving convergence issues with third-party models that make extensive use of discontinuous if expressions. Note that the *DISCONTINUOUSIFSLEWRATE* option is also applied to conditional expressions using the C-style *condition* ? *true-value* : *false-value* syntax.

### <span id="page-39-1"></span>**LIMITS() Function**

LIMITS(x, low, high, sharp)

The LIMITS() function is similar to LIMIT but provides a smooth response at the corners which leads to better convergence behaviour. The behaviour is shown below



The LIMITS function follows this equation:

LIMITS(x, low, high, sharp) =  $0.5*(\ln(\cosh(v1)) - \ln(\cosh(v2)))/v3 + (\text{low+high})$ 

Where

$$
v1 = \frac{\text{sharp}}{\text{high-low}}(x - \text{low})
$$

- $v2 = \frac{\text{sharp}}{\text{high-low}}$  \*(x-high)
- $v3 = \frac{\text{sharp}}{\text{high-low}}$

# <span id="page-40-0"></span>**Look-up Tables**

Expressions may contain any number of look-up tables. This allows a transfer function of a device to be specified according to - say - measured values without having to obtain a mathematical equation. Look-up tables are specified in terms of x, y value pairs which describe a piece-wise linear transfer function. There are three ways to create a lookup table:



Method 1 is more efficient at handling large tables (hundreds of values). However, method 2 is generally more flexible and is the recommended choice for most applications. Method 2 is also compatible with other simulators whereas method 1 is proprietary to SIMetrix.

For an example see [Table Lookup Example](#page-42-0)

# <span id="page-41-0"></span>**Relational Operators and Functions**

The operators ' $\langle \cdot, \cdot \rangle \langle = \cdot, \cdot \rangle$ ' and ' $\rangle = \rangle$ ' are known as relational operators. The result of executing these is a value of either 1.0 or 0.0 depending whether the relation is true. These are often used with the  $if()$ function.

The functions,  $lt(x, y)$ ,  $le(x, y)$ ,  $gt(x, y)$  and  $ge(x, y)$  perform the same task but with an important difference. These functions control the time step so that a time point is performed both before and after the threshold is crossed with a timestep between the two points that is no larger than the value specified by

their third argument. If no third argument is provided, a default value is used defined by option setting RELOPTHRESHTIMETOL which itself defaults to 10ns.

The time step control feature of these functions is useful for use in applications such as comparators. For example, suppose a comparator is implemented using an expression such as  $V(inp) > V(inn)$ . This might be used to trigger activity on the rising edge of an input signal. If the circuit is in an idle state the time steps could be very long, perhaps in the millisecond region. For this example, let's suppose that the timestep is currently 1ms and the  $V(inp) > V(inn)$  changes state. This might not be registered until up to 1ms after the threshold is actually crossed. Further the actual delay is random and could therefore introduce quite serious errors maybe even preventing an edge triggered event occurring. This problem is often solved by limiting the maximum time step but in some applications this can slow the simulation time unacceptably.

A better solution is to control the time step so that the threshold is detected accurately. This can be done by instead calling the function  $lt(V(inp), V(inn), 1n)$ . Here the time step will be controlled to an accuracy of 1ns which will solve the problem of slow edges.

The regular operators ' $\langle \cdot, \cdot \rangle \langle \cdot \rangle$ ' and ' $\rangle =$ ' can also be configured to behave in the same way using another boolean option setting: RELOPTHRESHDETECT. The operators do not have a third argument so these always use the time tolerance defined by RELOPTHRESHTIMETOL. See [.OPTIONS](#page-250-1)

# **3.3.5 Examples**

### <span id="page-42-0"></span>**Table Lookup Example**

The following arbitrary source definition implements a soft limiting function

#### Using method 1:

```
B1 n2 n3 V=table[-10, -5, -5, -4, -4, -3.5, -3, -3, 3, 3, 4,
+ 3.5, 5, 4, 10, 5] (v(N1))
```
#### Using method 2:

```
B1 n2 n3 V=TABLE(v(N1), -10, -5, -5, -4, -4, -3.5, -3, -3, 3, 3, 4,
+ 3.5, 5, 4, 10, 5)
```
#### Using method 3:

B1 n2 n3 V=TABLEX(v(N1), -10, -5, -5, -4, -4, -3.5, -3, -3, 3, 3, 4, + 3.5, 5, 4, 10, 5)

The resulting transfer functions are illustrated in the following picture:



# **Parameter Example**

It is possible to assign expressions to component values which are evaluated when the circuit is simulated. This has a number of uses. For example you might have a filter design for which several component values affect the roll off frequency. Rather than recalculate and change each component every time you wish to change the roll of frequency it is possible to enter the formula for the component's value in terms of this frequency.



The above circuit is that of a two pole low-pass filter. C1 is fixed and R1=R2. The design equations are:

```
R1=R2=2/(2*pi*f0*C1*alpha)
C2=C1*alpha*alpha/4
```
where f0 is the cut off frequency and alpha is the damping factor.

The complete netlist for the above circuit is:

```
V1 V1_P 0 AC 1 0
C2 0 R1_P {C1*alpha*alpha/4}
C1 VOUT R1_N {C1}
E1 VOUT 0 R1_P 0 1
R1 R1_P R1_N {2/(2*pi*f0*C1*alpha)}
R2 R1_N V1_P {2/(2*pi*f0*C1*alpha)}
```
Before running the above circuit you must assign values to the variables. This can be done by one of three methods:

- With the .PARAM statement placed in the netlist.
- With Let command from the command line or from a script. (If using a script you must prefix the parameter names with global:)
- By sweeping the value with using parameter mode of a swept analysis (see [General Sweep](#page-215-0) [Specification\)](#page-215-0) or multi-step analysis (see [Multi Step Analyses\)](#page-217-0).

Expressions for device values must be entered enclosed in curly braces ('{' and '}').

Suppose we wish a 1kHz roll off for the above filter.

Using the [.PARAM](#page-272-0) statement, add these lines to the netlist

```
.PARAM f0 1k
.PARAM alpha 1
.PARAM C1 10n
```
Using the Let command, you would type:

Let f0=1k Let alpha=1 Let C1=10n

If you then wanted to alter the damping factor to 0.8 you only need to type in its new value:

```
Let alpha=0.8
```
then re-run the simulator.

To execute the Let commands from within a script, prefix the parameter names with global:. E.g. "Let global:f0=1k"

In many cases the .PARAM approach is more convenient as the values can be stored with the schematic.

# **3.3.6 Optimisation**

#### **Overview**

An optimisation algorithm may be enabled for expressions used to define arbitrary sources and any expression containing a swept parameter. This can improve performance if a large number of such expressions are present in a design.

The optimiser dramatically improves the simulation performance of the power device models developed by Infineon. See [Optimiser Performance.](#page-45-0)

Note that the optimiser referred to here is an algorithm that manipulates expressions found in arbitrary sources to make them evaluate more efficiently. This is not to be confused with the circuit optimiser described [here](#page-309-0)

## **Why is it Needed?**

The simulator's core algorithms use the Newton-Raphson iteration method to solve non-linear equations. This method requires the differential of each equation to be calculated and for arbitrary sources, this differentiation is performed symbolically. So as well as calculating the user supplied expression, the simulator must also evaluate the expression's differential with respect to each dependent variable. These differential expressions nearly always have some sub-expressions in common with sub-expressions in the main equation and other differentials. Calculation speed can be improved by arranging to evaluate these sub-expressions only once. This is the main task performed by the optimiser. However, it also eliminates factors found on both the numerator and denominator of an expression as well as collecting constants together wherever possible.

# **Using the Optimiser**

The optimiser is automatically enabled and no action is required to make use of it. If desired, it can be disabled using:

**.OPTIONS** optimise=0

# <span id="page-45-0"></span>**Optimiser Performance**

The optimisation algorithm was added to SIMetrix primarily initially to improve the performance of some publicly available power device models from Infineon. These models make extensive use of arbitrary sources and many expressions are defined using .FUNC. Since its original development, many more device manufacturers have developed models using the same method and these also benefit from the performance enhancement.

The performance improvement gained for these model is in some cases dramatic. For example a simple switching PSU circuit using a SGP02N60 IGBT ran around 5 times faster with the optimiser enabled and there are other devices that show an even bigger improvement.

### **Accuracy**

The optimiser simply changes the efficiency of evaluation and doesn't change the calculation being performed in any way. However, performing a calculation in a different order can alter the least significant digits in the final result. In some simulations, these tiny changes can result in much larger changes in circuit solution. So, you may find that switching the optimiser on and off may change the results slightly.

# **3.4 Subcircuits**

### **3.4.1 Overview**

Subcircuits are a method of defining a circuit block which can be referenced any number of times by a single netlist line or schematic device. Subcircuits are the method used to define many device models such as op-amps.

# **3.4.2 Subcircuit Definition**

Subcircuits begin with the .SUBCKT statement and end with .ENDS. A subcircuit definition is of the form:

```
.SUBCKT subcircuit_name nodelist [[params:] default_parameter_list]
definition_lines
.ENDS
```


# **Example**

This is an example of an opamp subcircuit called SXOA1000. VINP, VINN VOUT VCC and VEE are its external connections. The three .model lines define devices that are local, that is, they are only accessible within the subcircuit definition.

```
.subckt SXOA1000 VINP VINN VOUT VCC VEE
I2 D2_N VEE 100u
I1 Q3_E VEE 100u
C1 VOUT R1_P 10p
D1 Q7_C D1_N D1
D2 D1_N D2_N D1
D3 VEE Q3_E D1
Q2 VEE D2_N VOUT 0 P1
Q3 Q3_C R3_P Q3_E 0 N1
Q1 VCC Q7_C VOUT 0 N1
Q6 Q3_C Q3_C VCC 0 P1
Q7 Q7_C Q5_C VCC 0 P1
R1 R1_P Q5_C 100
Q4 Q5_C R2_N Q3_E 0 N1
R2 VINP R2_N 1K
```

```
Q5 Q5_C Q3_C VCC 0 P1
R3 R3_P VINN 1K
.model N1 NPN VA=100 TF=1e-9
.model P1 PNP VA=100 TF=1e-9
.model D1 D
.ends
```
# **Where to Place Subcircuit Definition**

Subcircuit definitions may be placed in a number of locations.

- Directly in the netlist. This is the best place if the subcircuit is specific to a particular design. If you are entering the circuit using the schematic editor, see [Simulator Reference Manual/Running the](#page-17-0) [Simulator/Using the Simulator with the SIMetrix Schematic Editor/Adding Extra Netlist Lines](#page-17-0) to find out how to add additional lines to the netlist.
- Put in a separate file and pull in to the schematic with [.INC](#page-234-0) statement placed in the netlist.
- Put in a library file and reference in schematic with SIMetrix form of [.LIB](#page-238-0) statement placed in the netlist. Similar to 2. but more efficient if library has many models not used in the schematic. Only the devices required will be read in.
- Put in a library file and install as a model library. See *User's Manual/Device Library and Parts Management/Installing Models* for full details.

# **3.4.3 Subcircuit Instance**

Once a subcircuit has been defined, any number of instances of it may be created. These are of the form:

```
Xxxxx nodelist sub_circuitname [ [params:] parameters]
```


# **3.4.4 Passing Parameters to Subcircuits**

You can pass parameters to a subcircuit. Consider the filter example provided in [Using Expressions.](#page-32-0) Supposing we wanted to define several filters with different characteristics. We could use a subcircuit to define the filter but the values of the components in the filter need to be different for each instance. This can be achieved by passing the parameter values to each instance of the subcircuit.

So:

```
** Definition
.SUBCKT Filter IN OUT params: C1=1n alpha=1 f0=1k
C2 0 R1_P {C1*alpha*alpha/4}
C1 OUT R1_N {C1}
E1 OUT 0 R1_P 0 1
R1_R1_P R1_N \{2/(2*pi*f0*C1*alpha)\}R2 R1_N IN {2/(2*pi*f0*C1*alpha)}
```

```
.ENDS
** Subcircuit instance
X1 V1_P VOUT Filter params: C1=10n alpha=1 f0=10k
** AC source
V1 V1_P 0 AC 1 0
```
In the above example the parameters after *params:* in the .subckt line define default values should any parameters be omitted from the subcircuit instance line. It is not compulsory to define defaults but is generally recommended.

### **Note**

In the syntax definition for both subcircuit definitions and subcircuit instances, the *params:* specifier is shown as optional. If *params:* is included the '=' separating the parameter names and their values becomes optional.

# **3.4.5 Nesting Subcircuits**

Subcircuit definitions may contain both calls to other subcircuits and local subcircuit definitions.

If a subcircuit definition is placed within another subcircuit definition, it becomes local. That is, it is only available to its host subcircuit.

Calls to subcircuits may not be recursive. A subcircuit may not directly or indirectly call its own definition.

# **3.4.6 Global Nodes**

Sometimes it is desirable to refer to a node at the circuit's top level from within a subcircuit without having to explicitly pass it. This is sometimes useful for supply rails.

SIMetrix provides three methods.

- '#' prefix. Any node *within* a subcircuit prefixed with '#' will connect to a top level node of the same name *without* the '#' prefix.
- '\$g\_' prefix. Any node in the circuit prefixed '\$g\_' will be treated as global.
- Using [.GLOBAL.](#page-227-0)

The second approach is compatible with PSpice®. The third approach is compatible with Hspice®

Note the first two approaches are subtly different. In the second approach the '\$g\_' prefix must be applied to all connected nodes, whereas in the first approach the '#' prefix must be applied *only* to subcircuit nodes.

# **3.4.7 Subcircuit Preprocessing**

SIMetrix features a netlist preprocessor that is usually used for SIMPLIS simulations and was developed for that purpose. The preprocessor has some features that aren't available in the native simulator and for this reason it would be useful to be able to use the preprocessor for SIMetrix simulations.

It is not necessary to apply the preprocessor to the entire netlist. Any subcircuit call that defines preprocessor variables using the 'vars:' specifier will be passed to the preprocessor. For example:

```
X$C1 R1_P 0 ELEC_CAP_L13 vars: LEVEL=3 CC=1m
+ RSH_CC=1Meg IC=0 RESR=10m LESL=100n USEIC=1
```
calls the ELEC\_CAP\_L13 subcircuit but passes it through the preprocessor first. This model is a model for an electrolytic capacitor and uses a number of .IF statements to select model features according to the LEVEL parameter.

The preprocessor also provides a means of generating multiple devices using .WHILE. For information on the preprocessor, see the *SIMPLIS Reference Manual/Running SIMPLIS/Netlist Preprocessor*.

You can define parameters for preprocessed models using .VAR. See [.VAR](#page-288-0)

# **3.5 Model Binning**

### **3.5.1 Overview**

Some devices can be *binned*. This means that a number of different model definitions can be provided for the same device with each being valid over a limited range of some device parameter or parameters. The simulator will automatically select the appropriate model according to the value given for the device parameters.

Currently only BSIM3, BSIM4 and HiSIM HV MOSFETs may be binned. The binning is controlled by the length and width device parameters (L and W) while the LMIN, LMAX, WMIN and WMAX model parameters specify the valid range for each model.

# **Important Note**

The binned models should be placed directly in the netlist or called using either .INC or the Hspice® form of .LIB. They will not work correctly when installed as a model library or accessed with the SIMetrix form of .LIB.

# **3.5.2 Defining Binned Models**

Binned models are defined as a set consisting of two or more .MODEL definitions. Each of the definitions must be named using the following format:

root\_name.id



Each model definition must also contain a MIN/MAX parameter pair for each bin control parameter. For the BSIM3 MOSFET there are two bin control parameters, namely L and W with corresponding MIN/MAX pairs LMIN/LMAX and WMIN/WMAX. For a binned BSIM3 model, all four must be present. These parameters define the range of L and W over which the model is valid. When a model is required, the simulator searches all models with the same root\_name for a definition whose LMIN/LMAX and WMIN/WMAX parameters are compatible with the device's L and W.

### **3.5.3 Example**

```
.MODEL N1.1 NMOS LEVEL=49 ... parameters ...
+ LMIN=1u LMAX=4u WMIN=1u WMAX=4u
.MODEL N1.2 NMOS LEVEL=49 ... parameters ...
```

```
+ LMIN=4u LMAX=10u WMIN=1u WMAX=4u
.MODEL N1.3 NMOS LEVEL=49 ... parameters ...
+ LMIN=1u LMAX=4u WMIN=4u WMAX=10u
.MODEL N1.4 NMOS LEVEL=49 ... parameters ...
+ LMIN=4u LMAX=10u WMIN=4u WMAX=10u
** This device will use N1.1
M1 1 2 3 4 N1 L=2u W=2u
** This device will use N1.2
M2 1 2 3 4 N1 L=6u W=2u
** This device will use N1.3
M3 1 2 3 4 L=2u W=7u
** This device will use N1.4
M4 1 2 3 4 L=6u W=7u
```
# **3.6 Language Differences**

SIMetrix is compatible with some PSpice® and Hspice® extensions mainly so that it can read external model files. Some aspects of these alternative formats are incompatible with the SIMetrix native format and in such cases it is necessary to declare the language being used. See [Language Declaration](#page-24-0) for details on how to do this.

The following sections describe the incompatibilities between the three languages.

# **3.6.1 Inline Comment**

Hspice® uses the dollar ('\$') symbol for inline comments while SIMetrix and PSpice® use a semi-colon (';'). The language declaration described above determines what character is used.

# **3.6.2 Unlabelled Device Parameters**

The problem with unlabelled device parameters is illustrated with the following examples.

The following lines are legal in Hspice® mode but illegal in SIMetrix mode.

```
.PARAM area=2
Q1 C B E S N1 area
```
Q1 will have an area of 2. Conversely the following is legal in SIMetrix but is illegal in Hspice®:

```
.PARAM area=2
Q1 C B E S N1 area area
```
Again Q1 has an area of 2.

The problem is that SIMetrix does not require '=' to separate parameter names with their values whereas Hspice® does. *area* is a legal BJT parameter name so in the first example SIMetrix can't tell whether *area* refers to the name of the BJT parameter or the name of the .PARAM parameter defined in the previous line. Hspice® can tell the difference because if *area* meant the BJT parameter name it would be followed by an  $=$ '.

This line is legal and will be correctly interpreted in both modes

```
.PARAM area=2
Q1 C B E S N1 area=area
```
Although Hspice® always requires the '=' to separate parameter names and values, it continues to be optional in SIMetrix even in Hspice® mode. It only becomes compulsory where an ambiguity needs to be resolved as in the second example above.

# **3.6.3 LOG() and PWR()**

The LOG() function means log to the base 10 in SIMetrix but in PSpice® and Hspice® means log to the base e. PWR() in PSpice® and SIMetrix means  $|x|^y$  whereas in Hspice® it means "if  $x \ge 0, |x|^y$  else  $-|x|$ <sup>y</sup>". The language declaration only affects the definition when used in expressions to define model and device parameters. When used in arbitrary source expressions, the language assumed is controlled by the method of implementing the device as follows:

#### SIMetrix:

B1 1 2 V=expression

#### PSpice®

E1 1 2 VALUE =  $\{expression\}$ 

#### Hspice®

E1 1 2 VOL = `expression'

Note that the function LN() always means log to base e and LOG10() always means log to base 10. We recommend that these functions are always used in preference to LOG to avoid confusion.

# **3.7 Customising Device Configuration**

### **3.7.1 Overview**

Models for discrete devices and for integrated circuit processes come from a variety of sources and are often designed for particular simulators, in particular, PSpice and Hspice. These simulators are not generally compatible with each other so it is not easy for SIMetrix to be simultaneously compatible with both. Further, SIMetrix itself needs to retain backward compatibility with its own earlier versions.

An example of conflict can be found with the standard diode. The SIMetrix diode with no level parameter specified is mainly compatible with PSpice. But the standard Hspice diode is quite different and not compatible. The SIMetrix Level=3 diode is however compatible with Hspice both for level=1 and level=3. To use Hspice level=1 diode models the user has to edit the model so that level is changed to 3.

It is not always convenient to modify model files and for this reason SIMetrix provides two methods to globally change level numbers and model names needed to select a particular device model. These are:

#### [.MAP statement](#page-239-0)

[Device configuration file](#page-240-0)

Both methods work the same way; the difference is the scope and lifetime of the changes. .MAP works only for the netlist in which it appears, whereas the device configuration file is a permanent setting and works for all simulations.

# **3.8 Initial Conditions**

Initial conditions may be applied to capacitors and inductors and may also be applied to a single node using the .IC statement. Initial conditions force a voltage or current to be applied during the DC operating point analysis. Here we describe the various methods to apply an initial condition.

### **3.8.1 Node Initial Condition**

A voltage initial condition may be applied to a node using the .IC statement, see [.IC.](#page-233-0) This method applies the initial condition through a fixed resistor. In effect the following circuit is applied to the node during the DC operating point then removed when the main analysis starts:



The above shows a driving resistance of 1 $\Omega$ . This is the default value but can be changed using the ICRES option:

**.OPTIONS** ICRES=1m

The above sets the resistance to  $1m\Omega$ .

Note that an initial condition may also be applied to a node or across a pair of nodes using a capacitor with a value of zero. See next section.

### **3.8.2 Capacitor Initial Condition**

An initial condition may be defined for a capacitor using the IC parameter. The following diagram shows how this is configured:



The actual interpretation of the IC parameter depends on the INITCONDMODE option setting: **.OPTIONS** INITCONDMODE=0|1|2

It also depends on the BRANCH parameter on the capacitor:

Cxxxx n1 n2 capacitance IC=init\_condition BRANCH=0|1

The different configurations have come about because of a need for compatibility with other simulators, namely SIMPLIS, Berkeley SPICE and PSpice.

The following table describes the various configurations:



Note that for full PSpice compatibility, the ICRES option should be set to 1m. Alternatively the option setting PSPICECOMPATIBILITY=1 or PSPICECOMPATIBILITY=2 may be set which sets ICRES to 1m and INITCONDMODE to 2.

# **3.8.3 Inductor Initial Condition**

An initial condition may be defined for a inductor using the IC parameter. The following diagram shows how this is configured:



The actual interpretation of the IC parameter depends on the INITCONDMODE option setting:

**.OPTIONS** INITCONDMODE=0|1|2

It also depends on the BRANCH parameter on the inductor:

Lxxxx n1 n2 inductance IC=init\_condition BRANCH=0|1

The different configurations have come about because of a need for compatibility with other simulators, namely SIMPLIS, Berkeley SPICE and PSpice.

The following table describes the various configurations:



# **Chapter 4**

# **Analog Device Reference**

# **4.1 Overview**

This chapter provides the full details of every option and parameter available with every *primitive* analog device that the simulator supports.

For documentation on digital and mixed signal devices supplied with SIMetrix, please see [Digital/Mixed](#page-159-0) [signal Device Reference.](#page-159-0)

# <span id="page-55-0"></span>**4.2 Further Documentation**

Some devices are fully documented by their developers and we have not repeated that documentation here. In most cases the documents may be found at our web site:

*https://www.simetrix.co.uk/app/supplementary.htm*

then click on Download links. You will need a user name and password to access this page.

# **4.3 ASM HEMT Gallium Nitride FET Model**

The "Advanced Spice Model High Electron Mobility Transistor" model is available with *Pro* and *Elite* versions. The model was developed for the emerging Gallium Nitride technology that is increasingly used for high-voltage high-frequency power applications. The current version implemented in SIMetrix is 101.0.0.

The ASM HEMT model was developed by Sourabh Khandelwal and others currently at Macquarie University, Sydney, Australia.

Documentation for the model may be found at the SIMetrix web site. See [Further Documentation](#page-55-0)

# **4.3.1 Netlist Entry**

Uxxx drain gate source bulk temperature modelname instance\_parameters

#### Where

*modelname* Model name *instance\_parameters* Instance parameters

# **4.3.2 Model Syntax**

**.MODEL** modelname ASMHEMT model\_parameters

Where



# **4.3.3 Notes**

The device may have 4 or 5 terminals with the netlist format as shown above.

Self heating will be modelled if the parameter SHMOD is non-zero and RTH0 is greater than zero. If the temperature node is present it can be used to add a thermal network. If omitted, an internal temperature node labelled *dt* will be used to implement self-heating effects. This node can be probed using the name *REF*#dt. For example, if the device has the reference U23, the internal temperature node may be accessed using the name U23#dt. To access internal nodes the KeepInternal option setting must be set. See [Option](#page-235-0) **[Settings](#page-235-0)** 

# **4.4 AC Table Lookup (including S-Parameters)**

# **4.4.1 Netlist Entry**

Uxxx node\_pairs modelname

#### Where



# **4.4.2 Model Format**

```
.MODEL modelname actable LOAD=filename [
NUMPORTS=number_of_ports ] [ DCMETHOD=extrapolate|extend ]
[ ]INTERPMETHOD=yparams|sparams]
[DCPARAMS=[dcgainvalues] ]
```
Where:





# **4.4.3 AC Table Notes**

The AC Table device implements a circuit device that is defined by a frequency lookup table. This device operates only in the small signal analysis modes, AC, Noise and TF. In transient and DC analyses it behaves like a simple linear DC gain block with no frequency dependence.

The lookup table for this device must be defined by a file and uses the industry standard 'Touchstone' format. The full details of this format are supplied as a separate document and maybe found on the SIMetrix web site. Please visit [Further Documentation](#page-55-0) for details. The document is freely distributable under the terms described therein and may also be found at various Internet sites.

The SIMetrix implementation of the touchstone format includes the following:

- 1. Y-parameters to any number of ports
- 2. S-parameters to any number of ports

Although there is no hard limit to the number of ports, there is likely to be a practical upper limit for s-parameters as these require conversion to y-parameters. A definition with a very large number of ports will likely be slow to run and maybe subject to substantial errors.

Z, H and G parameters are not supported. Also, noise parameters are not supported.

Touchstone files traditionally use the extension s*n*p (s-parameters) or y*n*p (y-parameters) where *n* indicates the number of ports. Be aware that SIMetrix uses the NUMPORTS parameter in the .model statement to determine the number of ports and will ignore the value of *n* in the filename extension.

# <span id="page-57-0"></span>**4.5 Arbitrary Source**

# **4.5.1 Netlist Entry**

#### Voltage source:

Bxxxx n+ n- [MIN=min\_value] [MAX=max\_value] V=expression

#### Current source:

Bxxxx n+ n- [MIN=min\_value] [MAX=max\_value] [M=multiplier] I=expression

#### Charge source:

Bxxxx n+ n- [M=multiplier] Q=expression

#### Flux source:

Bxxxx n+ n- FLUX=expression

An arbitrary source is a voltage or current source whose output can be expressed as an arbitrary relationship to other circuit voltages or currents.



The small-signal AC behaviour of the non-linear source is a linear dependent source with a proportionality constant equal to the derivative (or derivatives) of the source at the DC operating point.

Note that if MIN and/or MAX parameters are specified, they must precede the defining expression.

Charge and flux sources implement capacitors and inductors respectively. See [Charge and Flux Devices](#page-59-0) for details.

If the source is a current, the direction of flow is into the positive node  $(n+)$ .

# **4.5.2 Notes on Arbitrary Expression**

It is essential that the expression used for an arbitrary source is *well conditioned*. This means that it must be valid for all values (i.e. from  $-\infty$  to  $+\infty$ ) of its input variables (i.e. circuit voltages and currents) and that it is continuous. It is also desirable - although not always absolutely necessary - for the function to be continuous in its first derivative; i.e. it does not have any abrupt changes in slope.

A badly designed expression will lead to poor convergence, non-convergence or slow run times. This is especially the case if the source is used in a feedback loop. If the arbitrary source is used open loop then the above conditions can sometimes be relaxed especially if the input signal is well defined e.g. derived directly from a signal source.

Some functions are not continuous in nature. E.g. the STP() and SGN() functions are not. These may nevertheless be used in an expression as long as the end result is continuous.

Similarly, the IF() function (or ternary conditional using '?' and ':') should be used with care. The following IF() function *is* continuous:

IF(v1>v2, 0, (v1-v2)  $*2$ )

When  $v1=v2$  both true and false values equate to zero so the function has no abrupt change. The function still has a discontinuous first derivative with respect to both v1 and v2 which is still undesirable but will work satisfactorily in most situations.

The following example is *not* continuous:

IF(v1>v2, 0, 5)

The result of this will switch abruptly from 0 to 5 when  $v1=v2$ . This is not something that the simulator can be guaranteed to handle and cannot be implemented in real life.

A better, albeit less intuitive method, of achieving the intent of the above is:

```
(TANH((v2-v1)*factor)+1)*2.5+2.5
```
where factor is some number that determines the abruptness of the switching action. For a value of 147, 95% of the full output will be achieved with just 10mV overdrive.

Alternatively the IF functions slew rate feature may be used:

IF(v1>v2, 0, 5, 1e9)

See [IF\(\) Function](#page-39-0) for further details.

# <span id="page-59-0"></span>**4.5.3 Charge and Flux Devices**

It is possible to define capacitors and inductors directly using the arbitrary source. Capacitors must be defined in terms of their charge and inductors by their flux. These are defined in the same as voltage and current arbitrary sources but using 'q' or 'flux' instead of 'v' or 'i'. E.g. the following defines a simple linear capacitor:

B1 n1 n2  $Q = C*V(n1, n2)$ 

Similarly a linear inductor is:

B1 n1 n2 flux =  $L * i(B1)$ 

The main benefit of this feature is that it makes it possible to define non-linear capacitors and inductors directly. It is also possible to use the ddt() and sdt() functions to create capacitors and inductors using regular current and voltage sources. However, the above method is more efficient.

As with voltage and current arbitrary sources, it is possible to use any combination of voltages and currents in the expression. So, for example, the following defines a transformer:

```
Bprimary p1 p2 flux = Lp*i(Bprimary) + M*i(Bsecondary)
Bsecondary s1 s2 flux = Ls*i(Bsecondary) + M*i(Bprimary)
```
# **4.5.4 Arbitrary Source Examples**

### **Example 1 - Ideal Power Converter**

This examples also demonstrates the use of expressions within subcircuits (see [Using Expressions\)](#page-32-0).

The following subcircuit implements an idealised power converter with an efficiency of eff and whose output voltage is proportional to the input voltage (vinn,vinp) multiplied by the control voltage (vcp,vcn). It is intended to simulate the voltage/current characteristics of a switching power converter.

```
.subckt powerconv voutp voutn vinp vinn vcp vcn
biin1 vinp vinn i=-v(voutp, voutn)/v(vinp, vinn)*i(vout1)/{eff}
vout1 bmult1_n voutn 0
bmult1 voutp bmult1_n v=v(vinp, vinn) *v(vcp, vcn)
r1 vcp vcn 1meg
.ends
```
Once again, with an appropriate schematic symbol, the device can be placed on the schematic as a block as shown below:



# **Example 2 - Voltage Multiplier**

The expression for an arbitrary source must refer to other voltages and/or currents on the schematic. Currents are referenced as voltage sources and voltages as netnames. Netnames are usually allocated by the netlister. For information on how to display and edit the schematic's netnames, refer to [Displaying Net](#page-17-1) [and Pin Names.](#page-17-1)



In the above circuit the voltage across B1 will be equal to the product of the voltages at nodes n1 and n2.

An alternative approach is to define the arbitrary source within a subcircuit. E.g.

```
.subckt MULT out in1 in2
B1 out 0 \text{ V=V(inl)}*V(in2).ends
```
which can be added to the netlist manually. (To find out how to add additional lines to the netlist when using the schematic editor, refer to [Adding Extra Netlist Lines\)](#page-17-0). A symbol could be defined for it and then placed on the schematic as a block as shown below:



# **Example 3 - Voltage comparator**

B3 q3\_b 0 V=atan(V(n1,n2)\*1000)

This can also be added to the schematic in the same way as for the multiplier described above.

# **4.5.5 PSpice and Hspice syntax**

SIMetrix supports the PSpice® and Hspice® syntax for arbitrary sources. This is for compatibility with some manufacturers device models. For PSpice® the VALUE = and TABLE = devices are supported as well as Q (charge) and F (flux) devices. For Hspice® VOL= and CUR= are supported.

Basic syntax for PSpice sources is as follows:

#### Voltage source:

Exxxx node1 node2 VALUE {expression}

#### Current source:

Gxxxx node1 node2 VALUE {expression}

#### Charge source:

Exxxx node1 node2 Q {expression}

#### Flux source:

Exxxx node1 node2 F {expression}

In all of the above, *expression* is in the same format and can use the same functions as the native SIMetrix arbitrary source with some important differences as described below:

- The log() function is natural log. In the SIMetrix native source, log() means log to base 10. To avoid confusion it is always best to use ln() for natural log and log10() for log to base 10.
- The  $\hat{ }$  operator means exclusive-or if used in the test expression of an IF() function otherwise it means raise-to-power. In the SIMetrix native source it always means raise-to-power.

# **4.6 Bipolar Junction Transistor (SPICE Gummel Poon)**

# **4.6.1 Netlist Entry**

Qxxxx collector base emitter [substrate] modelname [area] [OFF] [IC=vbe,vce] [TEMP=local\_temp] [M=mult] [DTEMP=dtemp]



# **4.6.2 NPN BJT Model Syntax**

**.model** modelname NPN ( parameters )

### **4.6.3 PNP BJT Model Syntax**

**.model** modelname PNP ( parameters )

### **4.6.4 Lateral PNP BJT Model Syntax**

**.model** modelname LPNP ( parameters )

# **4.6.5 BJT Model Parameters**

The symbols ' $\times$ ' and ' $\div$ ' in the Area column means that the specified parameter should be multiplied or divided by the *area* factor respectively.









# **4.6.6 Hspice Temperature Parameters**

The parameters defined in the following table are temperature coefficients and apply if the Hspice temperature model is enabled. This is the case if one or more of the following parameters are defined in the .MODEL statement:

TLEV, TLEVC, TIKF1, TIKF2, TIKR1, TIKR2, TIRB1, TIRB2.

If none of these parameters are specified, the standard (SPICE) temperature model is enabled and the following parameters have no effect.







# **4.6.7 Notes**

The bipolar junction transistor model in SPICE is an adaptation of the integral charge control model of Gummel and Poon.

This modified Gummel-Poon model extends the original model to include several effects at high bias levels. The model will automatically simplify to the simpler Ebers-Moll model when certain parameters are not specified.

The dc model is defined by the parameters IS, BF, NF, ISE, IKF, and NE which determine the forward current gain characteristics, IS, BR, NR, ISC, IKR, and NC which determine the reverse current gain characteristics, and VAF and VAR which determine the output conductance for forward and reverse regions. Three ohmic resistances RB, RC, and RE are included, where RB can be high current dependent. Base charge storage is modelled by forward and reverse transit times, TF and TR, the forward transit time TF being bias dependent if desired, and non-linear depletion layer capacitances which are determined by CJE, VJE, and MJE for the B-E junction, CJC, VJC, and MJC for the B-C junction and CJS, VJS, and MJS for the C-S (Collector-Substrate) junction. The temperature dependence of the saturation current, IS, is determined by the energy-gap, EG, and the saturation current temperature exponent, XTI. Additionally base current temperature dependence is modelled by the beta temperature exponent XTB in the new model.

This implementation includes further enhancements to model quasi-saturation effects. This is governed by the model parameters RCO, QCO, GAMMA and for temperature dependence, QUASIMOD, VG, D and CN. The quasi-saturation model is compatible with PSpice. Hspice models may be accommodated by setting RC to zero and RCO to the value of RC in the Hspice model.

### **References**

The Quasi-saturation model was developed from the following paper:

George M. Kull, Laurence W. Nagel, Shiuh-Wuu Lee, Peter Lloyd, E. James Prendergast and Heinz Dirks, "A Unified Circuit Model for Bipolar Transistors Including Quasi-Saturation Effects". IEEE Transactions on Electron Devices, Vol. ED-32, No 6 June 1985, pages 1103-1113

# **4.7 Bipolar Junction Transistor ( VBIC without self heating)**

### **4.7.1 Netlist Entry**

Qxxxx collector base emitter [substrate] modelname [M=multiplier] [AREA|SCALE=area]





# **4.7.2 Model Syntax**

**.MODEL** modelname NPN|PNP LEVEL=4 parameters

# **4.7.3 Model Parameters**









# **4.7.4 Notes**

The VBIC model is only available with *Elite* versions.

The Vertical Bipolar Inter-Company (VBIC) model is an advanced bipolar junction transistor model. This is the 4-terminal non-thermal version. There is also a version that supports self-heating effects and has 5 terminals, see [Bipolar Junction Transistor \(VBIC with self heating\).](#page-71-0)

For more information about VBIC, please refer to this link:

*[VBIC Reference](http://www.simetrix.co.uk/app/ext/vbic.htm)*

# <span id="page-71-0"></span>**4.8 Bipolar Junction Transistor (VBIC with self heating)**

# **4.8.1 Netlist Entry**





# **4.8.2 Model Syntax**
**.MODEL** modelname NPN|PNP LEVEL=1004 parameters

#### **4.8.3 Model Parameters**

Model parameters are identical to the non-thermal version except for the addition of the following:



#### **4.8.4 Notes**

The VBIC model is only available with *Elite* versions.

This model is the same as the VBIC non-thermal model except for the addition of self-heating effects. Use the non-thermal version if you do not need self-heating as its implementation is simpler and will run faster.

The *thermal\_node* may be used to connect external thermal networks to model thermal flow. Power in watts is represented by current and temperature rise in Kelvin is represented by the voltage. Note that the voltage is temperature rise above the simulation temperature, not an absolute value.

# **4.9 Bipolar Junction Transistor (MEXTRAM)**

See [NXP Compact Models.](#page-149-0)

# **4.10 Bipolar Junction Transistor (HICUM)**

#### **4.10.1 Netlist Entry**

Qxxxx collector base emitter [substrate] modelname

Where:



### **4.10.2 NPN Model Syntax**

**.MODEL** modelname NPN LEVEL=8 parameters

OR

**.MODEL** modelname HICUM\_211 PNP=0 parameters

#### **4.10.3 PNP Model Syntax**

**.MODEL** modelname PNP LEVEL=8 parameters

OR

**.MODEL** modelname HICUM\_211 PNP=1 parameters

#### **4.10.4 Notes**

The model provided is "Level 2 version 2.11".

The model was implemented from Verilog-A code. It has received only minor changes from the original supplied by the developers. These changes are to implement PNP devices and to overcome a problem in the original model whereby it is possible for it to converge to an erroneous state.

The SIMetrix implementation of this model has been tested using the benchmark results provided by the developers. The majority of the tests showed a match of better than 0.1%. A few were over  $1\%$  with one deviating by 7%. These were investigated and it was found that the reference data was in error probably because of insufficient convergence tolerance.

# **4.11 Capacitor**

#### **4.11.1 Netlist Entry**

```
Cxxxx n1 n2 [model_name] value [IC=initial_condition] [TEMP=local_temp]
  [TC1=tc1] [TC2=tc2] [VC1=vc1] [VC2=vc2] [BRANCH=0|1] [M=mult] [DTEMP=dtemp]
   [ESR=esr]
```


*dtemp* Differential temperature. Similar to *local\_temp* but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence. *esr* Effective series resistance. If non-zero (the default value), a resistor of

value *esr* will be connected in series with the capacitor. The resulting implementation of a series RC network is more efficient and offers better convergence than using a separate R and C. This is especially the case if the capacitor has a high value and is non-grounded.

Important: this resistor is noiseless; if the noise in the ESR is important in your design, you should use a separate resistor and omit this parameter in the capacitor.

#### **4.11.2 Model Syntax**

**.model** modelname CAP ( parameters )

## **4.11.3 Model Parameters**



# **4.12 Current Controlled Current Source**

## **4.12.1 Netlist Entry**

#### **Linear Source**

Fxxxx nout+ nout- vc current\_gain [GOUT=output\_conductance]





The controlling device can be any native (i.e. non-subcircuit) device in the circuit. The current used will be the current flowing into its first terminal. The first terminal is the one that is first in the device's netlist entry. Note that if the device is not a voltage source or implemented as a voltage source, the current is sensed by placing a zero-volt voltage source in series with the sensing device. This is done automatically and no user action is required.

GOUT has a default value of zero unless the PSPICEGMIN option is set in which case it has a default value of GMIN. GMIN is set using ".OPTIONS GMIN=*value*" and has a default value of 1e-12.

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for IC's. (Some operational amplifier models for example use several polynomial sources). In general, however the arbitrary source (see [Arbitrary Source\)](#page-57-0) is more flexible and easier to use.

### **Polynomial Source**

```
Fxxxx nout+ nout- POLY( num_inputs ) vc1 vc2 ...
+ polynomial_specification
```


The specification of the controlling voltage source or source requires additional netlist lines. The schematic netlister automatically generates these for the four terminal device supplied in the symbol library.

### **4.12.2 Example**



In the above circuit, the current in the output of F1 (flowing from top to bottom) will be 0.1 times the current in R2.

#### <span id="page-76-0"></span>**4.12.3 Polynomial Specification**

The following is an extract from the SPICE2G.6 user manual explaining polynomial sources.

SPICE allows circuits to contain dependent sources characterised by any of the four equations

- $i=f(v)$
- $v=f(v)$
- $i=f(i)$
- $v=f(i)$

where the functions must be polynomials, and the arguments may be multidimensional. The polynomial functions are specified by a set of coefficients *p0, p1, ..., pn*. Both the number of dimensions and the number of coefficients are arbitrary. The meaning of the coefficients depends upon the dimension of the polynomial, as shown in the following examples:

Suppose that the function is one-dimensional (that is, a function of one argument). Then the function value fv is determined by the following expression in fa (the function argument):

$$
fv = p0 + (p1.fa) + (p2.fa2) + (p3.fa3) + (p4.fa4) + (p5.fa5) + ...
$$

Suppose now that the function is two-dimensional, with arguments fa and fb. Then the function value fv is determined by the following expression:

$$
fv = p0 + (p1.fa) + (p2.fb) + (p3.fa2) + (p4.fa.fb) + (p5.fb2)
$$
  
+
$$
(p6.fa3) + (p7.fa2.fb) + (p8.fa.fb2) + (p9.fb3) + ...
$$

Consider now the case of a three-dimensional polynomial function with arguments fa, fb, and fc. Then the function value fv is determined by the following expression:

$$
fv = p0 + (p1.fa) + (p2.fb) + (p3.fc) + (p4.fa2) + (p5.fa.fb) + (p6.fa.fc) + (p7.fb2) + (p8.fb.fc)+ (p9.fc2) + (p10.fa3) + (p11.fa2.fb) + (p12.fa2.fc) + (p13.fa.fb2) + (p14.fa.fb.fc)+ (p15.fa.fc2) + (p16.fb3) + (p17.fb2.fc) + (p18.fb.fc2) + (p19.fc3) + (p20.fa4) + ...
$$

Note If the polynomial is one-dimensional and exactly one coefficient is specified, then SPICE assumes it to be  $p1$  (and  $p0 = 0.0$ ), in order to facilitate the input of linear controlled sources.

## **4.13 Current Controlled Switch**

#### **4.13.1 Netlist Entry**

Wxxx nout+ nout- vc model

*nout*+ Positive output node



The controlling device can be any native (i.e. non-subcircuit) device in the circuit. The current used will be the current flowing into its first terminal. The first terminal is the one that is first in the device's netlist entry. Note that if the device is not a voltage source or implemented as a voltage source, the current is sensed by placing a zero-volt voltage source in series with the sensing device. This is done automatically and no user action is required.

#### **4.13.2 Current Controlled Switch Model Syntax**

**.model** modelname ISWITCH ( parameters )

#### **4.13.3 Current Controlled Switch Model Parameters**



### **4.13.4 Current Controlled Switch Notes**

The current controlled switch has two modes of operation:

1. Continuous mode: Behaves like a current controlled resistor. Between ION and IOFF the resistance varies gradually following a cubic law as described with the following equation: where:

 $R = 1/exp(-Lm - Lr * factor * (1.5 - 2 * factor * factor))$  $factor = I_{control} - 0.5$  $Lm = -0.5 * ln(q_{on} * q_{off})$  $Lr = ln(q_{off}/q_{on})$  $I_{control} = I_{cntrl} > 1.0$ :  $1.0, I_{cntrl} < 0.0$ :  $0.0, I_{cntrl}$  $I_{cntrl} = (i_{in} - (ION + IOFF)/2)/(ION - IOFF) + 0.5$  $g_{off} = ROFF \iff 0: 1/ROFF, ROFF = 0: GMIN$  $g_{on} = RON \leq 0: 1/RON, RON = 0: GMIN$ 

2. Hysteresis mode: Switches in a controlled time with a hysteresis characteristic. This mode is enabled if the IT parameter is defined. The switch transitions to the on state when:

 $I_{control} > IT + IH$ 

and to the off state when:

 $I_{control} < IT - IH$ 

The transition will be delayed by TD and the transition time will be TON when changing from OFF state to ON state and TOFF when changing from ON state to OFF state.

The transition will follow the same characteristic as continuous mode. That is, during the transition period the actual resistance of the switch will follow the continuous mode characteristic with the control current following a linear transition between ION and IOFF.

Hysteresis mode is similar and usually compatible with what is known as short-transition mode in PSpice. The difference is that in short-transition mode, the switching time is uncontrolled whereas in SIMetrix hysteresis mode the transition time is controlled by the TON and TOFF parameters.

GMIN is a simulation parameter which defaults to 1.0E-12 but which can changed using the [.OPTIONS](#page-250-0) statement.

## **4.14 Current Controlled Voltage Source**

### **4.14.1 Netlist Entry**

#### **Linear Source**

Hxxxx nout+ nout- vc transresistance



The controlling device can be any native (i.e. non-subcircuit) device in the circuit. The current used will be the current flowing into its first terminal. The first terminal is the one that is first in the device's netlist entry. Note that if the device is not a voltage source or implemented as a voltage source, the current is sensed by placing a zero-volt voltage source in series with the sensing device. This is done automatically and no user action is required.

It is legal for the device to reference itself. E.g.

H1 n1 n2 H1 1

The above implements a 1 Ohm resistor.

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for IC's. (Some Op-amp models use several polynomial sources). In general, however the arbitrary source is more flexible and easier to use.

## **Polynomial Source**

```
Hxxxx nout+ nout- POLY( num_inputs ) vc1 vc2 ...
   + polynomial_specification
```


The specification of the controlling voltage source or source requires additional netlist lines. The schematic netlister automatically generates these for the four terminal device supplied in the symbol library.

# **4.15 Current Source**

### **4.15.1 Netlist Entry**

Ixxxx n+ n- [DC dcvalue] [AC magnitude [phase]] [transient\_spec]



## **4.16 Diode - Level 1 and Level 3**

#### **4.16.1 Netlist Entry**

Dxxxx n+ n- model\_name [area] [OFF] [IC=vd] [TEMP=local\_temp] + [PJ=periphery] [L=length] [W=width] [M=mult] [DTEMP=dtemp]

#### *n*+ Anode



### **4.16.2 Examples**



### **4.16.3 Diode Model Syntax**

**.model** modelname D ( LEVEL=[1|3] parameters )

#### **4.16.4 Diode Model Parameters - Level = 1**

The symbols ' $\times$ ' and ' $\div$ ' in the Area column means that the specified parameter should be multiplied or divided by the *area* factor respectively.





Notes The dc characteristics of the diode are determined by the parameters IS, N, ISR, NR and IKF. An ohmic resistance, RS, is included. Charge storage effects are modelled by a transit time, TT, and a non-linear depletion layer capacitance which is determined by the parameters CJO, VJ, and M. The temperature dependence of the saturation current is defined by the parameters EG, the energy and XTI, the saturation current temperature exponent. Reverse breakdown is modelled by an exponential increase in the reverse diode current and is determined by the parameters BV and IBV (both of which are positive numbers).



# **4.16.5 Diode Model Parameters - Level = 3**



The parameters CJSW and JSW are scaled by the instance parameter PJ whose default value is 0.0.

If L and W instance parameters are supplied, the diode is scaled by the factor: M\*(L\*SHRINK-XW)\*(W\*SHRINK-XW) otherwise it is scaled by M\*AREA.

#### **4.16.6 Using Hspice Diodes**

In Hspice Level 1 diodes are the same as the SIMetrix Level 3 diode. To map Level 3 to Level 1, add this line to the netlist

**.OPTIONS** HSPICEMODELS=1

This setting also has the same effect:

**.OPTIONS** HSPICECOMPATIBILITY=1

See [.OPTIONS](#page-250-1) for more details

M and AREA are instance parameters which default to 1.0

# **4.17 Diode - Soft Recovery**

#### **4.17.1 Netlist Entry**

Dxxxx n+ n- model\_name [TEMP=local\_temp]



#### **4.17.2 Diode Model Syntax**

**.model** modelname SRDIO ( parameters )

## **4.17.3 Soft Recovery Diode Model Parameters**



#### **4.17.4 Basic Equations**

The model is based on the paper "A Simple Diode Model with Reverse Recovery" by Peter Lauritzen and Cliff Ma. (See references). The model's governing equations are quite simple and are as follows:

$$
i_d = \frac{q_e - q_m}{TT}
$$

$$
\frac{dq_m}{dt} + \frac{q_m}{TAU} - \frac{q_e - q_m}{TT} = 0
$$

$$
q_e = IS \cdot TAU \cdot \left(\exp\left(\frac{v_d}{N \cdot V_t}\right) - 1\right)
$$

In addition the model uses the standard SPICE equations for junction capacitance and temperature dependence of IS.

#### **4.17.5 References**

Peter O. Lauritzen, Cliff L. Ma, *A Simple Diode Model with Reverse Recovery*, IEEE Transactions on Power Electronics, Vol. 6, No 2, pp 188-191, April 1991.

# **4.18 Diode CMC**

The "Diode CMC" model is available with the *Elite* versions of SIMetrix.

The "Diode CMC" model is derived from the NXP Juncap 2 model with a recovery model developed by the University of Hiroshima with other developments by the Silicon Integration Initiative (Si2). It is used predominantly for integrated circuit design.

One version of the model is currently available. This is version 2. This may be accessed using parameters LEVEL=7 and VERSION=2

#### **4.18.1 Netlist Entry**

The device must have 2 terminals with the netlist format as shown below.

```
Dxxx anode cathode modelname instance parameters
```
#### **4.18.2 Diode Model Syntax**

**.model** modelname D (LEVEL=7 VERSION=2 parameters )

# **4.19 Diode - Perfect**

The Perfect Diode has zero off-state current and zero on-state resistance. Its forward voltage drop defaults to zero but can be set to any value through a model parameter

### **4.19.1 Netlist Entry**

The device must have 2 terminals with the netlist format as shown below.

Uxxx anode cathode modelname

#### **4.19.2 Perfect Diode Model Syntax**

**.model** modelname perfect\_diode ( parameters )

#### **4.19.3 Perfect Diode Model Parameters**



#### **4.19.4 Basic Equations**

 $V_d \leq VFWD$ :  $I_d = 0$ 

$$
I_d > 0.0 : V_d = VFWD
$$

Where:

 $V_d$  is the voltage across the diode.

 $I_d$  is the current through the diode.

#### **4.19.5 Notes**

Although the device has perfect behaviour, it is sometimes necessary to introduce imperfections in order to allow convergence. If convergence problems are encountered, adding some shunt resistance, shunt capacitance or series resistance can help.

# **4.20 Inductor (Ideal)**

Lxxxx n1 n2 value [IC=init\_cond] [BRANCH=0|1]

## **4.20.1 Netlist Entry**



#### **4.20.2 See Also**

[Mutual Inductor.](#page-142-0)

# **4.21 Inductor (Saturable)**

## **4.21.1 Netlist Entry**





## **4.21.2 Model format - Jiles-Atherton model with hysteresis**

**.MODEL** model\_name CORE parameters

### **4.21.3 Model format - simple model without hysteresis**

**.MODEL** model\_name CORENH parameters

#### **4.21.4 Jiles-Atherton Parameters**



## **4.21.5 Non-hysteresis Model Parameters**



## **4.21.6 Notes on the Jiles-Atherton model**

The Jiles-Atherton model is based on the theory developed by D.C. Jiles and D.L. Atherton in their 1986 paper "Theory of Ferromagnetic Hysteresis". The model has been modified to correct non-physical behaviour observed at the loop tips whereby the slope of the B-H curve reverses. This leads to non-convergence in the simulator. The modification made is that proposed by Lederer et al. (See references below). Full details of the SIMetrix implementation of this model including all the equations

are provided in a technical note. This can be found at the SIMetrix web site please visit [Further](#page-55-0) [Documentation](#page-55-0) for details.

The AHMODE parameter selects the equation used for the anhysteric function, that is the non-linear curve describing the saturating behaviour. When set to 0 the function is the same as that used by PSpice. When set to 1 the function is the original equation proposed by Jiles and Atherton. See the Jiles-Atherton-Model.pdf technical note for details.

If the UE parameters is specified either on the device line or in the model, an air gap value is calculated and the parameters GAP and GAPM are ignored. See the Jiles-Atherton-Model.pdf technical note for the formula used.

The parameter names and their default values for the Jiles-Atherton model are compatible with PSpice, but the netlist entry is different.

#### **4.21.7 Notes on the non-hysteresis model**

This is simply a reduced version of the Jiles-Atherton model with the hysteresis effects removed. The anhysteric function and the air-gap model are the same as the Jiles-Atherton model.

#### **4.21.8 Implementing Transformers**

This model describes only a 2 terminal inductor. A transformer can be created using a combination of controlled sources along with a single inductor. The SIMetrix schematic editor uses this method.

The schematic editor provides a means of creating transformers and this uses an arrangement of controlled sources to fabricate a non-inductive transformer. Any inductor can be added to this arrangement to create an inductive transformer. The method is simple and efficient. The following shows how a non-inductive three winding transformer can be created from simple controlled sources:

```
F1 0 n1 E1 1
E1 W1A W1B n1 0 1
F2 0 n1 E2 1
E2 W2A W2B n1 0 1
F3 0 n1 E3 1
E3 W3A W3B n1 0 1
```
Connecting an inductor between n1 and 0 in the above provides the inductive behaviour. This is in fact how the SIMetrix schematic editor creates non-linear transformers.

Note that you cannot use the mutual inductor device with the saturable inductor.

#### **4.21.9 Plotting B-H curves**

Both models can be enabled to output values for flux density in Tesla and magnetising force in  $A.m^{-1}$ . To do this, add the following line to the netlist:

**.KEEP** Lxxx#B Lxxx#H

Replace Lxxx with the reference for the inductor. (e.g. L23 etc.). You will find vectors with the names Lxxx#B Lxxx#H available for plotting in the waveform viewer.

#### **4.21.10 References**

1. Theory of Ferromagnetic Hysteresis, DC.Jiles, D.L. Atherton, Journal of Magnetism and Magnetic Materials, 1986 p48-60.

2. On the Parameter Identification and Application of the Jiles-Atherton Hysteresis Model for Numerical Modelling of Measured Characteristics, D Lederer, H Igarashi, A Kost and T Honma, IEEE Transactions on Magnetics, Vol. 35, No. 3, May 1999

# **4.22 Inductor (Table lookup)**

#### **4.22.1 Netlist Entry**

Uxxxx n1 n2 model\_name [IC=initial\_condition] [USEIC=use\_ic]



#### **4.22.2 Model syntax**

**.MODEL** model\_name TABLE\_INDUCTOR parameters



#### **Model Example**

**.MODEL** TABLE\_IND table\_inductor L=1 USEIC=0 IC=0 + RSERIES=0 RSHUNT=0 SMOOTH=2 TABLE\_SIZE=7 + ITABLE=[0, 8.3333, 16.666, 25, 33.3333, 41.666, 50] + LTABLE=[3.36e-07, 3.36e-07, 3.34e-07, 3.27e-07, 3.09e-07, 1.86e-07, 4.21e-08]

The above example has an inductance of 3.36e-07H at 0A falling to 4.21e-08 at 50A.

#### **4.22.3 Boundary Inductance**

The inductance for this device is defined by a lookup table over a specific range. However, the behaviour at currents beyond that defined in the table must also be defined. We refer to the inductance as the 'boundary inductance'. This follows a characteristic of the form:

$$
A/(C + i^2) + LMIN/L
$$

Where A and C are chosen so that the absolute inductance and  $\frac{dL}{di}$  matches the table function at the final point.

#### **4.22.4 Smoothing Function**

The SMOOTH parameter can be set to an integer between 1 and 4 to select a smoothing function. The following table describes the alternative strategies available:



SMOOTH=2 and SMOOTH=3 select a cubic spline function. A cubic spline fits a series of cubic polynomials through all points such that the function is continuous in the first and second derivatives. Cubic splines generally require boundary conditions to be set; that is some condition to define the first and last points. This is the only difference between SMOOTH=2 and SMOOTH=3. SMOOTH=2 usually gives the best results but can, in some situations, result in a positive slope at the join with the boundary inductance function. This cannot be matched to the boundary inductance and in these circumstances the device will fail with the error message:

```
***ERROR*** instance <ref>: Cannot fit spline to table using SMOOTH=2 strategy.
Try using SMOOTH=1 or SMOOTH=3
```
In this case SMOOTH=1 or SMOOTH=3 can be selected.

# **4.23 Insulated Gate Bipolar Transistor**

#### **4.23.1 Netlist Entry**

*emitter* Emitter node



*area* Device area in m<sup>2</sup> (overrides model parameter of the same name)



#### **4.23.2 Model syntax**

**.MODEL** model\_name NIGBT parameters



## **4.23.3 Notes**

The IGBT model is based on the model developed by Allen R. Hefner at the National Institute of Standards and Technology. The parameter names, default values and units have been chosen to be compatible with the PSpice implementation of the same model.

For more information, please refer to:

*Modelling Buffer Layer IGBT's for Circuit Simulation*, Allen R. Hefner Jr, IEEE Transactions on Power Electronics, Vol. 10, No. 2, March 1995

*An Experimentally Verified IGBT Model Implemented in the Saber Circuit Simulator*, Allen R. Hefner, Jr., Daniel M. Diebolt, IEE Transactions on Power Electronics, Vol. 9, No. 5, September 1994

# **4.24 Junction FET**

#### **4.24.1 Netlist Entry**

```
Jxxxx drain gate source modelname [area] [OFF] [IC=vds, vgs]
+ [TEMP=local_temp] [M=mult] [DTEMP=dtemp]
```


## **4.24.2 N Channel JFET: Model Syntax**

**.model** modelname NJF ( parameters )

#### **4.24.3 P Channel JFET: Model Syntax**

**.model** modelname PJF ( parameters )

### **4.24.4 JFET: Model Parameters**

The symbols ' $\times$ ' and ' $\div$ ' in the Area column means that parameter should be multiplied or divided by the area factor respectively.





# **4.24.5 DIBL Equations**

The parameters DVT0, DVT1, DVT2 and DVTP are non-standard. These accommodate drain-induced barrier lowering (DIBL) and modify the threshold voltage with Vds as follows:

$$
V_{th} = VTO-DVTO*V_{ds} - \frac{DVT1}{(DVT2+V_{ds})^{DVTP}}
$$

## **4.24.6 Examples**



Q2 is a U430 with a local temperature of 100°C.

# **4.25 Laplace Transfer Function - Lumped Implementation**

## **4.25.1 Netlist entry**

Axxxx input output model\_name

## **4.25.2 Connection details**



#### **4.25.3 Model format**

**.MODEL** model\_name s\_xfer parameters

## **4.25.4 Model parameters**





#### **4.25.5 Description**

This device was formerly known as the S-domain Transfer Function Block. It implements an arbitrary linear transfer function expressed in the frequency domain using a Laplace transform. This is one of two models that can implement a Laplace transfer function. The other one is [Laplace Transfer Function](#page-100-0) [Convolution Implementation](#page-100-0)

The operation and specification of the device is illustrated with the following examples.

#### **4.25.6 Examples**

#### **Example 1 - A single pole filter**



Model for above device:

**.model** Laplace s\_xfer laplace="1/(s+1)" denormalized\_freq=1

This is a simple first order roll off with a 1 second time constant as shown below



## **Example 2 - Single pole and zero**

```
.model Laplace s_xfer
+ laplace="(1/s)/(1/s + 1/(0.1*s+1))"
+ denormalized_freq=1
```
The laplace expression has been entered how it might have been written down without any attempt to simplify it. The above actually simplifies to  $(0.1*s+1)/(1.1*s+1)$ .



#### **Example 3 - Underdamped second order response**

```
.model Laplace s_xfer
+ laplace="1/(s2+1.1*s+1)"
+ denormalized_freq=2k
```
The above expression is a second order response that is slightly underdamped. The following graph shows the transient response.



## **Example 4 - 5th order Chebyshev low-pass filter**

The S-domain transfer block has a number of built in functions to implement standard filter response. Here is an example. This is a 5th order chebyshev with -3dB at 100Hz and 0.5dB passband ripple.

```
.model Laplace s_xfer
+ laplace="chebyshevLP(5,100,0.5)"
+ denormalized_freq=1
```
and the response:



# **4.25.7 The Laplace Expression**

As seen in the above examples, the transfer function of the device is defined by the model parameter LAPLACE. This is a text string and must be enclosed in double quotation marks. This may be any arithmetic expression containing the following elements:





#### <span id="page-99-0"></span>**4.25.8 Defining the Laplace Expression Using Coefficients**

Instead of entering a Laplace expression as a string, this can also be entered as two arrays of numeric coefficients for the numerator and denominator. In general this is less convenient than entering the expression directly, but has the benefit that it supports the use of parameters. In this method, use the NUM\_COEFF and DEN\_COEFF parameters instead of the LAPLACE expression.

The following simple example, demonstrates the method

```
.param f0=10
\textbf{.param } w0 = \{2*3.14159265*f0\}.model laplace s_xfer num_coeff = [1] den_coeff = [{1/w0},1]
```
#### **4.25.9 Other Model Parameters**

- DENORMALISED FREO is a frequency scaling factor.
- INT IC specifies the initial conditions for the device. This is an array of maximum size equal to the order of the denominator. The right-most value is the zero'th order initial condition.
- NUM\_COEFF and DEN\_COEFF see [Defining the Laplace Expression Using Coefficients.](#page-99-0)
- GAIN and IN\_OFFSET are the DC gain and input offset respectively.

#### **4.25.10 Limitations**

SIMetrix expands the expression you enter to create a quotient of two polynomials. If the constant terms of both numerator and denominator are both zero, both are divided by S. That process is repeated until one or both of the polynomials has a non-zero constant term.

The result of this process must satisfy the following:

- The order the denominator must be greater than or equal to that of the numerator.
- The constant term of the denominator may not be zero.

#### **4.25.11 Implementation**

This device implements a Laplace transform using a network of integrators. The diagram below shows the configuration used for a third order network.



Vout = Vin.(N3.s3 + N2.s2 + N1.s + N0)/(s3 + D2.s2 + D1.s + D0)

This method can implement a quotient of polynomials in the s variable and any expression that can be reduced to a quotient of polynomials. For such expressions it is fast and efficient.

This method cannot implement expressions containing arbitrary functions such as square-root or exponentials. Such Laplace expressions must be implemented using the convolution method.

# <span id="page-100-0"></span>**4.26 Laplace Transfer Function - Convolution Implementation**

### **4.26.1 Netlist Entry**

Uxxxx p n cp cn modelname [M=m IC=ic VOLTAGE\_MODE=vm]



#### **4.26.2 Model Syntax**

**.model** modelname LAPLACE ( parameters )

#### **4.26.3 Model Parameters**



Note 1 Gain of block defaults to the value of the Laplace transfer function with s=0. If the transfer function cannot be evaluated at s=0, the expression is evaluated with s=1e-11. If that also fails DCGAIN is set to zero

<span id="page-101-0"></span>Note 2 If PSPICE\_COMPAT=0 1e-30 otherwise 1e-305

#### **4.26.4 Laplace transfer function**

The Laplace expression defines the behaviour of the device in the frequency domain. For example  $(1/(s+1))$ , defines a simple single pole low-pass filter. The expression may contain arithmetic operators and a number of functions as described in the following sections. Be aware that not any expression is physically realisable; for example ' $\exp(s)$ ' defines a negative delay, that is a device whose output responds to an input in the future.

#### **Operators**

 $+$  -  $\star$  / ^

where  $\land$  means raise to power. For lumped network implementation, the power must be an integer. Non-integral powers may be entered for convolution implementation.

#### **Constants**

Any decimal number following normal rules. SPICE style engineering suffixes are accepted.

#### **s Variable**

This can be raised to a power using  $\gamma$ , for example s $\gamma$ 2. If the power is an integer between 0 and 9 the  $\gamma$ may be omitted. For example:  $s2$  is the same as  $s^2$ .

### **Functions**

The following functions may be used.



#### **Filter response functions**

Filter response functions may be used in both lumped network implementation and convolution implementation.

These are described in the following table:



### **Lookup tables**

The frequency response of a system may be defined in tabular form using lookup tables. The lookup table consists of a sequence of values arranged in triplets. Each triplet is in the form  $frequency, value1, value2$ where  $value1$  and  $value2$  define the magnitude and phase in various ways as described below.

There are five variants of the lookup table as described below:



#### Example

Table\_M(0.01,1,30, 1,1,30, 10,0.1,30, 100,0.01,-30)

The above defines a response with a gain of 1 and a phase shift of 30 degrees from 0.01Hz to 1Hz. From 1Hz to 10Hz the gain falls from 1 to 0.1 with the phase shift remaining at 30 degrees. From 10Hz to 100Hz the gain falls from 0.1 to 0.01 and the phase changes from 30 to -30 degrees.

In real life it is not possible to implement a characteristic with the above behaviour as it is non-causal. However, it can be implemented if a suitable delay is added to the characteristic. The delay may be added using the DELAY parameter. Alternatively it may be added to the Laplace expression using  $exp(-delay.s)$ . E.g:

 $Table_M(0.01, 1, 30, 1, 1, 30, 10, 0.1, 30, 100, 0.01, -30)$  \* exp(-s\*2)

The above adds a 2 second delay.

For ease of reading, each triplet in the table may be placed on a separate line by prefixing each line with a '+' character. E.g.



Interpolation Between defined frequency points, the Laplace transfer function finds the magnitude and phase using interpolation. The interpolation is performed logarithmically on the magnitude data. Values outside the table frequency range are defined by their respective end points.

If the table contains zero frequency terms or zero magnitude terms, the values are replaced with the values of parameters TABLE\_ZERO\_FREQ and TABLE\_ZERO\_MAG parameters respectively. This is because the interpolation is performed logarithmically and this requires all values to be  $> 0$ .

For the above example the magnitude and phase are shown below:



#### **Parameters**

Parameters (defined with .PARAM) may be used in Laplace expressions.

#### **4.26.5 Implementation**

The Laplace transfer function is implemented using a convolution method.

In the frequency domain, a linear system may be represented by:

$$
Vout(s) = Vin(s).f(s)
$$

where  $f(s)$  is the transfer function.

In the time domain the same system may be represented by:

$$
Vout(t) = Vin(t) * f(t)
$$

Where  $f(t)$  is the impulse response of  $f(s)$  and  $*$  is the convolution operator.

This method is challenging to implement as simple convolution applied to simulation data in its raw form is an  $\mathcal{O}(n^2)$  algorithm. This means that the number of computations required at each step is proportional to the square of the number of steps. In practice this becomes unacceptably slow when there are more than about 10000 time steps.

SIMetrix overcomes this performance limitation by using an FFT based fast convolution method with a computation speed of  $\mathcal{O}(n \log^2 n)$ . Although dramatically faster, this algorithm requires data to be presented to it at fixed-interval steps which has the effect of placing an upper frequency limit. The actual upper frequency limit can be arbitrarily increased by increasing the number of steps (the value of  $n$ ) at the expense of speed and the memory consumed. In practice the default settings work well in most applications and give good performance and accuracy.

To perform the convolution, the simulator must also extract the impulse response of the Laplace transform. SIMetrix has three methods to do this:



#### **4.26.6 Impulse Response**

#### **Problems with Impulse Response Extraction**

For the convolution method an impulse response of the Laplace transfer function must be extracted. As mentioned above, three methods are attempted. The inverse FFT method and Stehfest methods are approximate in nature and for this reason, the result from each method is tested. If the test fails the impulse response is rejected and another method is attempted. If all methods fail the simulation will abort.

Transfer functions that decay slowly are likely to fail the inverse FFT method as this method requires that the impulse response decay to zero or nearly to zero. If the Stehfest method also fails, the problem can sometimes be resolved by increasing the inverse FFT size. This is controlled by the IMPULSE IFFT N

parameter. This increases the duration over which the inverse FFT is evaluated so providing a longer time to decay.

In many situations the impulse response extraction fails because the transfer function is non-causal. This means that it has a response in negative time. Non-causal transfer functions can be made causal by adding a delay.

#### **Impulse Response Testing**

If the inverse FFT method or Stehfest methods are used to extract the impulse response, the result is tested before allowing it to be used for the simulation.

The Stehfest method is tested by performing a spot frequency check. That is the impulse response is used to measure the gain of a sequence of sine waves in the time domain to check that the magnitudes match to that predicted in the frequency domain. The parameters IMPULSE\_TEST\_FMAX and IMPULSE\_TEST\_FMIN determine the range of frequencies used.

The inverse FFT method may be tested by one of two methods determined by the IMPULSE\_IFFT\_TEST\_METHOD parameter. If set to 0, the spot frequency method as described above will be used. If set to 1, the default, the impulse response is tested by measuring its decay to zero. The inverse FFT method is accurate if the response decays to zero and this is used to test the result.

The tolerance required for the test is set by the IMPULSE\_TEST\_TOL parameter.

#### **Impulse Response Cache**

The impulse response is cached to speed up subsequent simulations with the same response. The cache is located here:

C:\Users\*login-name*\AppData\Roaming\SIMetrix Technologies\SIMetrix*vvv*\LaplaceCache

where *login-name* is the name used to log in to your system and *vvv* is the version, e.g. 830 for version 8.3. This can be deleted at any time. The cache is size limited to 250Mbytes by default. This can be changed using the option variable LaplaceCacheSizeMBytes. Type 'Set LaplaceCacheSizeMBytes=nnn' at the command line to set a new value.

The cache may be disabled by setting the IMPULSE\_ENABLE\_CACHE parameter to 0.

#### **Impulse Response Analytical Extraction**

The impulse response analytical extraction attempts to match the transfer function to one of the following patterns. The parameters  $a, b, c$  etc represent constant values.





The analytic matching algorithm will attempt to match partial expressions as well as the whole expression if they are combined by addition, subtraction or multiplication. For example:

$$
(1/(s+1)) * exp(-s)
$$

will be matched to the product of  $1/(s + 1)$  and  $exp(-s)$ . Respectively these have impulse responses of  $e^{-t}$  and  $\delta(1+t)$  and those two impulse responses will be convolved to yield the final result. Note that this only succeeds if all partial expressions can be matched analytically.

To exploit this method, ensure that the expression is entered in a manner that keeps each partial expression distinct. For example, the following would be matched correctly:

$$
1/(s+1) * 1/(s+2)
$$

as this would be seen as the two partial expressions  $1/(s+1)$  and  $1/(s+2)$  each of which can be resolved analytically. The final result would be obtained by convolving the two impulse responses.

However the following mathematically identical expression would not be matched:

 $1/((s + 1) * (s + 2))$ 

The analysis algorithm does not attempt to decompose denominator products so this will not be recognised analytically. The above would be extracted using inverse FFT which would usually be successful but
might not be if the run time is considerably shorter than the time constant.

### **4.26.7 Run Time Error Control**

During the simulation run the time step is controlled using a truncation error method. The tolerances used for this error control are set using the TRUNC\_RELTOL and TRUNC\_ABSTOL parameters. The truncation error test may be disabled altogether by setting the TRUNC\_TEST parameter to zero.

### <span id="page-108-0"></span>**4.26.8 PSpice LAPLACE and FREQ compatibility**

SIMetrix is compatible with PSpice Laplace transfer functions at the netlist level entered in one of these forms

```
Exxx n1 n2 LAPLACE { input_expression } { laplace_expression }
Gxxx n1 n2 LAPLACE { input_expression } { laplace_expression }
Exxx n1 n2 FREQ {input_expression} [keyword1] [keyword2] table_values DELAY=delay
Gxxx n1 n2 FREQ {input_expression} [keyword1] [keyword2] table_values DELAY=delay
```
Where:



SIMetrix will implement the PSpice expression in the best way possible. If the Laplace expression can be expressed as a quotient of polynomials, the lumped model (see [Laplace Transfer Function - Lumped](#page-94-0) [Implementation\)](#page-94-0) will be used instead of the convolution model as long as it does not contain any parameters.

# **4.27 Lossy Transmission Line**

### **4.27.1 SPICE3 LTRA Lossy Transmission Line**

The built-in lossy transmission line model is now obsolete and should not be used in new designs. It has been superseded by the subcircuit-based RLGC model. See below.

### **4.27.2 Subcircuit-based RLGC Model**

A subcircuit-based lossy transmission line model is also provided in the model library and accessible in the schematic editor from the menu system. The sub-circuit model uses the [Laplace Transfer Function](#page-100-0) [Convolution Implementation](#page-100-0) device as its base. The sub-circuit model is faster, more accurate and also supports both shunt and series losses. The subcircuit model may be entered using

Xxxx p1 n1 p2 n2 LOSSY\_LINE **params**:

```
+ C=cap-per-unit-length
```

```
+ L=ind-per-unit-length
```

```
+ G=shunt-conductance-per-unit-length
```

```
+ R=series-r-per-unit-length LENGTH=length
```
# **4.28 MOSFET**

Note

Level 1, 2, 3 and 17 MOSFETs are described in this section. For other devices:

[BSIM3](#page-115-0) [BSIM4](#page-117-0) [HiSim HV](#page-119-0)

**[PSP](#page-120-0)** 

MOS9, MOS11 and other NXP devices see [NXP Compact Models](#page-149-0)

# **4.28.1 Netlist Entry**

```
Mxxxx drain gate source bulk modelname [L=length] [W=width]
+ [AD=drain_area] [AS=source_area]
+ [PD=drain_perimeter] [PS=source_perimeter]
+ [NRD=drain_squares] [NRS=source_squares]
+ [NRB=bulk_squares]
+ [OFF] [IC=vds,vgs,vbs] [TEMP=local_temp] [M=area]
```


(The following 8 parameters are not supported by the level 17 MOSFET model)



- *dtemp* Differential temperature. Similar to local\_temp but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence. Currently implemented only for LEVEL 1,2 and 3.
- Notes SIMetrix supports four types of MOSFET model specified in the model definition. These are referred to as levels 1, 2, 3 and 7. Levels 1,2, and 3 are the same as the SPICE2 and SPICE3 equivalents. Level 17 is proprietary to SIMetrix. For further information see Level 17 MOSFET parameters below.

## **4.28.2 NMOS Model Syntax**

**.model** modelname NMOS ( level=level\_number parameters )

### **4.28.3 PMOS Model Syntax**

**.model** modelname PMOS ( level=level\_number parameters )

## **4.28.4 MOS Levels 1, 2 and 3: Model Parameters**







### **4.28.5 CJ Default**

If not specified CJ defaults to

 $\sqrt{\epsilon_s q \times \text{NSUB} \times 1}$ e $6/(2 \times \text{PB})$ 

where

 $\epsilon_s = 1.03594314e-10$  (permittivity of silicon)

q = 1.6021918e-19 (electronic charge)

NSUB, PB model parameters

### **4.28.6 Gate Charge Model, Levels 1, 2 and 3**

Two gate charge models are available for MOS Levels 1, 2 and 3 selectable by the .OPTIONS setting SPICEMOSCHARGEMODEL:

**.OPTIONS** SPICEMOSCHARGEMODEL=0|1

The option value is defined as follows:



1 Yang-Chatterjee charge model. This is the model used by PSpice. It is charge based and as such does correctly conserve charge

MOS level 1-3 models are predominantly used as part of many manufacturer-designed power MOS and IGBT subcircuit models. In most cases the choice of gate charge model is unimportant. However, for a few models, the results vary significantly with the choice of model used. Most models are designed for PSpice and so the safest choice is the Yang-Chatterjee charge model

(**.OPTIONS** SPICEMOSCHARGEMODEL=1). However, SIMetrix version 8.0 and earlier do not support this model so for compatibility with earlier versions the Meyer capacitance model is the default.

The setting **. OPTIONS** SPICECOMPATIBILITY=2 automatically enables the Yang-Chatterjee charge model as the default.

### **4.28.7 Notes for levels 1, 2 and 3:**

The three levels 1 to 3 are as follows:

LEVEL 1 Shichman-Hodges model. The simplest and is similar to the JFET model



The L and W parameters perform the same function as the L and W parameters on the device line. If omitted altogether they are set to the option values (set with [.OPTIONS](#page-250-0) statement) DEFL and DEFW respectively. These values in turn default to 100 microns.

The above models differ from all other SIMetrix (and SPICE) models in that they contain many geometry relative parameters. The geometry of the device (length, width etc.) is entered on a per component basis and various electrical characteristics are calculated from parameters which are scaled according to those dimensions. This is approach is very much geared towards integrated circuit simulation and is inconvenient for discrete devices. If you are modelling a particular device by hand we recommend you use the level 17 model which is designed for discrete vertical devices.

## **4.28.8 MOS Level 17: Model Parameters**





### **4.28.9 Notes for level 17**

In SIMetrix version 5.2 and earlier, this model used a level parameter value of 7 instead of the current 17. The number was changed so that a PSpice compatible BSIM3 model (level=7) could be offered. In order to retain backward compatibility, any level 7 model containing the parameters cgdmax, cgdmin, xg1cgd, xg2cgd or vtcgd will automatically be switched to level=17.

The level 17 MOSFET was developed to model discrete vertical MOS transistors rather than the integrated lateral devices that levels 1 to 3 are aimed at. Level 17 is based on level 1 but has the following important additions and changes:

- New parameters to model gate-drain capacitance
- 2 new parameters to model rdson variation with temperature.
- All parameters are absolute rather than geometry relative. (e.g. capacitance is specified in farads not farads/meter)

All MOSFET models supplied with SIMetrix are level 17 types. Many models supplied by manufacturers are subcircuits made up from a level 1, 2 or 3 device with additional circuitry to correctly model the gate-drain capacitance. While the latter approach can be reasonably accurate it tends to be slow because of its complexity.

Gate-drain capacitance equation:

$$
C_{gd} = \left(0.5 - \frac{1}{\pi} \tan^{-1} \left( \left(\text{VTCGD} - v\right) - \text{XG1CGD} \right) \right) \text{CGDMIN} + \left(0.5 - \frac{1}{\pi} \tan^{-1} \left( \left(\text{VTCGD} - v\right) \text{XG2CGD} \right) \right) \text{CGDMAX}
$$

where v is the gate-drain voltage. This is an empirical formula devised to fit measured characteristics. Despite this it has been found to follow actual measured capacitance to remarkable accuracy.

To model gate-drain capacitance quickly and to acceptable accuracy set the five  $C_{gd}$  parameters as follows:

- 1. Set CGDMIN to minimum possible value of  $C_{gd}$  i.e. when device is off and drain voltage at maximum.
- 2. Set CGDMAX to maximum value of  $C_{gd}$  i.e. when device is on with drain-source voltage low and gate-source voltage high. If this value is not known use twice the value of  $C_{gd}$  for  $V_{gd} = 0$ .
- 3. Set XG2CGD to 0.5, XG1CGD to 0.1 and leave VTCGD at default of 0.

Although the parasitic reverse diode is modelled, it is connected inside the terminal resistances, RD and RS which does not represent real devices very well. Further, parameters such as transit time (TT) which model the reverse recovery characteristics of the parasitic diode are not included. For this reason it is recommended that the reverse diode is modelled as an external component. Models supplied with SIMetrix are subcircuits which include this external diode.

# <span id="page-115-0"></span>**4.29 BSIM3 MOSFETs**

## **4.29.1 Notes**

The BSIM3 model is available with *Pro* and *Elite* versions of SIMetrix. Two versions are supplied namely 3.24 and 3.3.

BSIM3 models can be accessed using one of four values for the LEVEL parameter:

LEVEL=7 specifies a PSpice compatible model

LEVEL=8 specifies the standard Berkeley BSIM3 model.

LEVEL=49 specifies the Hspice® implementation using the Hspice® junction capacitance model.

LEVEL=53 is also a Hspice® version but uses the standard Berkeley junction cap model.

The following PSpice parameters are supported when using level 7: TT, L, W, RG, RD, RS, RB, RDS, JSSW

The following Hspice® parameters are supported when using level 49/53: CJGATE, HDIF, LDIF, WMLT, XL, XW, IS, N, NDS, VNDS, PHP, LMLT, CTA, CTP, PTA, PTP, TREF, RD, RS, RDC, RSC, CBD, CBS, FC, TT, LD, WD, EG, GAP1, GAP2, XLREF, XWREF, ACM, CALCACM, TLEV, TLEVC

The Hspice® noise model is also supported for NLEV=0,1 and 2.

The 'M' instance parameter has also been implemented with all variants. This specifies the number of equivalent parallel devices.

Additional temperature parameters: All variants support the TEMP and DTEMP instance parameters. TEMP specifies absolute temperature (Celsius) while DTEMP specifies the temperature relative to the circuit global temperature.

All variants support the model parameters T\_MEASURED (equivalent to TNOM), T\_ABS (as TEMP instance parameter) and T\_REL\_GLOBAL (as DTEMP instance parameter)

## **4.29.2 Version Selector**

The VERSION parameter can be specified to select which version is used. As detailed above, SIMetrix supports three different BSIM3 versions although 8 versions have been released by Berkeley. The following table shows which version will actually be used according to the VERSION parameter value.



Note that a second decimal point will be ignored so 3.2.4 is the same as 3.24. If the version parameter is set to a value not listed above, SIMetrix will raise an error condition. This can be overridden by setting .OPTIONS AnyVersion.

## **4.29.3 Model Parameters**

The parameters describing BSIM3 are documented in the original Berkeley manual. See below. The following table lists parameters that are non-standard.



# **4.29.4 Further Documentation**

Original Berkeley documentation may be found at our web site. Please visit [Further Documentation](#page-55-0) for details.

## **4.29.5 Process Binning**

BSIM3 devices may be binned according to length and width. Refer to [Model Binning](#page-49-0) for details.

# <span id="page-117-0"></span>**4.30 BSIM4 MOSFETs**

### **4.30.1 Notes**

The BSIM4 model is only available with the *Elite* versions of SIMetrix.

BSIM4 models are accessed using LEVEL=14.

Versions 4.21, 4.3, 4.4, 4.5, 4.60, 4.61, 4.62, 4.63, 4.64, 4.65, 4.70 and 4.80 are currently supported. To set the version to be used, use the VERSION parameter as defined in the following table:



Note that a second decimal point will be ignored so 4.2.1 is the same as 4.21. If the version parameter is set to a value not listed above, SIMetrix will raise an error condition. This can be overridden by setting .OPTIONS AnyVersion.

The implementation is standard Berkeley but with the addition of the 'M' instance parameter which specifies the number of equivalent parallel devices.

## <span id="page-117-1"></span>**4.30.2 Further Documentation**

Original Berkeley documentation is provided at our web site. Please visit [Further Documentation](#page-117-1) for details. Note the document covers version 4.70 of the model. Earlier versions are available from the BSIM3/4 web site at *[BSIM Reference](http://www.simetrix.co.uk/app/ext/bsim.htm)*.

## **4.30.3 Process Binning**

BSIM4 devices may be binned according to length and width. Refer to [Model Binning](#page-49-0) for details. Note the multi-fingered devices are binned according to width per finger.

### **4.30.4 Mapping to Level 54 for Hspice**

Hspice uses Level 54 to define BSIM4 MOSFETs whereas the SIMetrix level is 14. The HSPICEMODELS option setting may be used to change this:

**.OPTIONS** HSPICEMODELS=1

This setting also has the same effect:

**.OPTIONS** HSPICECOMPATIBILITY=1

See [.OPTIONS](#page-250-1) for more details

# **4.31 BSIM-BULK MOSFET (formerly BSIM6)**

The BSIM-BULK model is available with the *Elite* versions of SIMetrix

The BSIM-BULK MOSFET model is designed for integrated circuit development for analog and RF applications. The BSIM-BULK model was developed by The BSIM Group, located in the Department of Electrical Engineering and Computer Sciences (EECS) at the University of California, Berkeley.

Documentation for the model may be found at the SIMetrix web site. See [Further Documentation](#page-55-0)

### **4.31.1 Netlist Entry**

Mxxx drain gate source bulk [temperature] modelname instance\_parameters

### **4.31.2 NMOS Model Syntax**

**.model** modelname NMOS ( LEVEL=77 VERSION=106 parameters )

### **4.31.3 PMOS Model Syntax**

**.model** modelname PMOS ( LEVEL=77 VERSION=106 parameters )

### **4.31.4 Notes**

One version of the model is currently available. This is version 106.2. This may be accessed using parameters LEVEL=77 and VERSION=106.

The device may have 4 or 5 terminals with the netlist format as shown above.

Self heating will be modelled if the parameter SHMOD is non-zero and RTH0 is greater than zero. If the temperature node is present it can be used to add a thermal network. If omitted, an internal temperature node labelled *t* will be used to implement self-heating effects. This node can be probed using the name *REF*#t. For example, if the device has the reference M23, the internal temperature node may be accessed using the name M23#t. To access internal nodes the KeepInternal option setting must be set. See [Option](#page-235-0) **[Settings](#page-235-0)** 

This model may be binned on length and width in a similar manner to the BSIM3 model. See [Model](#page-49-0) [Binning.](#page-49-0)

# **4.32 BSIM-CMG MOSFET (FinFET)**

The BSIM-CMG model is available with the *Elite* versions of SIMetrix

The BSIM-CMG MOSFET model is designed for sub 20nm integrated circuit geometries using FinFET technology. The BSIM-CMG model was developed by The BSIM Group, located in the Department of Electrical Engineering and Computer Sciences (EECS) at the University of California, Berkeley.

Documentation for the model may be found at the SIMetrix web site. See [Further Documentation](#page-55-0)

### **4.32.1 Netlist Entry**

Mxxx drain gate source bulk [temperature] modelname instance\_parameters

### **4.32.2 NMOS Model Syntax**

**.model** modelname NMOS ( LEVEL=72 VERSION=111 parameters )

### **4.32.3 PMOS Model Syntax**

**.model** modelname PMOS ( LEVEL=72 VERSION=111 parameters )

### **4.32.4 Notes**

One version of the model is currently available. This is version 111.0. This may be accessed using parameters LEVEL=72 and VERSION=111.0

The device may have 4 or 5 terminals with the netlist format as shown above.

Self heating will be modelled if the parameter SHMOD is non-zero and RTH0 is greater than zero. If the temperature node is present it can be used to add a thermal network. If omitted, an internal temperature node labelled *t* will be used to implement self-heating effects. This node can be probed using the name *REF*#t. For example, if the device has the reference M23, the internal temperature node may be accessed using the name M23#t. To access internal nodes the KeepInternal option setting must be set. See [Option](#page-235-0) **[Settings](#page-235-0)** 

This model may be binned on length and number of fins (NFIN). See [Model Binning](#page-49-0) for details about binning. Bining model parameters are LMIN, LMAX, NFINMIN and NFINMAX.

# <span id="page-119-0"></span>**4.33 HiSim HV MOSFET**

The HiSim HV model is available with the *Elite* versions of SIMetrix.

The HiSim HV MOSFET model is model designed for integrated circuit design and is used in many PDKs from IC foundries. The HiSim HV model was developed by the University of Hiroshima.

Documentation for the model may be found at the SIMetrix web site. See [Further Documentation](#page-55-0)

### **4.33.1 Netlist Entry**

Mxxx drain gate source bulk [ substrate [ temperature ]] modelname instance\_parameters

## **4.33.2 NMOS Model Syntax**

**.model** modelname NMOS ( LEVEL=level VERSION=version parameters )

### **4.33.3 PMOS Model Syntax**

**.model** modelname PMOS ( LEVEL=level VERSION=version parameters )

See notes below for values of level and version.

### **4.33.4 Notes**

Five versions of the HiSim HV model are available:



The device may have 4 to 6 terminals with the netlist format is shown below.

Mxxx drain gate source bulk [ substrate [ temperature ]] modelname instance\_parameters

With 4 terminals connected, substrate effect must be disabled by setting parameter COSUBNODE=0. If the parameter COSELFHEAT is set to 1, self heating will be modelled using an internal temperature node labelled *temp*. The internal node can be probed using the name *REF*#temp. For example, if the device has the reference M23, the internal temperature node may be accessed using the name M23#temp. To access internal nodes the KeepInternal option setting must be set. See [Option Settings](#page-235-0)

With 5 terminals connected the behaviour of the model is slightly different between versions. With version 2.1 and greater, the 5th terminal may be configured to be either the substrate node or the temperature node. If parameter COSUBNODE=1, the substrate node will be enabled and if self-heating is active, the temperature node will be internal as described for four terminals above. If parameter COSUBNODE=0, the 5th terminal becomes the temperature node and substrate effect will be inactive.

With 5 terminals connected for version 1.2.1, the fifth terminal is only active if COSUBNODE=1. If parameter COSUBNODE=0 this connection is simply connected to ground through a zero-volt voltage source. In both cases the temperature node is internal.

With all 6 terminals connected the parameter COSUBNODE must be set to 1.

Note that if the temperature node is used (5 or 6 terminals) the vecror name *REF*#temp will return the 'current' (i.e. the thermal power flow) into the temperature pin.

This model may be binned on length and width in a similar manner to the BSIM3 model. See [Model](#page-49-0) [Binning.](#page-49-0)

# <span id="page-120-0"></span>**4.34 PSP MOSFET**

The PSP model is available with the *Elite* versions of SIMetrix.

### **4.34.1 Netlist Entry**

Mxxxx drain gate source bulk modelname [instance\_parameters]

#### Where:



Refer to PSP documentation (see below) for further details.

### **4.34.2 NMOS Model Syntax Version 101.0**

MODEL modelname NMOS LEVEL=1010 parameters

#### OR

**.MODEL** modelname PSP101 type=1 parameters

## **4.34.3 PMOS Model Syntax Version 101.0**

**.MODEL** modelname PMOS LEVEL=1010 parameters

#### OR

**.MODEL** modelname PSP101 type=-1 parameters

### **4.34.4 NMOS Model Syntax Version 102.3**

MODEL modelname NMOS LEVEL=1023 parameters

#### OR

**.MODEL** modelname PSP102 type=1 parameters

### **4.34.5 PMOS Model Syntax Version 102.3**

**.MODEL** modelname PMOS LEVEL=1023 parameters

#### OR

**.MODEL** modelname PSP102 type=-1 parameters

Refer to PSP documentation (see below) for details of parameters

### **4.34.6 Notes**

This is a model jointly developed by NXP (formerly Philips Semiconductor) and Pennsylvania State University.

Two versions are provided:

- 1. 101.0, non-binning, non-NQS geometric version.
- 2. 102.3, non-binning, non-NQS geometric version.

The model was implemented from the Verilog-A description.

Other versions of the PSP model are available from the NXP SIMKIT devices. See [SIMKIT Devices.](#page-149-1)

Documentation for the model may be found at our web site. Please refer to [Further Documentation](#page-55-0) for details.

# **4.35 MOSFET GMIN Implementation**

GMIN is a conductance added to all non-linear devices to improve DC convergence. For LEVEL 1-3 and LEVEL 17 MOSFETs, the default GMIN is implemented as shown below:



This is compatible with SPICE and earlier versions of SIMetrix.

For BSIM3 and BSIM4 devices, and also for LEVEL1-3 and LEVEL 17 devices if the NEWGMIN .OPTIONS setting is set, the GMIN implementation is:



OLDMOSGMIN is a .OPTIONS setting with the default value of zero. MOSGMIN is also a .OPTIONS setting with the default value of GMIN. Using the above configuration with OLDMOSGMIN = 0 often converges faster especially if the Junction GMIN stepping algorithm is used.

# **4.36 Resistor**

# **4.36.1 Netlist Entry**

Rxxxx n1 n2 [model\_name] [value] [L=length] [W=width] [ACRES=ac\_resistance] [TEMP=local\_temp] [TC1=tc1] [TC2=tc2] [M=mult] [DTEMP=dtemp]



## **4.36.2 Notes**

- If *model\_name* is omitted, *value* must be specified.
- If *model\_name* is present and *value* is omitted, *length* and *width* must be specified in which case the value of the resistance is RES \* RSH \* L/W where RSH is the sheet resistance model parameter and RES is the resistance multiplier. See model parameters below. If ACRES is specified and non-zero its value will be used unconditionally for AC analyses and the calculation of thermal noise.

### **4.36.3 Resistor Model Syntax**

**.model** modelname R ( parameters )

## **4.36.4 Resistor Model Parameters**





### **4.36.5 Notes**

The flicker noise parameters are proprietary to SIMetrix. Flicker noise voltage is:

$$
V_n^2 = \mathrm{KF}\cdot\mathrm{RSH}^2/(L\cdot W)\cdot V_r^2\cdot\Delta f/f^\mathrm{EF}
$$

Where:

 $V r =$  Voltage across resistor.

The equation has been formulated so that KF is constant for a given resistive material.

If one of L, W is not specified, the flicker noise voltage becomes:

$$
V_n^2 = \mathbf{K} \mathbf{F} \cdot \mathbf{R}^2 \cdot V_r^2 \cdot \Delta f / f^{\text{EF}}
$$

Where R is the final resistance.

i.e. the noise current is independent of resistance. This doesn't have any particular basis in physical laws and is implemented this way simply for convenience. When resistor dimensions and resistivity are unavailable, the value of KF will need to be extracted for each individual value.

# **4.37 Resistor - Hspice Compatible**

### **4.37.1 Netlist Entry**

Rxxxx n1 n2 [model\_name] [value] [L=length] [W=width] [AC=ac\_resistance] [TC1=tc1] [TC2=tc2] [M=mult] [SCALE=scale] [DTEMP=dtemp] [C=c]





# **4.37.2 Resistor Model Syntax**

**.model** modelname R (LEVEL=2 parameters )





# **4.37.3 Resistance Calculation**

In the following *reff* is the effective non-temperature adjusted resistance used for DC analyses, *reffac* is the effective non-temperature adjusted resistance used for AC analyses.

If instance resistance is specified:

 $reff = value \times SCALE/M$ 

### otherwise if *weff* \**leff* \*RSH>0

reff = SCALE\*RSH\*leff / (weff\*M)

#### where:

 $weff = SHRINK*W - 2*DW$ 

 $left =$  SHRINK\*L - 2\*DLR

#### otherwise

reff = SCALE\*RES/M

#### If instance AC parameter is specified:

raceff =  $AC*SCALE/M$ 

#### otherwise if RAC given

raceff = SCALE\*RAC/M

#### otherwise

raceff = reff

# **4.37.4 Capacitance Calculation**



*capeff* is the non temperature adjusted capacitance.

If instance parameter C is given:

 $capeff = M*SCALE*C$ 

#### otherwise if model parameter CAP is given

 $capeff = M*SCALE*CAP$ 

#### otherwise

capeff = (leffc\*weffc\*coxmod + 2\*((leffc+weffc)\*CAPSW))\*M\*SCALE

#### where:

 $left c =$  SHRINK\*L -  $2 * DL$  $weffc = SHRINK*W - 2*DW$ 

See below for *coxmod* calculation.

# **Calculation of COX**

#### If COX given

coxmod = COX

#### otherwise if THICK <> 0 AND DI<>0

coxmod =  $8.8542149e-012*DI/THICK$ 

#### otherwise if THICK <> 0 AND DI=0

 $cosmod = 3.453148e-011/THICK$ 

#### otherwise

 $covmod = 0.0$ 

### **4.37.5 Temperature Scaling**

### **Resistance**

 $R(t) = reff \cdot tscale$ 

#### where:

tscale = 1+(tclinst+tdelta\*tc2inst)\*tdelta

#### where

```
tdelta = tinst-TREF-273.15
```
tc1inst = if instance TC1 given: TC1 else TC1R

tc2inst = if instance TC2 given: TC2 else TC2R

tinst = [global circuit temperature] + DTEMP (Kelvin)

### **Capacitance**

```
C(t) = capeff * tscale
```
#### where

tcscale =  $1+(TC1C+tdelta*TC2C)*tdelta$ 

tdelta defined above.

## **4.37.6 Flicker Noise**

$$
I_n = \frac{{\rm K}{\rm F} \times I^{\rm AF}}{L_{\rm eff}^{\rm LF} \times W_{\rm eff}^{\rm WF} \times f^{\rm EF}}
$$

### <span id="page-128-1"></span>**4.37.7 ACRESMOD Parameter**

This parameter controls the calculation of resistance in AC analysis. With ACRESMOD=0 AC analysis uses the large signal resistance value, that is the value of resistance calculated during the DC analysis. If ACRESMOD=1, the small signal resistance is used, that is, the value of dv/di at the operating point. If the resistance is defined as an expression containing circuit variables (i.e. it is voltage dependent), the large signal resistance is different to the small signal resistance.

This resistor model has been developed primarily for compatibility with Hspice models. Hspice itself always uses the large signal resistance. However, this will create a discrepancy between AC analysis and a transient analysis of a small signal. To resolve this discrepancy, set ACRESMOD to 1.

In summary, to be compatible with Hspice, use ACRESMOD=0, for consistent results between AC and transient analyses, use ACRESMOD=1.

In noise analysis the large signal value is always used.

### <span id="page-128-0"></span>**4.37.8 Making the Hspice Resistor the Default**

This resistor model requires the specification of a model name and the creation of a .MODEL statement with LEVEL=2. This is likely to be inconvenient if a model file containing Hspice resistors is being used.

To overcome this, the HSPICEMODELS option setting may be used to make this resistor the default. Add this line to the netlist:

```
.OPTIONS HSPICEMODELS=1
```
This setting also has the same effect:

**.OPTIONS** HSPICECOMPATIBILITY=1

See [.OPTIONS](#page-250-1) for more details

# **4.38 CMC Resistor**

## **4.38.1 Netlist entry**

Uxxxx n1 nc n2 model\_name parameters

### **4.38.2 Model Format**

**.MODEL** model\_name R3\_CMC model\_parameters

Full details of this model can be found in the document r3\_cmc\_release1.0.0\_2007Jun12.pdf which may be found at our web site. Please refer to [Further Documentation](#page-55-0) for details.

# **4.39 Subcircuit Instance**

# **4.39.1 Netlist Entry**

Xxxxx n1 n2 n3 ... subcircuit\_name [pinnames: pin1 pin2 pin3 ...] [[**params**:] [M=m] expression1 expression2 ....]



See [Subcircuits](#page-46-0) for more information.

# **4.40 Transmission Line**

## **4.40.1 Netlist Entry**

```
Txxxx p1 n1 p2 n2 Z0=impedance [TD=delay] [F=frequency [NL=norm_length]]
   [rel=rel] [abs=abs]
```


TD takes precedence over NL/F. Either TD or F must be specified.

These remaining parameters control the way the line is simulated rather than its electrical characteristics. More accurate results (at the expense of simulation time) can be obtained by using lower values.



## **4.40.2 Example**



The above line has an impedance of 50 $\Omega$  and a delay of 1 $\mu$ S.

# **4.41 Voltage Controlled Current Source**

## **4.41.1 Netlist Entry**

Gxxxx nout+ nout- vc+ vc- [GAIN=]transconductance [GOUT=output\_conductance]





GOUT has a default value of zero unless the PSPICEGMIN option is set in which case it has a default value of GMIN. GMIN is set using ".OPTIONS GMIN=*value*" and has a default value of 1e-12.

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for IC's. (Most operational amplifier models for example use several polynomial sources). In general, however the [arbitrary source](#page-57-0) is more flexible and easier to use.

The netlist format for a polynomial source is:

```
Gxxxx nout+ nout- POLY( num_inputs ) vc1+ vc1- vc2+ vc2- ...
   + polynomial_specification
```


## **4.41.2 PSpice Syntax**

SIMetrix accepts PSpice syntax for arbitrary sources using VALUE, TABLE, Q and F operators. See [PSpice and Hspice Syntax](#page-61-0) for more details.

SIMetrix also accepts the PSpice LAPLACE and FREQ operators. See [PSpice LAPLACE and FREQ](#page-108-0) [compatibility](#page-108-0)

# **4.42 Voltage Controlled Switch**

# **4.42.1 Netlist Entry**

Sxxxx nout1 nout2 vc+ vc- modelname IC=ic



### **4.42.2 Voltage Controlled Switch Model Syntax**

**.model** modelname VSWITCH ( parameters )

**.model** modelname SW ( parameters )

# **4.42.3 Voltage Controlled Switch Model Parameters**



GIN has a default value of zero unless the PSPICEGMIN option is set in which case it has a default value of GMIN. GMIN is set using ".OPTIONS GMIN=*value*" and has a default value of 1e-12.

### **4.42.4 Voltage Controlled Switch Notes**

The voltage controlled switch has two modes of operation:

1. Continuous mode: Behaves like a voltage controlled resistor. Between VON and VOFF the resistance varies gradually following a cubic law as described with the following equation:

where:

$$
R = 1/exp(-Lm - Lr * factor * (1.5 - 2 * factor * factor))
$$
  
factor =  $V_{control} - 0.5$   

$$
Lm = -0.5 * ln(g_{on} * g_{off})
$$
  

$$
Lr = ln(g_{off}/g_{on})
$$
  

$$
g_{off} = ROFF < 0 : 1/ROFF, ROFF = 0 : GMIN
$$
  

$$
g_{on} = RON < 0 : 1/RON, RON = 0 : GMIN
$$

2. Hysteresis mode: Switches in a controlled time with a hysteresis characteristic. This mode is enabled if the VT parameter is defined. The switch transitions to the on state when:

$$
V_{control} > VT + VH
$$

and to the off state when:

 $V_{control} < VT - VH$ 

The transition will be delayed by TD and the transition time will be TON when changing from OFF state to ON state and TOFF when changing from ON state to OFF state.

The transition will follow the same characteristic as continuous mode. That is, during the transition period the actual resistance of the switch will follow the continuous mode characteristic with the control voltage following a linear transition between VON and VOFF.

Hysteresis mode is similar and usually compatible with what is known as short-transition mode in PSpice. The difference is that in short-transition mode, the switching time is uncontrolled whereas in SIMetrix hysteresis mode the transition time is controlled by the TON and TOFF parameters.

GMIN is a simulation parameter which defaults to 1.0E-12 but which can changed using the [.OPTIONS](#page-250-0) statement.

The SIMetrix voltage controlled switch is compatible with PSpice® but note that in hysteresis mode, the SIMetrix switches in a controlled time whereas the PSpice version switches abruptly.

# **4.43 Voltage Controlled Switch - Perfect**

## **4.43.1 Netlist Entry**

Uxxxx nout1 nout2 vc+ vc- modelname



## **4.43.2 Perfect Voltage Controlled Switch Model Syntax**

**.model** modelname perfect\_switch ( parameters )

### **4.43.3 Perfect Voltage Controlled Switch Model Parameters**



### **4.43.4 Perfect Voltage Controlled Switch Notes**

The perfect voltage controlled switch model has zero on resistance and infinite off resistance.

The resistance of the switch is defined as follows:

$$
V_{ramp} = \frac{V_c - VOFF}{VON - VOFF}
$$

$$
V_{ramp} \ge 1.0 : R_{switch} = 0.0
$$

$$
V_{ramp} \le 0.0 : R_{switch} = \infty
$$

$$
0.0 < V_{ramp} < 1.0 : R_{switch} = \frac{1.0 - V_{ramp}}{V_{ramp} \cdot RMD}
$$

Where:

 $V_c$  is the voltage between terminals vc+ and vc-

 $R_{switch}$  is the resistance connecting nout1 and nout2

VOFF, VON and RMID are model parameters as defined above

Note that the perfect voltage controlled switch model is noise-free

# **4.44 Voltage Controlled Voltage Source**

### **4.44.1 Netlist Entry**

Exxxx nout+ nout- vc+ vc- gain



SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for ICs. (Most opamp models for example use several polynomial sources). In general, however the arbitrary source is more flexible and easier to use.

The netlist format for a polynomial source is:

```
Exxxx nout+ nout- POLY( num_inputs ) vc1+ vc1- vc2+ vc2-
  ... polynomial_specification
```


## **4.44.2 PSpice Syntax**

SIMetrix accepts PSpice syntax for arbitrary sources using VALUE, TABLE, Q and F operators. See [PSpice and Hspice Syntax](#page-61-0) for more details.

SIMetrix also accepts the PSpice LAPLACE and FREQ operators. See [PSpice LAPLACE and FREQ](#page-108-0) [compatibility](#page-108-0)

# **4.45 Voltage Source**

# **4.45.1 Netlist Entry**

```
Vxxxx n+ n- [[DC] dcvalue] [DCOP] [INFCAP] [AC magnitude [phase]]
  [transient_spec]
```




# <span id="page-135-0"></span>**4.45.2 Pulse Source**

PULSE ( v1 v2 [td [tr [tf [pw [per ]]]]] )

Where:





- a. *Time step* is set up by the .TRAN simulator statement which defines a transient analysis. Refer to [.TRAN.](#page-285-0)
- b. *Stop time* refers to the end time of the transient analysis.

SIMetrix deviates from standard SPICE in the action taken for a pulse width of zero. Standard SPICE treats a zero pulse width as if it had been omitted and changes it to the stop time. In SIMetrix a zero pulse width means just that.

Both the above examples give a pulse lasting  $5\mu$ S with a period of 10 $\mu$ S, rise and fall times of 100nS and a delay of 0. The voltage source has a 0V base line and a pulse of 5V while the current source has a 0mA base line and a pulse of 1mA.



## **Examples**



## <span id="page-136-0"></span>**4.45.3 Piece-Wise Linear Source**

PWL ( t1 v1 [t2 v2 [t3 v3 [... ]]] )

Each pair of values (*ti vi*) specifies that the value of the source is *vi* at time  $= ti$ . The value of the source at intermediate values of time is determined by using linear interpolation on the input values.

Although the example given below is for a voltage source, the PWL stimulus may be used for current sources as well.

### **Example**



Gives:



# <span id="page-137-0"></span>**4.45.4 PWL File Source**

PWLFILE filename

This performs the same function as the normal piece wise linear source except that the values are read from a file named *filename*.

The file contains a list of time voltage pairs in text form separated by any whitespace character (space, tab, new line). It is not necessary to add the '+' continuation character for new lines but they will be ignored if they are included. Any non-numeric data contained in the file will also be ignored.

### **Notes**

The PWLFILE source is *considerably* more efficient at reading large PWL definitions than the standard PWL source. Consequently it is recommended that all PWL definitions with more than 200 points are defined in this way.

The data output by Show /file is directly compatible with the PWLFILE source making it possible to save the output of one simulation and use it as a stimulus for another. It is recommended, however, that the results are first interpolated to evenly spaced points using the Interp() function.

The use of engineering suffixes (e.g. k, m, p etc.) is *not* supported by PWLFILE.

The PWLFILE source is a feature of SIMetrix and does not form part of standard SPICE.

Note, you can use the simulator statements .FILE and .ENDF to define the contents of the file. E.g.

```
Vpwl1 N1 N2 PWLFILE pwlSource
...
.FILE pwlSource
...
...
.ENDF
```
This will be read in much more efficiently than the standard PWL and is recommended for large definitions. See [.FILE and .ENDF.](#page-225-0)

# <span id="page-138-0"></span>**4.45.5 Sinusoidal Source**

SIN[E] ( vo va [freq [delay [theta [ phase]]]] )

Where:



a. *Stop time* refers to the end time of the transient analysis.

The shape of the waveform is described by:



# **Example**



Gives output of:



# <span id="page-139-0"></span>**4.45.6 Exponential Source**

```
EXP ( v1 v2 [td1 [tau1 [td2 [tau2 ]]]] )
```
Where:



a. Time step is set up by the .TRAN simulator directive which defines a transient analysis. Refer to [.TRAN.](#page-285-0)

Defined by:

```
0 to td1: v1td1 to td2: v1 + (v2 - v1) \cdot [1 - e^{-(t - td1)/tau1}]td2 to stop time: v1 + (v2 - v1) \cdot [1 - e^{-(t - td1)/tau1}] + (v2 - v1) \cdot [1 - e^{-(t - td2)/tau2}]
```
### <span id="page-140-0"></span>**4.45.7 Single Frequency FM**

SFFM ( vo va [fc [mdi [fs ]]] )

Where:



a. *Stop time* refers to the end time of the transient analysis.

Defined by:  $vo + va \cdot \sin[2\pi \cdot fc \cdot t + mdi \cdot \sin(2\pi \cdot fs \cdot t)]$ 

### <span id="page-140-1"></span>**4.45.8 Noise Source**

noise interval rms\_value [start\_time [stop\_time]]

Source generates a random value at *interval* with distribution such that spectrum of signal generated is approximately flat up to frequency equal to 1/(2\**interval*). Amplitude of noise is *rms\_value* volts. *start\_time* and *stop\_time* provide a means of specifying a time window over which the source is enabled. Outside this time window, the source will be zero. If *stop\_time* is omitted or zero a value of infinity will be assumed.

# **4.45.9 Extended PWL Source**

```
PWLS [TIME_SCALE_FACTOR=time_factor] [VALUE_SCALE_FACTOR=value_factor]
   pwls_spec [ pwls_spec ... ]
```
Where:





# **Sine Parameters**



The sine value is defined as follows:

```
if t>0 OR DELAY<0
  PEAK * SIN(f*2pi*t+PHASE*pi/180) + OFFSET
else
  PEAK * SIN(PHASE*pi/180) + OFFSET
```
#### Where:

 $f = \text{FREQ} + t \times \text{RAMP}$ 

t = *time* - *tref* - DELAY

*time* is the global simulation time

*tref* is the reference time for this spec

# **Pulse Parameters**



RISE, FALL, WIDTH and PERIOD must be greater than zero. DELAY must be greater than or equal to zero

## **WAV Parameters**



Reads a WAV format data file. WAV is a format used generally for sampled audio data. SIMetrix can read these files subject to these conditions:

No more than 2 channels

Bits per sample is 8, 16, 24 or 32

Data is uncompressed

# **4.46 Mutual Inductor**

Specifies coupling between two inductors.

# **4.46.1 Netlist Entry**

Kxxxx L1 L2 [L3...] coupling\_factor





If mutual inductance is M then:

$$
v_{L_1} = L_1 \frac{di_{L_1}}{dt} + M \frac{di_{L_2}}{dt}
$$

$$
v_{L_2} = L_2 \frac{di_{L_2}}{dt} + M \frac{di_{L_1}}{dt}
$$

$$
K = \frac{M}{\sqrt{L_1 \cdot L_2}}
$$

K cannot be greater than 1.

### **4.46.2 Notes**

You can only couple ideal inductors using this method. The saturable inductor devices may not be coupled in this way. See [Inductor \(Saturable\)](#page-86-0) for more information.

To use the mutual inductor directly on a schematic you will need to add the device line to the netlist. See [Adding Extra Netlist Lines](#page-17-0) for information about how to do this.

If it is desired to couple more than two inductors and different coupling factors are required for certain combinations, you can enter multiple K devices to define the coupling between inductors. However, a coupling factor must be defined for every combination of inductor pairs. For example, with three inductors, there must be a definition for L1-L2, L2-L3 and L1-L3.

For iron cored transformers values of K between 0.99 and 0.999 are typical. For ferrites lower values should be used. If the windings are concentric (i.e. one on top of the other) then 0.98 to 0.99 are reasonable. If the windings are side by side on a sectioned former, K values are lower - perhaps 0.9 to 0.95. The addition of air gaps tends to lower K values.

## **4.46.3 Example**

A transformer with 25:1 turns ratio and primary inductance of 10mH

```
** Inductors
Lprimary N1 N2 10m
Lsecondary N3 N4 16u
** Coupling of 0.99 typical for ungapped ferrite
K1 Lprimary Lsecondary 0.99
```
## **4.47 Verilog-HDL Interface (VSXA)**

#### **4.47.1 Overview**

The VSXA device provides digital functionality defined by a Verilog-HDL definition. The connections to the VSXA device map directly to input and output ports defined within the Verilog-HDL module and may be connected to analog or digital SIMetrix components or other VSXA devices.

The Verilog-HDL simulation is performed by an external Verilog simulator and at least one such simulator is supplied with SIMetrix and is pre-installed with no additional setup or configuration required. Communication between the external Verilog-HDL simulator is achieved through the VPI programming interface and in principle this can allow any VPI compliant Verilog-HDL simulator to be used for this purpose.

This section describes details of the VSXA device. For more general information about using the Verilog-HDL feature, refer to Chapter 13 in the User's Manual.

#### **Netlist**

Uxxxx nodes modelname



### **Model Syntax**

MODEL modelname vsxa parameters







As well as the above parameters, you can also define values for parameters declared in the associated Verilog file. These carry the same name as the Verilog parameter.

## **4.47.2 Analog Input Interface**

Any port in the Verilog definition that is defined as an input will be treated by the analog simulator as a VSXA input connection. This has the following characteristics:

1. Input resistance equal to the value of the *in\_res* model parameter.

- 2. Detects a logic one when the input signal rises above a voltage equal to the *in\_high* model parameter.
- 3. Detects a logic low when the input signal drops below a voltage equal to the *in\_low* model parameter.
- 4. When the input voltage is between the *in\_low* and *in\_high* values, the signal detected will be the most recent value detected, that is it will hold its value like a schmitt trigger. For DC and t=0 the value will be that defined by the PORTINIT parameter. This is logic zero by default. A PORTINIT value of 1 will set this to logic one and any other value will set it to an unknown state.
- 5. The analog system will only send an UNKNOWN state to a Verilog input if the DC voltage lies between the thresholds and the corresponding PORTINIT value is other than 0 or 1. Once an input has acquired a logic zero or logic one state, it will thereafter behave as a schmitt trigger.

Important: VSXA inputs that are only connected to other VSXA inputs and no more than one VSXA output are implemented entirely within the Verilog domain and are not connected to the analog simulator. The digital data for such connections is nevertheless made available. See for further details.

#### **4.47.3 Analog Output Interface**

Any port in the Verilog definition that is defined as an output will be treated by the analog simulator as a VSXA output connection. This is modelled as shown in the following diagram:



Each switch has an on state resistance of OUT\_RES and an off state resistance of OUT\_RES\_HIZ. In the logic one state, S1 is on, in the logic zero state S2 on, while in the high-impedance state, neither switch is on. When transitioning from one state to another state, each switch's resistance changes linearly to the new state's value in the time determined by the parameters T\_RISE and T\_FALL.

Important: A VSXA output that is only connected to VSXA inputs is implemented entirely within the Verilog domain and are not connected to the analog simulator.

#### **4.47.4 Data Vector Output**

#### **Voltage Data**

Connections between VSXA devices and any other SIMetrix device (including non-Verilog digital devices) are analog nodes in every way and will generate voltage data vectors in the usual way.

Connections between VSXA devices *and* other VSXA devices that do not connect to anything else and do not connect more than one Verilog module output port are implemented entirely within the Verilog simulator domain and do not interface to the analog simulator. For such connections, digital data vectors are created. These transition between the values OUT\_LOW and OUT\_HIGH with rise and fall times equal to the timing resolution set by the VerilogResolution option setting. This defaults to 1fs.

In some situations it is possible that the overhead of creating this data could slow down the simulation. This would be the case where such internally connected signals carry high speed data that is much faster than the analog time steps. In these cases the output of this data can be disabled using the DISABLE\_INTERNAL\_VECTORS parameter for the VSXA device that carries the output driving port. They can also be globally disabled using the VerilogDisableInternalVectors [.OPTIONS](#page-250-0) setting.

#### **Current Data**

VSXA devices generate current vectors in the normal way for all connections that connect to analog signals. These vectors are named as follows:

```
ref#port_name
```
In the case of vector ports port name is the name of the port appended with the index of the wire within the port. For example, with the following Verilog definition:

```
module adder(in1, in2, out) ;
   input [3:0] in1 ;
   input [3:0] in2 ;
   output [3:0] out ;
```
the *port\_names* for the out port would be out0, out1, out2 and out3.

#### **4.47.5 Module Cache**

#### **Operation**

Before starting a simulation and also when creating a symbol from a Verilog design, SIMetrix needs to gather some information about each Verilog module used in the circuit. It does this by starting a Verilog simulation then interrogating the Verilog simulator via VPI. This process can take some time if there are many Verilog modules in the circuit. To speed things up, SIMetrix caches the information obtained for future use.

The cache mechanism calculates the MD5 checksum of the Verilog file and stores this with the cached information in the cache file. When the cached information is required, SIMetrix calculates the MD5 checksum of the Verilog file and looks to see whether there is a cache item with that MD5 value. If there is, it will use the cached data. If not it will retrieve the information via the Verilog simulator.

#### **Location**

The cache file is located at *vldatapath*/module-cache.sxche

Where *vldatapath* is a directory defined by the VlDataPath global option setting. This can be set using the Set command typed at the command line. E.g.

Set VlDataPath=path

The default value of *path* is:

*simetrix\_app\_data\_dir*/veriloghdl

*simetrix app data dir* is the directory where SIMetrix configuration settings are stored and defaults to C:\Users\*login-name*\AppData\Roaming. Refer to *User's Manual/Sundry Topics/Configuration Settings/Application Data Directory* for details about the Application Data path *simetrix\_app\_data\_dir*.

Be aware that this file is created when a simulation is closed. This takes place when a new simulation is started, when the Reset script command is executed or when the simulator process terminates.

#### **Limitations**

The cache mechanism only looks at the contents of the Verilog file referenced. It does not take account of include files for example. However, the only information stored in the cache are the module name, names and direction of the module ports and the names, types and default values of any parameters. It would be ususual to store these items in an include file but of course this is perfectly legal.

If the top level ports or/and parameters for your Verilog design are nor defined in the main file but in an include file, then you should either redesign the Verilog file or alternatively disable the cache for that module.

The cache can be disabled by setting the DISABLE\_MODULE\_CACHE model parameter. **Important:** the DISABLE\_MODULE\_CACHE parameter disables the creation of cached information; it does not disable using cached information if it already exists. This is because the cache is read before model parameters are read. You may wish to clear the cache altogether when setting this parameter. This can be done from the front end with menu **Verilog | Clear Verilog-HDL Module Info Cache**.

The cache can also be globally disabled using the [.OPTIONS](#page-250-0) setting VerilogDisableModuleCache.

## **4.48 NXP Compact Models**

#### **4.48.1 Introduction**

SIMetrix supports a range of device models developed by NXP Semiconductor. These are available with the *Elite* versions of SIMetrix

The table below shows the models available. Model statements should be in the form:

**.model** model\_name model\_type\_name LEVEL=level\_number parameters

E.g.

**.model** my\_model nmos LEVEL=103 ...

defines a MOS 9 nmos device.

To instantiate the device line must start with the letter as defined in the Device Letter column in the table below. The number of nodes must be within the range specified in the table.

#### **4.48.2 SIMKIT Devices**

The following table shows all available SIMKIT NXP models













### **4.48.3 Notes on SIMKIT Models**

#### **Binned Models**

Binned models are not yet integrated with the library binning system. So, to use the binning features of binned models, you will need to manually generate separate model names for each bin.

#### **Real Time Noise**

Some models do not fully implement real-time noise. Many MOS models include frequency dependent gate noise and this is not included in real-time noise analyses. Also some models include correlated noise which is also not included. In most cases these effects are small anyway and have little effect.

You can set this option in AC small-signal noise:

**.options** noMos9GateNoise

to disable the same effects in AC small signal noise. A comparison can then be made to estimate the effect these noise sources may have in real-time noise. Although the option name suggests that it only applies to MOS9, this does in fact work with all applicable models.

In the case of PSP 102 models, you can instead invoke the Verilog-A based model which fully supports all noise effects in real-time noise analysis. See next section for details.

#### **PSP 102**

The PSP 102 nmos and pmos geometric models (level 902) are also available as level 1023. However the two models are implemented differently. Level 902 is implemented through the SIMKIT interface. The model code itself in this case is created using ADMS from the Verilog-A description. However, it seems that the noise model for this is not created from the Verilog-A code and appears to have been hand coded. The Level 1023 version is built entirely from the Verilog-A code using the SIMetrix Verilog-A compiler but using a more advanced commercial C-compiler than the open source version supplied with SIMetrix. This version has the benefit over the Simkit version that it fully supports real-time noise including correlated effects and gate noise. It is however a little slower - typically about 5-10% compared to the SIMKIT version.

We have done extensive side by side tests of both models and both give identical results to a high degree of accuracy.

#### **Older Models**

Older "Philips Compact Models" (PCM) devices are no longer supported. Nearly all of the original PCM devices have been replaced by Simkit devices that are functionally identical. The following devices are not available in the Simkit library:

MOS 9 version 9.02 devices are no longer available, however, version 9.03 is fully backward compatible. Version 9.03 is available in the Simkit library. Version 9.02 was previously accessed using levels 102 and 202. These level numbers now map to version 9.03. The only change in behaviour is that some new version 9.03 parameters will be accepted correctly without error.

Mextram 5.03 is no longer available. Superseded by 5.04 but this is not directly compatible.

Diode level 200 is no longer available.

MOS 11 SIMetrix level 500/600 is no longer available. Superseded by 501/601. Currently no information is available as to whether or not the new version is backward compatible.

MOS level 302 is no longer available.

## **4.49 LTspice® Devices**

Some devices have been developed to allow compatibility with LTspice® models. In particular some Op-amp models for the former Linear Technology Corporation are only available in a form that uses special LTspice® devices. Some of these devices have been implemented in Verilog-A and are incorporated in the standard SIMetrix product. (A Verilog-A license is not required to run these models).

The following table lists the devices available:





The devices above accessed using the 'A' prefix letter have the possibility of being confused with XSpice devices which also start with the letter 'A'. However, all of the special LTspice® devices have 8 connections whereas the largest number of scalar connections for any XSpice device is 7 (for the J-K flip-flop). There are XSpice devices that have vector connections and for these it is possible to have 8 nodes and so these could be confused with LTspice® devices. Vector connections are enclosed with the characters '[' and ']' so to avoid conflict, devices that include these characters in node names will not be interpreted as LTspice® devices. The ':' character is also excluded as this delimits instance parameters for XSpice devices.

In addition, the following devices have been extended to add new parameters.



#### **4.49.1 LTspice® Notes**

#### **Additional Features**

Some additional features and changes have been made to enable LTspice® models to run correctly. These are listed below

• Interpret the micro symbol  $\mu$  as 1e-6. This has been implemented solely for compatibility with LTspice; we do not recommend using this in SIMetrix schematics or netlists.

SIMetrix will recognise both ANSI and UTF-8 encodings of this symbol. Note that the ANSI encoding is not universal. On some systems, in particular systems setup for Japanese, Chinese or Korean languages, the ANSI micro symbol (B5h) will display as a different character with most text editors. SIMetrix (and LTspice®) will still interpret the character as  $\mu$  and scale the preceding value accordingly. Finally, note that the UTF-8 encoding for the micro character (C2h B5h) is different to the encoding for the greek letter  $\mu$  (CEh BCh) but the two characters are visually indistinguishable. SIMetrix will also recognise the UTF-8 encoding of greek  $\mu$  as 1e-6.

- Arbitrary source X parameter. The X parameter in LTspice® is interpreted as the voltage across the source. This requires the setting **.options** LTspiceCompatibility=1
- Allow unquoted .PARAM expressions. This requires the setting **.options** LTspiceCompatibility=1
- dnlim and uplim functions implemented for arbitrary source expressions
- Capacitors defined using charge expressions in form Cxxx n1 n2 Q=expression

#### **Notes on Inductor Model**

If the parameters RSER, RPAR, CPAR or NOISELESS are provided with an inductor, a different model to the standard inductor will be used. The model has the following differences to the standard inductor:

- It cannot be used with a mutual inductor device
- The initial condition parameter operates in "SIMPLIS" mode exclusively. This means that the inductor will look like a perfect current source while the operating point is being computed if the IC parameter is specified. Note that this differs from LTspice which only enables the IC parameter when the .TRAN UIC switch is set. LTspice does allow initial conditions to be set using [.IC](#page-233-0) which SIMetrix does not currently support. The IC parameter provides a workaround to this limitation.

# **Chapter 5**

# **Digital/Mixed Signal Device Reference**

## **5.1 Digital Device Overview**

#### **5.1.1 Common Parameters**

A number of model parameters are common to most of the digital models. These are described below.

#### **Family Parameters**

These identify the logic family to which the input and outputs belong. See [Logic families](#page-340-0) for a detailed explanation. Most models have three family parameters:



#### **Output Parameters**





## **Input Parameters**



#### **5.1.2 Delays**

Most digital devices have at least one model parameter that specifies a time delay. Unless otherwise noted, all delays are *inertial*. This means that glitches shorter than the delay time will be swallowed and not passed on. For example, the following waveforms show the input and output of a gate that has a propagation delay of 10nS. The first pulse is only 5nS so does not appear at the output. The second pulse is 20nS so therefore is present at the output delayed by 10nS.



The Buffer device has an optional *stored delay* (also known as transport delay) parameter that makes possible the specification of pure delays.

## **5.2 And Gate**

#### **5.2.1 Netlist entry:**

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

#### **5.2.2 Connection details**



#### **5.2.3 Model format**

**.MODEL** model\_name d\_and parameters

#### **5.2.4 Model parameters**



#### **5.2.5 Device operation**

- If the model parameter OPEN\_C is false, The output will be at logic '0' if either input is at logic '0'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '1'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the *strength* of the output. If either input is at logic '0' the output strength will be STRONG. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state.

## **5.3 D-type Latch**



### **5.3.1 Netlist entry**

Axxxx data enable set reset out nout model\_name

## **5.3.2 Connection details**



### **5.3.3 Model format**

**.MODEL** model\_name d\_dlatch parameters

#### **5.3.4 Model parameters**





## **5.3.5 Device Operation**

The device is a level triggered latch with a single data input, complimentary outputs and active high asynchronous set and reset. The operation of the device is illustrated in the following diagram:



The asynchronous inputs (set and reset) override the action of the enable and data lines.

## **5.4 D-type Flip Flop**



## **5.4.1 Netlist entry**

Axxxx data clk set reset out nout model\_name

## **5.4.2 Connection details**



### **5.4.3 Model format**

**.MODEL** model\_name d\_dff parameters

## **5.4.4 Model parameters**





## **5.4.5 Device Operation**

The device is an edge triggered D-type flip flop with active high asynchronous set and reset. The operation of the device is illustrated by the following diagram:



## **5.5 Buffer**

#### **5.5.1 Netlist entry**

Axxxx in out model\_name

#### **5.5.2 Connection details**



#### **5.5.3 Model format**

**.MODEL** model\_name d\_buffer parameters

#### **5.5.4 Model parameters**



#### **5.5.5 Device Operation**

This device is a simple buffer with a single input and output. It can optionally be specified to have an open collector (open\_c parameter) or open emitter (open\_e parameter) output. Further, if the stored\_delay parameter is specified, the device will act as a pure delay. This means that it will pass pulses that are shorter than the delay time whereas normally (delay specified by rise\_delay and fall\_delay) such pulse would be swallowed (*stored\_delay* is also known as *transport delay*).



The following table describes the device operation in detail

Note the difference between open emitter and open collector operation. These modes have been designed to be as close to as possible to real devices, in particular their behaviour into an open circuit. An open emitter output, when switching from high to low is likely to follow the voltage on the device's base due to the base-emitter capacitance so the output state follows the input state. An open collector (or open drain) output on the other hand will remain in the low state when its input switches.

## **5.6 Frequency Divider**



#### **5.6.1 Netlist entry**

Axxxx freq\_in freq\_out model\_name

### **5.6.2 Connection details**



#### **5.6.3 Model format**

**.MODEL** model\_name d\_fdiv parameters

#### **5.6.4 Model parameters**



#### **5.6.5 Device Operation**

This device is a positive edge triggered frequency divider. Three model parameters allow arbitrary definition of the divide ratio, output duty cycle, output phase and initial delay. Operation of the frequency divider is illustrated by the following diagram which shows the output of a frequency divider with a DIV\_FACTOR of 10 and two alternative values of HIGH\_CYCLES.



The above was carried out with I\_COUNT=0. I\_COUNT is the initial value of the internal counter. The output first goes high when it attains a value of 1 or 1+DIVIDE\_RATIO so when I\_COUNT is zero (the default) the output first goes high after the first rising edge. If I\_COUNT is set to 5 the output first goes high after the 6th rising edge and if I\_COUNT is -20, the 21st rising edge.

## **5.7 Digital Initial Condition**

#### **5.7.1 Netlist entry**

Axxxx out model\_name

### **5.7.2 Connection details**



### **5.7.3 Model format**

**.MODEL** model\_name d\_init parameters

#### **5.7.4 Model parameters**



#### **5.7.5 Device Operation**

This device has the defined initial state (IC parameter) and initial strength (IS parameter) during the DC operating point solution, then reverts to HI-IMPEDANCE for the remainder of the analysis.

## **5.8 Digital Pulse**

#### **5.8.1 Netlist entry**

Axxxx out model\_name : parameters

### **5.8.2 Connection details**



#### **5.8.3 Instance parameters**



#### **5.8.4 Model format**

**.MODEL** model\_name d\_pulse parameters

#### **5.8.5 Model parameters**



#### **5.8.6 Device Operation**

This device supplies a repetitive or single pulse of defined period, delay and width. Optionally, the device may be specified to have an open emitter output allowing several pulse sources to be wire OR'ed to create complex pulses. All 5 main .MODEL parameters may also be specified on the device line as instance parameters in which case they override any values specified in the .MODEL statement.

If OPEN\_OUT is specified and true, a pull down resistor must be connected to the output.

## **5.9 Digital Signal Source**

#### **5.9.1 Netlist entry**

Axxxx [ out\_0 out\_1 .. out\_n ] model\_name

#### **5.9.2 Connection details**



#### **5.9.3 Model format**

**.MODEL** model\_name d\_source parameters

#### **5.9.4 Model parameters**



#### **5.9.5 Device Operation**

The digital signal source provides a multi bit arbitrary digital signal defined in a file.

#### **5.9.6 File Format**

The file is in ASCII format and is in the form of a table each row being on a new line. The first column defines the time values while the entries in the remaining columns define the output value for each of the outputs. So the total number of columns must be the number of outputs plus one. The output values must appear in the same order as the outputs in the netlist entry. So, the values for out\_0 will be in column 2, out 1 in column 3 etc.

The file may include blank lines and comment lines beginning with a '\*'.

The output values must specify the state as well as the strength using the following codes:





Note, these codes are not case sensitive.

## **5.9.7 Example**

#### The following file:

```
* This is an example source file
0.0 0s 0s 0r 1s
1u 0s 0s 0r 0z
2u 0s 0s 1r 0z
5u 1s 0s 1r 0z
22e-6 1s 1s 1r 0z
50u 0s 1s 1r 0z
60u 0s 1s 1r 0z
70u 0s 1s 1r 0z
80u 0s 1s 1r 0z
90u Us Us Ur 0s
```
and this circuit:



Produces the following waveforms



An error will result if the file fails in any way to comply with the format. There must be the exact number of entries in each row and the time values must be monotonic. Totally blank lines or lines containing only white space are permitted but any other non-comment line not complying with the format will fail.

## **5.10 Inverter**



#### **5.10.1 Netlist entry**

Axxxx in out model\_name

## **5.10.2 Connection details**



### **5.10.3 Model format**

**.MODEL** model\_name d\_inverter parameters

### **5.10.4 Model parameters**



#### **5.10.5 Device Operation**

If the OPEN C parameter is not specified or is FALSE, this device simply inverts the state of its input. I.e. if the input is logic '0' the output will be logic '1' and vice-versa. If the input is UNKNOWN the output will also be UNKNOWN.

If OPEN\_C is TRUE, the output state is always at logic '0' and the input determines its strength. If the input is at logic '1' the output strength is STRONG and if it is at logic '0' the output strength is HI-IMPEDANCE. The output strength will be UNDETERMINED if the input is UNKNOWN.

## **5.11 JK Flip Flop**

#### **5.11.1 Netlist entry**

Axxxx j k clk set reset out nout model\_name

#### **5.11.2 Connection details**



## **5.11.3 Model format**

**.MODEL** model\_name d\_jkff parameters

## **5.11.4 Model parameters**



## **5.11.5 Device Operation**

The following circuit and graph illustrate the operation of this device:



The following table describes the operation of the device when both inputs are at known states: The output can only change on a positive edge of the clock.



When either input is UNKNOWN, the situation is more complicated. There are some circumstances when a known state can be clocked to the output even if one of the inputs is unknown. The following table describes the operation for all possible input states. X means UNKNOWN.



## **5.12 Arbitrary Logic Block**

## **5.12.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] [ out\_0 out\_1 .. out\_n ] + model\_name : parameters

### **5.12.2 Connection details**



## **5.12.3 Instance Parameters**



## **5.12.4 Model format**

**.MODEL** model\_name d\_logic\_block parameters

### **5.12.5 Model parameters**



## **5.12.6 Device Operation**

See [Arbitrary Logic Block - User Defined Models.](#page-345-0)

## **5.13 Nand Gate**

## **5.13.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

#### **5.13.2 Connection details**



#### **5.13.3 Model format**

**.MODEL** model\_name d\_nand parameters

#### **5.13.4 Model parameters**



#### **5.13.5 Device operation**

- If the model parameter OPEN\_C is false, The output will be at logic '1' if either input is at logic '0'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the strength of the output. If
either input is at logic '0' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

## **5.14 Nor Gate**

### **5.14.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

### **5.14.2 Connection details**



#### **5.14.3 Model format**

**.MODEL** model\_name d\_nor parameters

### **5.14.4 Model parameters**



### **5.14.5 Device operation**

- If the model parameter OPEN\_C is false, The output will be at logic '0' if either input is at logic '1'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '1'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the *strength* of the output. If either input is at logic '1' the output strength will be STRONG. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state.

### **5.15 Open-Collector Buffer**

#### **5.15.1 Netlist entry**

Axxxx in out model\_name

### **5.15.2 Connection details**



### **5.15.3 Model format**

**.MODEL** model\_name d\_open\_c parameters

### **5.15.4 Model parameters**



### **5.15.5 Device Operation**

This device is included for compatibility with other XSPICE products. It is recommended that you use the digital buffer device (see [Buffer\)](#page-165-0) for new designs as this supports the additional common parameters such as static input loads and families.

The logic description for the open-collector buffer is described by the following table



## **5.16 Open-Emitter Buffer**

### **5.16.1 Netlist entry**

Axxxx in out model\_name

### **5.16.2 Connection details**



#### **5.16.3 Model format**

**.MODEL** model\_name d\_open\_e parameters

### **5.16.4 Model parameters**



### **5.16.5 Device Operation**

This device is included for compatibility with other XSPICE products. It is recommended that you use the digital buffer device (see [Buffer\)](#page-165-0) for new designs as this supports the additional common parameters such as static input loads and families.

The logic description for the open-collector buffer is described by the following table





# **5.17 Or Gate**

### **5.17.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

### **5.17.2 Connection details**



### **5.17.3 Model format**

**.MODEL** model\_name d\_or parameters

### **5.17.4 Model parameters**



### **5.17.5 Device operation**

- If the model parameter OPEN\_C is false, The output will be at logic '1' if either input is at logic '1'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the strength of the output. If either input is at logic '1' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

### **5.18 Pulldown Resistor**

#### **5.18.1 Netlist entry**

Axxxx out model\_name

### **5.18.2 Connection details**



### **5.18.3 Model format**

**.MODEL** model\_name d\_pulldown parameters

### **5.18.4 Model parameters**



### **5.18.5 Device Operation**

This is a single terminal device that can provide either a RESISTIVE or STRONG logic '0'. When resistive it can be used for wire-OR connected open emitter outputs. If STRONG is specified (by the STRONG parameter) its main application is as a digital ground connection.

# **5.19 Pullup Resistor**

#### **5.19.1 Netlist entry**

Axxxx out model\_name

#### **5.19.2 Connection details**



### **5.19.3 Model format**

**.MODEL** model\_name d\_pullup parameters

### **5.19.4 Model parameters**



### **5.19.5 Device Operation**

This is a single terminal device that can provide either a RESISTIVE or STRONG logic '1'. When resistive it can be used for wire-AND connected open collector outputs. If STRONG is specified (by the STRONG parameter) its main application is as a digital VCC connection.

# **5.20 Random Access Memory**

#### **5.20.1 Netlist entry**

Axxxx [ data\_in\_0 data\_in\_1 .. data\_in\_n ] [ data\_out\_0 data\_out\_1 .. + data\_out\_n ] [ address\_0 address\_1 .. address\_n ] write\_en + [ select\_0 select\_1 .. select\_n ] model\_name

### **5.20.2 Connection details**





#### **5.20.3 Model format**

**.MODEL** model\_name d\_ram parameters

#### **5.20.4 Model parameters**



### **5.20.5 Device Operation**

This device is provided for compatibility with other XSPICE products and is not recommended for new designs. In some circumstances, this device can consume large quantities of system (i.e. your PC's) RAM as it uses an inefficient method of storing state history. RAM's can also be implemented using the arbitrary logic block (see [Arbitrary Logic Block - User Defined Models\)](#page-345-0) which is much more efficient. An example of a simple 256X8 RAM can be found amongst the supplied example circuits (Examples/ALB\_Examples/RAM.sxsch and RAM.ldf).

## **5.21 Set-Reset Flip-Flop**

#### **5.21.1 Netlist entry**

Axxxx s r clk set reset out nout model\_name

### **5.21.2 Connection details**





### **5.21.3 Model format**

**.MODEL** model\_name d\_srff parameters

#### **5.21.4 Model parameters**



### **5.21.5 Device Operation**

The SR flip flop is similar to a JK flip flop except that the output is UNKNOWN when both S and R inputs are high. In a JK the output toggles in the same circumstances.

The following table describes the operation of the device when both inputs are at known states: The output can only change on a positive edge on the clock.



When either input is UNKNOWN, the situation is more complicated. There are some circumstances when a known state can be clocked to the output even if one of the inputs is unknown. The following table describes the operation for possible input states. X means UNKNOWN.



# **5.22 SR Latch**

### **5.22.1 Netlist entry**

Axxxx s r enable set reset out nout model\_name

### **5.22.2 Connection details**



### **5.22.3 Model format**

**.MODEL** model\_name d\_srlatch parameters

### **5.22.4 Model parameters**





### **5.22.5 Device Operation**

This device is identical to the SR flip flop except that it is level not edge triggered. That is the output may change whenever the enable input is high.

# **5.23 State Machine**

### **5.23.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] clk reset [ out\_0 out\_1 .. out\_n ] model\_name

### **5.23.2 Connection details**



### **5.23.3 Model format**

**.MODEL** model\_name d\_state parameters

#### **5.23.4 Model parameters**





#### **5.23.5 File Syntax**

The following is a formal description of the state machine file syntax using Backus-Naur form (BNF). '' and '' mean "zero or more" of the enclosed items.

state\_machine\_def :: state\_def state\_def

state def :: header\_line continuation\_line

header\_line :: STATENUM outputs inputs SEPARATOR STATE\_DEST

continuation\_line :: inputs SEPARATOR STATE\_DEST

outputs :: OUTPUT\_VALUE OUTPUT\_VALUE

inputs :: INPUT\_VALUE INPUT\_VALUE

STATENUM :: 0 based integer indicating state number.

SEPARATOR :: Any sequence of characters but not whitespace. '->' is conventional

STATE\_DESTINATION :: integer indicating state number.

**OUTPUT** VALUE :: two digit sequence to define one of the 12 output states. First character can be 0, 1 or U. Second character can be s, r, z or u for 'strong', 'resistive', 'high-z', and 'undefined' respectively.

#### **INPUT\_VALUE**  $:: 0, 1, x$ , or X

The idea is to have N *state\_def*'s where N is the number of states. Each *state\_def* has one *header\_line* and a number of following *continuation\_line*s. Both define the destination state for a given combination of inputs. The *header line* additionally defines the state being defined and the output value for that state. Header lines and continuation lines are distinguished by counting the tokens. The system does currently not appear to fail gracefully if this is wrong. A *header line* should have (num\_inputs+num\_outputs+3) tokens and a *continuation\_line* should have (num\_inputs+2).

The number of inputs and outputs is defined in the netlist line which is in the form:

Axxx [ inputs ] clk reset [ outputs ] modelname

### **5.23.6 Notes**

Currently this model is unsupported as it has not undergone testing or analysis. It is part of the original XSPICE system and should be compatible with other implementations but this cannot be guaranteed.

The following is an example of a state transition specification file





See Examples/Digital\_Devices/state\_updown.sxsch

# **5.24 Toggle Flip Flop**

### **5.24.1 Netlist entry**

Axxxx t clk set reset out nout model\_name

### **5.24.2 Connection details**



### **5.24.3 Model format**

**.MODEL** model\_name d\_tff parameters

### **5.24.4 Model parameters**





# **5.24.5 Device Operation**

The operation of the toggle flip flop is illustrated by the following diagrams. When the T input is high, the output toggles on each rising edge of the clock. If the T input is UNKNOWN the output will be UNKNOWN.





# **5.25 Tri-State Buffer**



### **5.25.1 Netlist entry**

Axxxx in enable out model\_name

### **5.25.2 Connection details**



### **5.25.3 Model format**

**.MODEL** model\_name d\_tristate parameters

### **5.25.4 Model parameters**





### **5.25.5 Device Operation**

This is a three terminal buffer device. The output state is equal to the input state and the output strength is determined by the enable input as follows:



# **5.26 Exclusive NOR Gate**

#### **5.26.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

### **5.26.2 Connection details**



#### **5.26.3 Model format**

**.MODEL** model\_name d\_xnor parameters



### **5.26.4 Model parameters**

### **5.26.5 Device Operation**

- If the OPEN C parameter is FALSE, the output is at logic '1' if an even number of inputs are at logic '1'. If any input is UNKNOWN the output will be UNKNOWN, otherwise the output will be at logic '0'.
- If the model parameter OPEN C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the strength of the output. If n even number of inputs are at logic '1' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. If any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

# **5.27 Exclusive OR Gate**

### **5.27.1 Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] out model\_name

### **5.27.2 Connection details**



### **5.27.3 Model format**

**.MODEL** model\_name d\_xor parameters

#### **5.27.4 Model parameters**



### **5.27.5 Device Operation**

- If the OPEN\_C parameter is FALSE, the output is at logic '1' if an odd number of inputs are at logic '1'. If any input is UNKNOWN the output will be UNKNOWN, otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the *strength* of the output. If an odd number of inputs are at logic '1' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. If any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

# **5.28 Analog-Digital Converter**

#### **5.28.1 Netlist entry**

```
Axxxx analog_in clock_in [ data_out_0 data_out_1 .. data_out_n ]
+ data_valid model_name
```
#### **5.28.2 Connection details**



### **5.28.3 Model format**

**.MODEL** model\_name ad\_converter parameters

### **5.28.4 Model parameters**



### **5.28.5 Device Operation**

This is a 1-32 bit analog to digital converter. The operation of this device is illustrated by the following diagrams:

*5.28. Analog-Digital Converter*







Conversion timings.

The ADC starts the conversion at the rising edge of the clock. The analog input signal is also sampled at this point. The output data changes in response to this, CONVERT\_TIME seconds later. At the same time the data valid output goes low (inactive) then high again after a delay equal to DATA\_VALID\_DELAY. It is possible to start a new conversion before the previous conversion is complete provided it is started later than MIN\_CLOCK seconds after the previous conversion was started. MIN\_CLOCK must always be less than CONVERT\_TIME. If the MIN\_CLOCK specification is violated, the conversion will not start.

### <span id="page-200-0"></span>**5.29 Analog-Digital Interface Bridge**

#### **5.29.1 Netlist entry**

Axxxx in out model\_name

#### **5.29.2 Connection details**



#### **5.29.3 Model format**

**.MODEL** model\_name adc\_bridge parameters

#### **5.29.4 Model parameters**





#### **5.29.5 Device Operation**

The analog-digital interface bridge is the main device used to connect analog signals to digital inputs. The device produces a digital signal that is in the logic '1' state when the analog input is above the high threshold (IN\_HIGH) and a logic '0' state when it is below the low threshold (IN\_LOW). When the analog input is in between these two states the output will be in the UNKNOWN state. The changes in state will be delayed according to the RISE\_DELAY and FALL\_DELAY parameters.

### **5.29.6 Analog input load**

The analog input presents a load to its driving circuit according to the digital load that is being driven. In other words the digital load is reflected to the analog input. Both static (i.e. DC) and dynamic (i.e. capacitance) elements of the load are reflected. To accurately reflect the sink and source currents, the interface bridge needs to know the voltage levels of the device it is driving. The digital device will (usually) have a SINK\_CURRENT and a SOURCE\_CURRENT model parameter each of which apply at defined logic voltage levels. These levels must be specified in the OUT\_LOW and OUT\_HIGH parameters of the AD interface bridge model. The input is modelled by a current source in parallel with a resistor. The values of these components are calculated from the above mentioned parameters and the digital load.

### **5.29.7 Input clamp**

The analog input is clamped at the voltages specified by CLAMP\_LOW and CLAMP\_HIGH. The clamping device has a characteristic similar but not identical to a junction diode in series with a resistance. Basically it has the characteristic of a diode up to a voltage excess of CLAMP\_BIAS after which it becomes resistive with a dynamic resistance of CLAMP\_RES. The diode characteristics are calculated so that the transition between the two regions is smooth.

### **5.29.8 Time Step Control - TIME\_TOL parameter**

Consider the following circuit and waveform



The graph shows the input and output of the NAND gate. Because the input is analog an implicit AD interface bridge will have been connected by the simulator. In the above example the parameters for this bridge have been set to:

**.model** HC\_adc adc\_bridge + in\_low=2.1 + in\_high=2.2

- + rise\_delay=1e-12 + fall\_delay=1e-12 + out\_family = "HC"  $+$  out\_low = 0 + out\_high = 5 + clamp\_bias=0.5
- + clamp\_res=10
- + time\_tol=10u

The last parameter, TIME\_TOL has been deliberately set ridiculously high to demonstrate what happens without time step control on the input. The input thresholds of the HC gate are 2.1 and 2.2 volts yet the output in the above example doesn't switch until the input has reached 0V. Because there is little activity in the analog circuit, the time steps are quite large. In fact in the above example the transient timepoints are at 55uS, 55.04uS, 56.2uS, 57.8uS and 60uS. The timepoint at 57.8u is just before the 2.2 volt threshold is reached and it isn't until the next time point, 2.2uS later that the lower threshold is broken. The result is the location of the negative edge at the output is delayed by approx. 2.2uS from where it should be. The

problem is that the analog system knows nothing of what is happening in the digital domain so carries on with large timesteps oblivious to the errors in the digital system.

To overcome this problem. SIMetrix features a mechanism (not in the original XSPICE system) that detects that the threshold has been passed and cuts back the time step to ensure that the digital edge occurs at an accurate point. The accuracy of this mechanism is controlled by the TIME\_TOL parameter. The smaller this parameter, the more accurately the exact threshold will be hit at the expense of short time steps and longer simulation runs. TIME\_TOL defaults to 100pS and in most applications this is a good choice. The following shows the result when TIME TOL is set to the default.



Here you can see the edge at the correct time.

The effect of not correctly simulating the threshold point has serious consequences when attempting to simulate relaxation oscillators constructed with digital inverters as the following graphs illustrate:



The top trace is without threshold control and the bottom trace is with it.

# **5.30 Digital-Analog Converter**

### **5.30.1 Netlist entry**

```
Axxxx [ digital_in_0 digital_in_1 .. digital_in_n ]
   + analog_out model_name
```
### **5.30.2 Connection details**



#### **5.30.3 Model format**

**.MODEL** model\_name da\_converter parameters

### **5.30.4 Model parameters**



### **5.30.5 Device Operation**

This device is a 1-32 bit digital to analog converter. Its operation is illustrated by the following diagrams.





DAC Waveforms



DAC waveforms expanded to show output slew

The device illustrated above has the following model definition:

**.model** DAC\_4 da\_converter + output\_slew\_time 1e-08 + output\_range 5

```
+ output_offset 0
```
In offset binary mode the D-A converter produce an output voltage equal to:

-OUTPUT\_RANGE/2 + OUTPUT\_OFFSET + code \* OUTPUT\_RANGE/2*<sup>n</sup>*

where *n* is the number of bits and code is the digital input code represented as an unsigned number between 0 and  $2^n - 1$ .

In 2's complement mode the output is:

OUTPUT\_OFFSET + code \* OUTPUT\_RANGE/2*<sup>n</sup>*

where n is the number of bits and code is the digital input code represented as a signed number between  $-2^{n/2}$  and  $2^{n/2} - 1$ .

Whenever the input code changes, the output is set on a trajectory to reach the target value in the time specified by OUTPUT\_SLEW\_TIME. UNKNOWN states are ignored. That is the input will be assumed to be at the most recent known state.

### **5.31 Digital-Analog Interface Bridge**

### **5.31.1 Netlist entry**

Axxxx in out model\_name

### **5.31.2 Connection details**



#### **5.31.3 Model format**

**.MODEL** model\_name dac\_bridge parameters

### **5.31.4 Model parameters**



#### **5.31.5 DC characteristics**

This digital to analog interface bridge is the main device used to connect digital signals to analog devices. The output provides an analog voltage and source resistance according to the state and strength of the driving digital input. The output has a non-linear characteristic that is a simplified model of a typical digital output stage. The following graphs show the output characteristics for the supplied high speed CMOS DA bridge. This has the following model parameters:

```
.model HC_dac dac_bridge
+ out_high=5 ; Logic high voltage
+ input_load=-31p ; Compensates for added rise and fall time
+ t_rise=2n ; Output rise time
+ t_fall=2n ; Output fall time
+ g_pullup=0.024 ; 1/(logic high output resistance)
+ g_pulldown=0.034 ; 1/(logic low output resistance)
+ g_hiz=1e-9 ; 1/(high impedance output res)
+ knee_low = 2.0 ; voltage at resistive/constant current
               ; knee logic low
+ knee_high =2.75 ; voltage at resistive/constant current
             ; knee logic high
+ v_smooth = 0.5 ; Knee smoothing band
```
+ in\_family="HC"



Logic '0' state - strength = STRONG

In the above graph, the slope of the curve at V=0 is determined by the G\_PULLDOWN parameter. The 'knee smoothing band' is a transitional area where the output switches from a constant resistance to a constant current. The smoothing characteristic is a quadratic and is calculated to be smooth at all points. This is required for good convergence behaviour. The knee smoothing band starts at KNEE\_LOW-V\_SMOOTH and finishes at KNEE\_LOW+V\_SMOOTH.



Logic '1' state - strength = STRONG

If a state with RESISTIVE strength is applied to the input of a digital to analog interface bridge, the output has the characteristic of a pure resistor connected to the voltage associated with the input's state. In the example given above, this would be a 1k resistor connected to 0V for the logic '0' state and a 1k resistor connected to +5V for the logic '1' state. (1k is 1/G\_RESISTIVE)

For the HI-IMPEDANCE strength, the output will look like a resistor of value 1/G\_HIZ connected to a voltage half way between the two analog output states. (1G connected to 2.5V in the above example.)

When the input state is UNKNOWN the output will be as if it were half way between the two known states. This is a compromise solution. The UNKNOWN state does not have a parallel in the analog domain so instead it is treated as a transitional state. In some cases the UNKNOWN state occurs in transitional cases although this is not the correct meaning of UNKNOWN.

### **5.31.6 Switching Characteristics**

When the logic state at the input changes, the output will transition from the current state to the target state in a time determined by T\_RISE or T\_FALL according to the direction of the state change.

# **5.32 Controlled Digital Oscillator**

### **5.32.1 Netlist entry**

Axxxx cntl\_in out model\_name : parameters

### **5.32.2 Connection details**



### **5.32.3 Instance Parameters**



#### **5.32.4 Model format**

**.MODEL** model\_name d\_osc parameters

### **5.32.5 Model parameters**



### **5.32.6 Device Operation**

This device produces an output frequency controlled by an analog input signal following an arbitrary piece-wise linear law. The input to output frequency characteristic is defined by two parameters CNTL\_ARRAY and FREQ\_ARRAY. The following is an example of a .MODEL statement:

```
.model vco d_osc
+ cntl_array=[-1,0,1,2,3,4,5]
+ freq_array=[0,10000,40000,90000,160000,250000,360000]
```
The frequency characteristic described by the above example follows a square law. The two arrays CNTL\_ARRAY and FREQ\_ARRAY must be the same length. These define the frequency output for a given analog input.

### **5.32.7 Time Step Control**

In order to control the accuracy of the phase of the output signal, this model may cut back the analog time step. At each analog time point, the required frequency is calculated and the digital output is set at that frequency. If the analog input changes by too large an amount between time points, the digital output phase could be substantially in error as the frequency is constant between analog time points. The actual error is calculated and if this exceeds PHASE\_TOL, the time point is rejected and a time point at which the error will be in tolerance is estimated.

Note: This model was included with the original XSPICE code but the SIMetrix version has been completely re-written. The original did not have any phase error control and could not give accurate results unless the analog time step was artificially kept small.

### **5.33 Analog-Digital Schmitt Trigger**

### **5.33.1 Netlist entry**

Axxxx in out model\_name

### **5.33.2 Connection details**



#### **5.33.3 Model format**

**.MODEL** model\_name adc\_schmitt parameters

#### **5.33.4 Model parameters**



### **5.33.5 Device Operation**

This device is basically identical to the [Analog-Digital Interface Bridge.](#page-200-0) The only difference is the behaviour of the device when the analog input lies between the threshold voltages. With the interface bridge, the output is UNKNOWN under these circumstances but with this Schmitt Trigger, the output retains its previous value and so is always in a known state. In summary, the output will only switch from low to high when the input exceeds the higher threshold (IN\_HIGH) and will only switch from high to low when the input descends below the lower threshold (IN\_LOW).

If initial input voltage lies between the hysteresis thresholds, the output state is determined by the init\_cond parameter.

# **Chapter 6**

# **Command Reference**

### **6.1 Overview**

Simulator commands instruct the simulator how to read in and simulate the circuit. All simulator commands begin with a period ( . ) .

For the remainder of this chapter and elsewhere in this manual, simulator commands are referred to as 'Statements' to distinguish them from commands entered in the command shell.

The schematic editor supports some of the statements described in this chapter but not all. Unsupported analysis statements may be added manually to the schematic's netlist. See [Adding Extra Netlist Lines](#page-17-0) for details.

The following simulator statements are recognised by SIMetrix.

[.AC](#page-220-0) [.DC](#page-223-0) [.ENDF](#page-225-0) [.ENDS](#page-282-0) [.FILE](#page-225-0) [.FUNC](#page-226-0) [.GLOBAL](#page-227-0) [.GRAPH](#page-227-1) [.IC](#page-233-0) [.INC](#page-234-0) [.INCLUDE](#page-234-0) [.KEEP](#page-234-1) [.LOAD](#page-237-0) [.LIB](#page-238-0) [.MODEL](#page-241-0) [.NOCONV](#page-244-0) [.NODESET](#page-244-1)

[.NOISE](#page-245-0)

[.OP](#page-248-0) [.OPTION](#page-250-0) [.OPTIONS](#page-250-0) [.PARAM](#page-272-0) [.PARAMETER](#page-272-0) [.POST\\_PROCESS](#page-274-0) [.PRINT](#page-274-1) [.SENS](#page-276-0) [.STEP](#page-281-0) [.SETSOA](#page-277-0) [.SUBCKT](#page-282-0) [.TEMP](#page-283-0) [.TF](#page-283-1) [.TRACE](#page-285-0) [.TRAN](#page-285-1) [.VECALIAS](#page-288-0)

The following statement is only recognised in model library files.

[.ALIAS](#page-221-0)

# **6.2 General Sweep Specification**

#### **6.2.1 Overview**

SIMetrix features a common sweeping algorithm which is used to define the swept analysis modes: .DC, .AC, .NOISE and (now) .TF, along with multiple analyses such as Monte Carlo.

The sweep algorithm has 6 modes:

- Device. Sweeps a single default value of a specified device. E.g. voltage of a voltage source, resistance of a resistor or the capacitance of a capacitor.
- Temperature
- Parameter. Parameter can be referenced in an expression for a model or instance parameter.
- Model parameter. Named model parameter.
- Frequency. (Not applicable to .DC)
- Monte Carlo. Perform a specified number of steps with distribution functions (i.e tolerances) enabled.
- Sensitivity. Perturbs each distribution function in turns to evaluate sensitivity of that function.
- Worst-case. Requires a prior sensitivity analysis. Perturbs all distribution functions to their full tolerance in a direction determined by their sensitivity to a specified goal function.

Standard SPICE only provides a subset of the above. .DC can only sweep voltage and current sources, .AC and .NOISE can only sweep frequency while .TF can't be swept at all.
As well as providing these modes, each of the modes can sweep in four different ways. These are linear, decade, octave and list.

### **6.2.2 Syntax**

All the swept analysis modes use the same general syntax to specify the sweep parameters. However, to maintain compatibility with SPICE and its derivatives including earlier versions of SIMetrix, each analysis mode allows variations to this standard syntax. The general syntax is described below while the variations allowed for each analysis mode are described in the section dedicated to that analysis mode.

All of the analysis modes can optionally be entered in a similar manner to .MODEL statements i.e. as an unordered list of parameter names followed by their values. For example, the following is a perfectly legal noise analysis specification:

```
.noise V=vout DEVICE=V1 VN=0 F=1k LIN=(100 -10m 10m)
+ INSRC=V1
```
In the various forms of the syntax described in the following sections, some of the parameter names may be omitted as long as they are entered in a particular order. It is sometimes, however, easier to remember parameter names rather than a default order, so the method described above may be more convenient for some users.

### **General syntax for swept analyses**

**.AC**|**.DC**|**.NOISE**|**.TF** sweep\_spec [ analysis specific parameters ]

sweep\_spec: One of the following:

```
DEVICE device_name step_spec F frequency
TEMP step_spec F frequency
PARAM param_name step_spec F frequency
MODEL model [PARAM] mod_param_name step_spec F frequency
FREQ step_spec
MONTE num_steps F frequency OUTFILE xml_logfile NOMCLOG
SENS [SENSID sensid] [SPAN span] [OUTFILE sens_outfile]
WC [SENSID sensid] [INFILE sens_infile] [WCID wcid] [OUTFILE wc_outfile]
```
Where





#### *step\_spec* is defined as follows:

**STP** start stop step **LIN** num\_points start stop **DEC** num\_points\_decade start stop **OCT** num\_points\_octave start stop **LIST** vall [ val2 ... ]

#### Where:



STP and LIN modes are both linear sweeps but specified differently. STP specifies start, stop and a step size, while LIN specifies start, stop and the total number of points.

# <span id="page-217-0"></span>**6.3 Multi Step Analyses**

### **6.3.1 Overview**

The sweep specification described in [General Sweep Specification](#page-215-0) can also be applied to define multiple analyses including Monte Carlo analysis. This can be applied to the swept modes .DC, .AC, .NOISE and .TF along with .TRAN. The analyses .SENS and .OP cannot be run in multi-step mode. A multi-step .OP is in fact the same as .DC so this is not required. Monte Carlo analysis is the subject of its own chapter (see [Monte Carlo Analysis\)](#page-294-0) but it is invoked in the same way as other multi-step modes. As well as the standard 6 sweep modes, small-signal multi-step analyses can be run in snapshot mode which uses snapshots created by a previous transient analysis.

Multi-step analyses may be nested. That is a multi-step specification can be applied to another multi-step specification. Nesting may be defined to any level.

### **6.3.2 Syntax**

The general form is:

```
.analysis_name analysis_parameters SWEEP
+ [sweep_spec] | [SNAPSHOT STP snapstart snapstop snapstep] |
 [SCRIPTCOUNT=numscriptruns SCRIPT=script] [ NUMCORES=num_cores]
.analysis_name analysis_parameters SWEEP
+ [reduced_sweep_spec] | [SCRIPTCOUNT=numscriptruns SCRIPT=script] [SWEEP reduced_sweep_spec]...
```

```
+ [ NUMCORES=num_cores]
```
Where:



### **Examples**

Run 10 Monte Carlo runs for 1mS transient analysis

**.TRAN** 1m SWEEP MONTE 10

As above but does 1000 steps split over 4 cores. So each core will do 250 steps. Requires a system equipped with at least 4 physical processor cores.

**.TRAN** 1m SWEEP MONTE 1000 NUMCORES=4

Sweep V1 from 0 to 5 volts in 0.1V steps for 200us transient

**.TRAN** 200u SWEEP DEVICE V1 STP 0 5 0.1

AC sweep of voltage source V5 from -300mV to 300mV. Repeat 6 times for parameter restail from 450 to 550.

```
.AC DEVICE=V5 LIN 100 -300m 300m F=100000
+ SWEEP PARAM=restail LIN 6 450 550
```
#### Run AC sweep using all available snapshots

**.AC** DEC 100k 10G SWEEP SNAPSHOT STP 0 0 0

Run a transient sensitivity analysis followed by a worst-case analysis

```
.TRAN 200u SWEEP SENS
.TRAN 200u SWEEP WC
```
### <span id="page-219-0"></span>**6.3.3 Syntax - Optimiser**

A special form of multi-step runs an optimisation analysis. This is an alternative to the form that uses the [.OPTIMISER](#page-249-0) statement. The multi-step optimiser mode can only specify a single analysis but runs more quickly especially for small circuits.

```
.analysis_name analysis_parameters SWEEP OPT
+ optparams=[parameter_names]
+ optinitvals=initial_values
+ [optminvals=minimum_values]
+ [optmaxvals=maximum_values]
+ alg=algorithm
+ [abstol=absolute_tolerance]
+ [reltol=relative_tolerance]
+ [iterlim=iteration_limit]
+ [schematic=schematic_file]
+ [results_file=results_file]
+ [show_progress]
```




## **6.4 .AC**

### **6.4.1 Syntax**

**.AC** inner\_sweep\_spec [ **F** frequency ] [**RUNNAME**=runname] [ **SWEEP** outer\_sweep\_spec ]

Spice compatible frequency sweep:

**.AC DEC**|**LIN**|**OCT** num\_points start stop

Instructs the simulator to perform a swept small signal AC analysis. SIMetrix AC analysis is not limited to a frequency sweep as it is with generic SPICE and derivatives. See [General Sweep Specification](#page-215-0) and examples below for more details.



Except for frequency sweep, the frequency at which the analysis is being performed should be specified. If omitted, the frequency will be assumed to be zero.

For non-frequency sweeps, a new dc operating point may be calculated at each step depending on what is

being swept. If a capacitor, inductor or an 'AC only' model parameter is being swept, then no new dc operating point will be required. Otherwise one will be performed. An 'AC only' parameter is one that does not affect DC operating point such as device capacitance.

### **6.4.2 Notes**

An AC analysis calculates the small signal frequency response of the circuit about the dc operating point. The latter is automatically calculated prior to commencing the frequency sweep. One or more inputs may be specified for AC analysis by using voltage or current sources with the AC specification (See [Voltage](#page-135-0) [Source\)](#page-135-0). The results of an AC analysis are always complex.

### **6.4.3 Examples**

SPICE compatible. Sweep frequency from 1kHz to 1Meg

**.AC** DEC 25 1k 1MEG

Sweep voltage source V1 100 points from -100mV to 100mV. Frequency = 100kHz

**.AC** DEVICE V1 LIN 100 -100m 100m F=100k

Sweep parameter Rscale from 0.5 to 3 in steps of 0.1. Frequency=20Meg

**.AC** PARAM Rscale STP 0.5 3 0.1 F=20Meg

Sweep resistor R1 with values 10k 12k 15k 18k 22k 27k 33k, Frequency =1.1KHz

**.AC** DEVICE R1 LIST 10k 12k 15k 18k 22k 27k 33k F=1.1K

Monte Carlo sweep 100 steps. Frequency = 10K. This is useful if - say - you are interested in the gain of an amplifier at one frequency and it needs to lie within a defined tolerance. Previously you would need to repeat an AC sweep at a single frequency to achieve this which could take a long time especially if the circuit has a difficult to find operating point. The analysis defined by the following line will take very little time even for a large circuit.

**.AC** MONTE 100 F=10K

### **6.4.4 Examples of Nested Sweeps**

As Monte Carlo above but repeated from 0 to 100C

**.AC** MONTE 100 F=10K SWEEP TEMP STP 0 100 10

... and at a number of frequencies

**.AC** MONTE 100 SWEEP FREQ DEC 5 1k 100k

### **6.5 .ALIAS**

#### **6.5.1 Syntax**

**.ALIAS** alias\_name device\_name device\_type

This statement may only be used in device model library files. It is not recognised by the simulator. It permits a device model or subcircuit to be referenced by a different name. This allows one model definition to be used for multiple part numbers.



#### **6.5.2 Example**

**.MODEL** BC547C NPN

- + IS=7.59E-15 VAF=19.3 BF=500 IKF=0.0710 NE=1.3808
- + ISE=7.477E-15 IKR=0.03 ISC=2.00E-13 NC=1.2 NR=1 BR=5
- + RC=0.75 CJC=6.33E-12 FC=0.5 MJC=0.33 VJC=0.65
- + CJE=1.25E-11 MJE=0.55 VJE=0.65 TF=4.12E-10 ITF=0.4 VTF=3
- + XTF=12.5 RB=172 IRB=0.000034 RBM=65

**.ALIAS** BC549C BC547C NPN

The above would provide identical definitions for both BC547C and BC549C bipolar transistors.

Notes .ALIAS definitions will recognise models defined in other files provided the file in which the alias resides and the file in which the model definition resides are part of the same library specification. A library specification is a single pathname possibly with a wildcard ('?' or '\*') to refer to multiple files. E.g. /simetrix/models/\*.mod is a library specification and refers to all files with the extension '.mod' in the directory /simetrix/models.

> Aliases must refer directly to a model or subcircuit definition and not to other aliases.

## **6.6 .DATA**

Three formats:

Simple format

**.DATA** name data [**TYPES=**types]

#### Multiple column format

**.DATA** name **FORMAT=COLUMNS** [**TYPES=**types] **COLUMNS=**column\_names data

#### XY Format

**.DATA** name **FORMAT=XY** [**TYPES=**types] data

Creates a vector that will be output to the simulation data group. This can be used in post-processing operations such as optimiser measurements.



The TYPES parameter is a list of comma separated physical type names. Maybe one of the following values



### **6.6.1 Example**



The above statement will create an XY Vector called Diode\_data and this will be placed in the simulation data group created by the current analysis.

# **6.7 .DC**

### **6.7.1 Syntax**

**.DC** inner\_sweep\_spec [**RUNNAME**=runname] [ **SWEEP** outer\_sweep\_spec ]

Spice compatible:

**.DC** device\_name start stop step

The remainder are SIMetrix 2.5 - 3.1 compatible:

**.DC TEMP** start stop step **.DC PARAM** param\_name start stop step **.DC MODEL** model [**PARAM**] mod\_param\_name start stop step

Instructs simulator to perform a DC sweep analysis. A dc analysis performs a dc operating point analysis for a range of values according to the sweep specification. SIMetrix DC analysis is not limited to sweeping a voltage or current source as with generic SPICE. Any mode defined by the general sweep specification (see [General Sweep Specification\)](#page-215-0) may be used although frequency sweep has no useful purpose.



If *start* is arithmetically greater than *stop* then *step* must be negative.

It is not necessary to declare parameters with .PARAM if using parameter sweep.

### **6.7.2 Examples**

SPICE compatible. Sweep V1 from 0 to 5 volts in steps of 0.1 volt

**.DC** V1 0 5 0.1

SIMetrix 3.1 compatible temperature sweep

**.DC** TEMP 0 100 2

Decade (i.e. logarithmic) sweep. Sweep V1 from 1mV to 1V with 25 points per decade

**.DC** V1 DEC 25 1m 1v

Note that the DEVICE keyword has been omitted. This is the default sweep mode for .DC.

Do 1000 Monte Carlo steps. This performs the same task as a Monte Carlo analysis applied to a DC operating point. In other products and earlier versions of SIMetrix this task would take a long time as the

operating point is solved from scratch each time. With the mode described by the following example, the operating point need only be calculated from scratch once. All subsequent steps are seeded by the previous one and usually require only a few iterations. The end result is a sometimes spectacular increase in speed.

```
.DC MONTE 1000
```
### **6.7.3 Examples of Nested Sweeps**

Decade sweep at temperatures 0 to 100 in steps of 10

**.DC** V1 DEC 25 1m 1v SWEEP TEMP STP 0 100 10

Note the STP keyword is necessary to signify the start-stop-step method of defining a linear sweep. Alternatively LIN can be used which defines the sweep in terms of the total number of points. The following is equivalent to the above:

**.DC** V1 DEC 25 1m 1v SWEEP TEMP LIN 11 0 100

Do 100 run Monte Carlo analysis for temperature sweep

**.DC** TEMP 0 100 2 SWEEP MONTE 100

## **6.8 .FILE and .ENDF**

#### **6.8.1 Syntax**

```
.FILE filename
file_contents
.ENDF
```
The .FILE statement allows the contents of a file referenced in a .MODEL statement to be placed directly in the netlist. Files are referenced in arbitrary logic blocks (see [Arbitrary Logic Block - User Defined](#page-345-0) [Models\)](#page-345-0), PWLFILE voltage and current sources (see [PWL File Source\)](#page-137-0), digital sources (see [Digital Signal](#page-170-0) [Source\)](#page-170-0) and digital state machines (see [State Machine\)](#page-190-0). Each of these may refer to files defined using .FILE and .ENDF.

#### **6.8.2 Example**

```
.MODEL COUNT_8 d_logic_block file=counter_def
.FILE counter_def
PORT (DELAY = 10n) CountOut out [0:7];
EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;
Count = Count + 1;
CountOut = count;
.ENDF
```
The .MODEL statement refers to a file called 'counter\_def'. This could be a real disk file called counter\_def or counter\_def.ldf, but in the above example it is instead defined directly in the netlist using .FILE and .ENDF.

#### **6.8.3 Important Note**

.FILE and .ENDF will *not* be recognised in library files.

### **6.8.4 Using with SIMPLIS**

When using .FILE and .ENDF with the SIMPLIS simulator, the text "SIMPLIS\_PASS\_THRU" must be placed at the end of the .FILE statement:

```
.FILE filename SIMPLIS_PASS_THRU
file_contents
.ENDF
```
# **6.9 .FUNC**

**.FUNC** name ( [arglist] ) { body }



.FUNC defines a function that can be used in a model or device parameter expression, a parameter defined using .PARAM or in an arbitrary source expression.

### **6.9.1 Examples**

```
.FUNC FREQ(V) { (V) * 120K}
.FUNC SWEEP(V) { SIN(TIME*FREQ(v) *2*PI) }
.FUNC RV1() { GAUSS(0.1) }
```
The third example may be called without parentheses as it has no arguments. E.g.:

```
PARAM random1 = rv1 random2 = rv1
```
In the above, random1 and random2 will have different values when run in a Monte Carlo analysis.

### **6.9.2 Optimiser**

Any expression that uses a function defined with .FUNC will be automatically processed by an optimisation algorithm. For more information see [Optimisation.](#page-45-0)

The optimiser attempts to speed simulations by making the expression evaluation more efficient. The optimiser is effective when .FUNC is used to create very complex expressions perhaps to develop a semiconductor device. In simple applications it may not make a noticeable improvement to performance. The optimiser can be enabled for *all* expressions and can also be disabled completely. To enable for all expressions use:

**.OPTIONS** optimise=2

To disable:

**.OPTIONS** optimise=0

## **6.10 .GLOBAL**

**.GLOBAL** node [ node... ]

Identifies nodes as global. This allows nodes specified at the top level of a circuit to be accessed within a subcircuit definition. For more information see [Subcircuits.](#page-46-0)

## **6.11 .GRAPH**

### **6.11.1 Parameters**

```
.GRAPH signal_name|"expression"
+ [ persistence = persistence ]
+ [ axisname = axisname ]
+ [ gridname = gridname ]
+ [ graphname = graphname
+ [ axistype = digital|grid|gridauto|axis|auto ]
+ [ curvelabel = curvelabel ]
+ [ xlabel = xlabel ]
+ [ ylabel = ylabel ]
+ [ xunit = xunit ]
+ [ yunit = yunit ]
+ [ xmin = xmin ]
+ [ ymin = ymin ]
+ [ xmax = xmax ]
+ \int ymax = ymax \int+ [ analysis = analyses_list ]
+ [ ylog = lin|log|auto ]
+ \begin{bmatrix} \mathbf{x} \mathbf{log} = \mathbf{lin} | \mathbf{log} | \mathbf{auto} \end{bmatrix}+ [ nowarn = true|false ]
+ [ initXLims = true|false]
+ [ bus = bustype ]
+ [ complete = true|false ]
+ [ order = order ]
+ [ colour | color = colour ]
+ [ colourname | colorname = colourname ]
+ [ disabled = true|false]
+ [ xdelta = xdelta ]
+ [ ydelta = ydelta ]
+ [ proberef = proberef ]
+ [ measure[index] = measure_expression]
+ [ measureLabel[index] = measure_label]
+ [ useNameAsTitle = true|false ]
+ [ separateCurves = true|false ]
+ [ guid = guid ]
+ [ ownXAxis = true|false ]
+ [ style = Histogram|ScatterPlot ]
```
.GRAPH instructs SIMetrix to plot a graph of the specified signal or expression. The graph can be plotted incrementally as the simulation proceeds or may be delayed until the run is complete.

Note that although .GRAPH is a simulator statement, it is implemented in the front end and will only function in full GUI mode. Batch mode simulation does not support .GRAPH.











The .GRAPH statement is the underlying simulator mechanism used by the schematic's fixed probes. See *User's Manual/Graphs, Probes and Data Analysis/Fixed Probes* for details.

.GRAPH supersedes the older and less flexible [.TRACE.](#page-285-0) The latter is, however, still supported and may sometimes be convenient for specifying multiple signals on one line.

### **6.11.2 Using Multiple .GRAPH Statements**

If specifying several .GRAPH statements to plot a number of curves on the same graph, you should make sure that the various parameters are consistent. If for example, a conflict arises if you specify xmin and xmax for two .GRAPHs that plot curves in the same graph sheet, and the values for xmin and xmax are different for each. You can specify xmin and ymin for just one of the .GRAPH statements or you can specify for all and make sure they are all the same. The same applies to other non-Boolean parameters i.e. ymin, ymax, xlabel, ylabel, xunits and yunits. The parameter initXLims, however must be specified with the same value for all .GRAPH statements specifying the same graph sheet.

Conflicting values of ylog and xlog are resolved by plotting the curves on separate axes or graph sheets respectively.

### **6.11.3 Creating X-Y Plots**

To create an X-Y plot, use the XY() function (*Script Reference Manual/Function Reference/XY* for full details of available functions). You should also specify "initXLims=false". E.g.

```
.GRAPH "XY( imag(vout), real(vout) )" initXLims=false
+ xlog=LIN complete=true
```
The above will create a Nyquist plot of the vector VOUT.

### **6.11.4 Using .GRAPH in Subcircuits**

.GRAPH maybe used in a subcircuit in which case a plot will be produced for all instances of that subcircuit. Note, however, that it will only work for single values and not for expressions when inside a subcircuit. The value of the *curveLabel* parameter will be prefixed with the instance name so that the displayed curves can be correctly identified.

### <span id="page-232-0"></span>**6.11.5 Using Expressions with .GRAPH**

You can enter an expression as well as single vectors to be plotted. A problem arises when plotting expressions incrementally that are regularly updated while the simulation is running. SIMetrix versions prior to v5 could not incrementally evaluate expressions, so each time the plot of an expression was updated, the expression had to be recalculated from the beginning. This was inefficient and it has always been recommended that the complete=true flag was added in these circumstance to inhibit incremental plotting.

SIMetrix - from version 5 - now has the ability to incrementally evaluate some expressions and there is no longer a recommendation to set complete=true. However, certain expression cannot be incrementally evaluated and when such expressions are entered, incremental plotting will automatically be disabled and the plot won't appear until the run is complete.

A notable example of expressions that cannot be incrementally evaluated is anything containing the phase() function. This is because the phase() function uses a state machine to determine when the phase wraps from -180 to 180 and back. An offset is then applied to make the phase plot continuous. Because of the state machine, it is always necessary to evaluate this function from start to finish which makes incremental evaluation difficult. An alternative is to use instead the arg() function. This is the same as phase, but does not have the state machine and always gives an output that lies between +/- 180 degrees.

### **6.11.6 Plotting Spectra with .GRAPH**

You can use .GRAPH to create spectrum plots using FFTs or Fourier. However, FFT is quite difficult to use on its own as it needs interpolated data. So, a new user defined function called Spectrum() has been developed that is especially designed for use with .GRAPH. Usage is:

Spectrum(vector, numPoints [, start [, stop]])

Where:



Spectrum() cannot be incrementally evaluated and so incremental plotting will automatically be disabled for any .GRAPH statement that uses it. See [Using Expressions with .GRAPH.](#page-232-0)

#### **Examples**

**.GRAPH** C2\_P curveLabel="Amplifier output" nowarn=true

Plots the vector C2\_P and gives it the label 'Amplifier output'. As NOWARN is TRUE, no warning will be given if C2\_P does not exist.

**.GRAPH** vout\_quad + axisType="grid" + axisName="grid1" + persistence=2 + curveLabel="Quadrature" + nowarn=true + analysis = TRAN|DC **.GRAPH** vout + axisType="grid" + axisName="grid1"

```
+ persistence=2
+ curveLabel="In Phase"
+ yLabel="Filter Outputs"
+ nowarn=true
+ analysis = TRAN|DC
```
The above illustrates the use of the parameters AXISTYPE and AXISNAME. Both the vectors specified by the above .GRAPH statements will be plotted on the same but separate grid. Because both grids have been given the AXISNAME grid1, each curve will be plotted on the same one. If the values of axisname for the above were different, each curve would be plotted on a *separate* grid. The ANALYSIS parameter has been specified in both cases, so plots will only be created for transient and dc sweep analyses.

## <span id="page-233-0"></span>**6.12 .IC**

```
\cdotIC V(node1)=val1 [ V(node2)=val2 ]...
```
#### OR

**.IC** node1 val1 [ node2 val2 ]

This statement sets transient analysis initial conditions.



If the UIC parameter is specified with the .TRAN statement no DC operating point will be calculated so an initial condition will set the bias point in the same way as an IC=... parameter on a BJT, capacitor, diode, JFET or MOSFET.

If the UIC parameter is absent from the .TRAN statement then a DC operating point is calculated before the transient analysis. In this case the net voltages specified on the .IC statement are forced to the desired initial values during the DC operating point solution. Once transient analysis begins this constraint is released. By default the voltage force is effectively carried out via a 1 $\Omega$  resistor. This can be changed with the option setting ICRES (see [.OPTIONS\)](#page-250-0).

### **6.12.1 Alternative Initial Condition Implementations**

An initial condition can also be specified using a voltage source with the DCOP parameter specified. E.g.

VIC1 2 3 3.5 DCOP

Will force a voltage of 3.5 volts between nodes 2 and 3 during the DC operating point solution. This has two advantages over .IC:

- 1. It has zero force resistance
- 2. It can be applied differentially

You can also use a capacitor with the BRANCH parameter set to 1. E.g.:

C1 2 3 10u BRANCH=1 IC=3.5

This will behave identically to the voltage source in the above example during the DC operating point but during a subsequent small-signal or transient analysis will present a 10 F capacitance to nodes 2 and 3.

See also: [Capacitor](#page-73-0) and [Voltage Source.](#page-135-0)

## **6.13 .INC**

**.INC** pathname

Insert the contents of the specified file.

*pathname* File system pathname for file to be included

The .INC statement is replaced by the specified file in its entirety as if was part of the original file. .INC statements may also be nested i.e. there may be .INC statements within the included file. Nesting may be to any level.

# **6.14 .KEEP**

**.KEEP** signal\_spec [signal\_spec ...]

This statement tells the simulator what values to store during a simulation. By default all signals at the top level and defined inside a hierarchical subcircuit are saved. .KEEP may be used in conjunction with some .OPTIONS settings to increase or reduce the data saved.





## **6.14.1 Option Settings**

A number of option settings are available to control data output. These can be used in conjunction with .KEEP statements to define what data is saved. The Option settings are defined in the table below:





### **Examples**

Default with no Keep options is to save all top level data and all signals inside hierarchical subcircuits. Data inside non-hierarchical subcircuits are not saved.

Don't save any data except signals defined in .KEEP or .GRAPH statements:

```
.OPTIONS KeepNone
```
Save all data except device internals and semiconductor currents in AC analyses. Includes data inside subcircuits and hierarchies:

**.OPTIONS** KeepAll

Save everything including device internals and semiconductor currents in AC analyses:

**.OPTIONS** KeepAll KeepAllAci KeepInternal

Don't save currents:

**.OPTIONS** KeepNoi

Save signals in the top level and the first level in the hierarchy:

```
.OPTIONS KeepSubCktDepth=1
```
Save about 20% of all data:

```
.OPTIONS KeepQuotaFactor=0.2
```
Store only voltages and currents in sub-circuit X1 excluding descendants.

```
.OPTIONS KeepNone
.KEEP X1.*v X1.*i
```
Store only voltages and currents in sub-circuit X1 including descendants.

```
.OPTIONS KeepNone
.KEEP X1.**v X1.**i
```
Store voltages within U3.U12 along with VOUT and VIN

**.OPTIONS** KeepNone **.KEEP** U3.U12.\*v VOUT VIN

Store all top level voltages and currents in U7

```
.OPTIONS KeepNone
.KEEP U7.*i
```
### **Notes**

.KEEP may be used inside a sub-circuit definition in which case .KEEP operates at a local level. For example .KEEP \*v inside a sub-circuit definition specifies that all voltages within that subcircuit (for all instances) will be saved. .KEEP \*\*v does the same but also includes any descendant sub-circuit instances.

SIMetrix uses subcircuits to implement hierarchical schematics. Subcircuits are also used in other ways, for example to implement device macro models. SIMetrix is able to distinguish between subcircuits used for hierarchies and other subcircuits. It does this by placing a comment line below the .SUBCKT line as shown below:

```
.subckt fastamp VOUTP VN VINP VP VINN VOUTN
*#hierarchy
...
.ends
```
The comment line \*#hierarchy marks the subcircuit as part of the schematic hierarchy. The schematic editor's netlist generator automatically adds \*#hierarchy lines as appropriate.

## **6.15 .LOAD**

```
.LOAD file [instparams=parameter_list] [nicenames=0|1] [goiters=goiters]
  [ctparams=ctparams] [suffix=suffix] [warn=warnlevel]
```
Loads a device file. This may be a Verilog-A file or a compiled binary (.sxdev file).



### **6.16 .LIB**

There are two forms of .LIB and the behaviour of each is completely different from each other. The SIMetrix Native Form specifies a file or group of files to be searched for any model or subcircuit that has not yet been found. The HSPICE® version is a selective version of .INC but unlike .INC it doesn't include the whole file, just a specified portion of it.

### **6.16.1 SIMetrix Native Form**

**.LIB** pathname

*pathname* File system path name specifying a single file or, by using a wildcard (\* or ?), a group of files. If the path name contains spaces, it must be enclosed in quotation marks (").

The SIMetrix form of this statement specifies a pathname to be searched for model and subcircuit libraries. Any number of .LIB statements may be specified and wildcards (i.e. \* and ? ) may be used.

If a model or subcircuit is called up by a device line but that definition was not present in the netlist, SIMetrix will search for it in files specified using the .LIB statement.

SIMetrix will also search for definitions for unresolved parameters specified in expressions. These are defined using [.PARAM.](#page-272-0)

### **Example**

The following statement instructs the simulator to search all files with the .mod extension in c:\Spice Model Library\for any required subcircuits or device models.

**.lib** "c:\Spice Model Library\\*.mod"

### **6.16.2 HSPICE Form**

**.LIB** `filename' entryname



When HSPICE® the form of .LIB is encountered, SIMetrix will search the file specified by *filename* for a section enclosed by:

**.LIB** entryname

and

.ENDL

.LIB calls may be nested as long as they are not recurrent. That is a .LIB call within a .LIB .ENDL block may not call itself but it may call another block within the same file. (HSPICE® itself does not permit this).

This form of .LIB is commonly used in model files issued by semiconductor fabrication plants which tend to be designed for use with HSPICE®. The entry name parameter is used for process corner and skew

selection. Typically the model file would have entries for - say - slow, nominal and fast models. These would reside under entry names of, perhaps, SS, NOM, and FF respectively. You can very rapidly switch between these model sets simply by changing the entry name on the .LIB line e.g.

would select the nominal models. Changing to:

**.LIB** `c:\models\fab1\process\_a\top.mod' NOM

would switch to the slow models.

### **6.17 .MAP**

```
.MAP MODELNAME=modelname DEVICE=device LEVEL=level [LETTER=letter]
[REPORT=reportstatus]
```
Map simulator device to model name and level number.



### **6.17.1 .MAP Notes**

All device models (that is the binary code that implements the device equations) have an internal name that is used to uniquely identify it, but this name is not used externally. Instead .MODEL statements use their own name (e.g. nmos, pnp) coupled with an optional LEVEL parameter to define the actual device referred to. For example, the MOS level 3 device is referred internally as "MOS3" but the .MODEL statements use the names NMOS or PMOS and set the LEVEL parameter to 3. The mapping between NMOS and LEVEL 3 to "MOS3" is defined in an internal table which can be modified by this statement. The .MAP statement can add new entries to the table so providing additional methods of accessing a device. It can also modify existing entries to point to a new device. To modify an existing mapping, you only need to provide ModelName, Device and Level values. The modelname and level must point to an existing combination that is already in use, e.g. ModelName=D and Level=1, and device would then be set to the new device that this combination is to point to, e.g. Diode3. So this is what the spec would be:

```
.MAP ModelName=D,Level=1,Device=Diode3
```
The above would make level 1 diodes use the same model as level=3. Here is another example:

**.MAP** ModelName=R,Level=0,Device=HspiceRes

Level=0 is the level value when the LEVEL parameter is not specified. In the case of resistors, no .MODEL statement is required at all, so the above line will change the default model used for all resistors to the Hspice model instead of the native SIMetrix model.

It is also possible to add a new mapping in which case the level and modelname parameters must be currently unused. Also when creating a new mapping the 'Letter' parameter must be specified. 'Letter' is the first letter of the component reference traditionally used to identify the type of device in SPICE netlists. For example 'Q' refers to BJTs and 'D' refers to diodes. or example, the following entries define LEVEL=69 as a valid level for accessing the PSP 1.03 model:

```
.MAP ModelName=nmos, Level=69, Device=psp103_n, report=on
.MAP ModelName=pmos, Level=69, Device=psp103_n, report=on
```
Note that two entries are required in order to support both n-channel and p-channel devices. The above doesn't change the existing level it adds an additional level. Both the original level number and 69 will be accepted and be equivalent. When defining a new mapping the letter must be specified and usually this should be the letter conventionally used for the class of device. If defining a new mapping for a MOSFET, the letter 'M' should be used, for a diode the letter 'D' should be used and so on. However, the letters, 'N', 'P', 'W', 'U' and 'Y' maybe used as well for any type of device.

### **6.17.2 Device Configuration File**

.MAP statements affect only the simulation on the netlist in which they appear. Alternatively the same re-mapping may performed more permanently using a device configuration file.

### **Creating a Device Configuration File**

The device configuration file (DCF) path and name are defined by the option variable DevConfigFile. By 'option variable', we mean the variables assigned using the command line Set command not simulator options set by .OPTIONS.

The default value for the setting is %SHAREPATH%/DeviceConfig.sxdcf, %SHAREPATH% resolves to the support directory under the installation root.

### **Format**

Each line in the DCF has the same format as the .MAP statement without the .MAP keyword:



The meaning of each of the above is the same as described for the .MAP statement

### **Example**

The following shows the DCF needed to remap the PSP 1.03 device as described above for the .MAP statement.

```
ModelName=nmos, Level=69, Device=psp103_n, report=on
ModelName=pmos, Level=69, Device=psp103_n, report=on
```
### <span id="page-240-0"></span>**6.17.3 List of All Simulator Devices**

A list of all internal devices may be obtained using the show\_devices script. This will copy to the system clipboard a tab delimited table listing all internal devices. This is guaranteed to be accurate as it is

generated directly by SIMetrix. To obtain this table proceed as follows:

1. Type this at the command line. (The edit box below the menu bar in the command shell. This is not available in the free SIMetrix Intro)

show\_devices

- 2. You should see a message "Device information has been copied to the system clipboard" appear
- 3. Using a spreadsheet program, execute the Paste function. You should see the table appear.

The table has seven columns:

Column 1: Internal name. This is the device name

Column 2: Model name as used in the .MODEL statement

Column 3: Level.

Column 4: Minimum number of terminals that this device must have

Column 5: Maximum number of terminals that this device may have

Column 6: Device letter

Column 7: Model Version

Column 8: License feature required to use this device

Some internal devices have a model name beginning with '\$\$'. These device do not use a .MODEL statement and have no model parameters. The name is used internally only.

Devices with a minimum number of terminals of -1 do not have a minimum number. Similarly devices with zero maximum number of terminals do not have a maximum.

## <span id="page-241-0"></span>**6.18 .MODEL**

```
.MODEL modelname modeltype ( param1=val1 [ param2=val2 ]... )
.MODEL modelname ako:inherited_name modeltype ( param1=val1 [ param2=val2 ]... )
```
This statement specifies a set of model parameters that are used by one or more devices. .model statements often reside in model libraries.



### **6.18.1 XSPICE Model Types**



# **6.18.2 SPICE Model Types**



### **6.18.3 Safe Operating Area (SOA) Limits**

It is possible to define SOA limits within the .MODEL statement. To do this, add one or more parameters in the following format:

LIMIT(name)=(min, max, xwindow)



### **6.18.4 Example**

The following is a model for a 1N5404 diode.

```
.MODEL D1n5404 D(Is=15.48f Rs=7.932m Ikf=0 N=1 Xti=3
```

```
+ Eg=1.11 Cjo=150p M=.3 Vj=.75 Fc=.5
```

```
Isr=120n Nr=2 Bv=525 Ibv=100u)
```
## **6.19 .NOCONV**

.NOCONV V(node1)=val1 [ V(node2)=val2 ]...

Disables convergence testing for the specified nodes.

## <span id="page-244-0"></span>**6.20 .NODESET**

 $NODESET$  V(node1)=val1 [ V(node2)=val2 ]...

#### OR

**.NODESET** node1 val1 [ node2 val2 ]

This statement sets an initial guess voltage at the specified node for the dc operating point solution.



Initially nodesets work exactly the same way as initial conditions. The nodeset voltage is applied via a 1 Ohm (by default but can be changed using NODESETRES option - see [.OPTIONS\)](#page-250-0) resistor and the solution is completed to convergence (by any of the methods). The nodeset is then released and the solution repeated. If the nodeset voltage is close to the actual solution the convergence of the second solution should be rapid.

Nodesets can be used to force a particular solution for circuits that have more than one stable state. Consider the following circuit:



A nodeset has been applied to the collector of Q1. This has forced Q1 to be on and Q2 to be off. If the nodeset were absent the solution would actually leave both Q1 and Q2 partially on. In real life this would not be stable but it is numerically accurate.

The other application of nodesets is to help convergence for the DC bias point. With SIMetrix, it is rarely necessary to use nodeset's to find the DC solution of a circuit. They can, however, be useful for speeding up the operating point analysis for circuits that have already been solved. You may wish to do this for a Monte-Carlo analysis, for example. SIMetrix features a method of creating nodesets for this purpose using the SaveRhs command. See [Using Nodesets.](#page-322-0)

Nodeset's should not be confused with initial conditions. (see [.IC\)](#page-233-0). Initial conditions tie a node to a particular voltage and keep it there throughout the DC operating point analysis. Nodesets merely suggest a possible solution but do not force it.

## **6.21 .NOISE**

```
.NOISE inner_sweep_spec [ V ] pos_node [ VN ] neg_node
   + [[ INSRC ] in_source ]
   + [ F frequency ] [RUNNAME=runname] [SWEEP outer_sweep_spec]
Spice Compatible:
```

```
.NOISE V(pos_node [, neg_out_node ]) in_source
+ DEC|LIN|OCT num_points start stop interval
```
This statement instructs the simulator to perform a small signal noise analysis.



### **6.21.1 Notes**

During noise analysis the simulator calculates the total noise measured between *pos\_node* and *neg\_node* at each frequency point. It also calculates and outputs this noise referred back to an input specified by *in\_source*. As for all other analysis modes a DC operating point analysis is carried out first but, unlike AC analysis, the results of this analysis are not made available. The simulator outputs vectors covering the contribution from each noise generating device to the total output noise. The names of these vectors begin with the component reference of the device followed by a suffix to indicate the source of the noise within the device. A listing of the suffixes is given below. It is important to note that it is not the noise being generated by each device that is output but the proportion of that noise that is propagated to the output.

It is not necessary to specify a separate AC analysis alongside the noise analysis as it is with SPICE2 and commercial derivatives of SPICE2.

The magnitude of any AC independent voltage or current source on the circuit has no effect on the results of a noise analysis. Unlike SPICE and earlier versions of SIMetrix, it is not necessary to specify an AC parameter for the source used for the noise input source. For the first form shown above, the input source is in fact optional. If it is omitted the input referred noise will not be calculated.

All noise results are in  $V/$ √ Hz except input noise referred back to a current source which is in  $A/$ √ hich is in  $A/\sqrt{Hz}$ . In standard SPICE3 the noise values produced for MOS2 and BSIM3 devices are in  $V^2 / \sqrt{Hz}$ . For consistency, these have now been changed to  $V/\sqrt{Hz}$ . The original SPICE3 behaviour can be restored by setting the simulator option OldMosNoise (see [.OPTIONS\)](#page-250-0).





### **6.21.3 Creating Noise Info File**

Noise analysis generates vectors in the same way as all other swept analyses. Individual vectors may also be tabulated in the list file using the .PRINT statement.

A noise output file may also be created from the front end. Select the command shell menu Graphs and Data | Create Noise Output File to create a text file with a summary of noise results. Included is a list of the integrated noise output for every device listed in order of magnitude. Select Graphs and Data | View Noise Output File to view the file. Note that this is a front end feature and is not implemented by the simulator.

#### **6.21.4 Examples**

Run noise analysis from 100Hz to 1MHz with 25 points per decade. Calculate noise at node named vout and noise referred back to voltage source vin:

**.NOISE** V( vout ) vin dec 25 100 1meg

Decade sweep resistor RSource from 100 to 10K with 25 points per decade. Frequency =  $1kHz$ 

**.NOISE** DEVICE RSource DEC 25 100 10k F=1K

### **6.22 .OP**

#### **.OP**

This statement instructs the simulator to perform a DC operating point analysis. Note that a DC operating point analysis is carried out automatically for transient (unless the UIC parameter is specified), AC, DC, transfer function and noise analyses.

DC operating point analysis attempts to find a stable bias point for the circuit. It does this by first applying an initial guess and then uses an iterative algorithm to converge on a solution. If it fails to find a solution by this method the simulator then attempts three further strategies.

For the first, a method known as 'source stepping' is employed. For this all voltage and current sources in the circuit are initially set to near zero and the solution found. The sources are then gradually increased until they reach their final value.

If this approach fails a second strategy 'GMIN stepping' is invoked. This conditions the solution matrix by increasing the diagonal term such that it is dominant. If large enough, convergence is virtually guaranteed. If successful then the diagonal term is reduced and a further solution sought using the previous solution as a starting point. This procedure is repeated until the diagonal term is returned to its correct value. Increasing the diagonal term is in a way similar, but by no means identical, to placing a small resistance at each node of the circuit.

If source stepping fails a final strategy, 'pseudo transient analysis' is invoked. This is the most powerful technique employed and nearly always succeeds. However, it is also the slowest which is why it is left until last. For more information on DC convergence see [Convergence, Accuracy and Performance.](#page-318-0)

If the final approach fails then the analysis will abort.

IMPORTANT: *It is not necessary to include .OP if other analyses are specified*. All other analysis modes will perform an operating point anyway so including .OP will simply cause it to be done twice. However, with .NOISE, .TF, and .SENS the results of the operating point analysis are not output. If the bias point of the circuit is required when running one of these analysis modes, a .OP will be needed.

### **6.22.1 'OFF' Parameters**

Some semiconductor devices feature the device parameter OFF. If there are devices in the circuit which specify this parameter, the bias point solution is found in two stages. In stage 1 the devices with OFF specified are treated as if their output terminals are open circuit and the operating point algorithm completes to convergence. In stage 2, The OFF state is then released and the solution restarted but initialised with the results of stage 1.

The result of this procedure is that OFF devices that are part of latching circuits are induced to be in the OFF state. Note that the OFF parameter only affects circuits that have more than one possible DC solution such as bistables. If the OFF parameter is specified in - say - an amplifier circuit - with a unique solution, the final result will be the same. It will just take a little longer to arrive at it.

#### **6.22.2 Nodesets**

Nodesets work in a similar way to the OFF parameter in that the solution is found in two stages. In the first the nodeset is applied and the solution found. It is then released and convergence continues. Nodeset are an aid to convergence and, like the OFF parameter, can coerce a particular solution if there is more than 1 stable state. See [.NODESET](#page-244-0) for details.

### **6.22.3 Initial Conditions**

Initial conditions force a particular voltage at a circuit node during bias point solution. The force is released for any subsequent analysis. See [.IC](#page-233-0) for more details.

### **6.22.4 Operating Point Output Info**

During the operating point analysis, operating point values of every device in the circuit are output to the list file (see [The List File\)](#page-26-0). This information is not usually output for other analysis modes unless explicitly requested. The output of operating point information is controlled by three simulator options:



## <span id="page-249-0"></span>**6.23 .OPTIMISER**

```
.OPTIMISER
+ optparams=[parameter_names]
+ optinitvals=[initial_values]
+ [ optminvals=[minimum_values] ]
+ [ optmaxvals=[maximum_values] ]
+ alg=algorithm
+ [ abstol=absolute_tolerance]
+ [ reltol=relative_tolerance]
+ [ iterlim=iteration_limit]
+ [ schematic=schematic_file]
+ [ results_file=results_file]
+ [ show_progress]
```
Configures an optimiser session. Requires at least one analysis statement and one [.OPTSPEC statement](#page-271-0) to be present in the netlist. The .OPTIMISER statement defines the parameters, stop criteria and optimisation algorithm.

The.OPTIMISER statement may be used with multiple analysis statements. If only a single analysis statement is required it is also possible to use the multi-step analysis mode. For details see [Multi-step](#page-219-0) [Analysis](#page-219-0)

*parameter\_names* Names of parameters whose optimal value will be sought in the optimisation process. This is a list of names separated by commas. Parameters may be used in expressions to define model and instance parameters in exactly the same way as the .PARAM statement



# <span id="page-250-0"></span>**6.24 .OPTIONS**

#### **.OPTIONS** [ opt1 [=val1]] ...

This statement allows the setting of various options specific to the simulator.



## **6.24.1 List of simulator options**












































# **6.25 .OPTSPEC**



Defines a measurement to be made as part of an optimisation analysis. Any number of .OPTSPEC statements may be defined but there must be at least one.





## **6.26 Notes**

- There must be one and one-only objective function. That is an .OPTSPEC statement of type minimise or maximise
- There can be any number of constraint functions

# **6.27 .PARAM**

```
.PARAM parameter_name [=] parameter_value [parameter_name [=] parameter_value]...
.PARAM parameter_name [=] AGAUSS(nominal, abs_variation, sigma, [multiplier]) ...
.PARAM parameter_name [=] AUNIF(nominal, abs_variation, [multiplier]) ...
.PARAM parameter_name [=] GAUSS(nominal, rel_variation, sigma, [multiplier]) ...
.PARAM parameter_name [=] UNIF(nominal, rel_variation, [multiplier]) ...
```
Defines a simulation variable for use in an expression. Expressions may be used to define device parameters, to define model parameters, for arbitrary sources and to define variables themselves. See [Using Expressions](#page-32-0) for details.

The syntax for the first form is described below. For details of the remaining forms (using AGAUSS, AUNIF, GAUSS and UNIF) see [Hspice Distribution Functions.](#page-306-0)



### **6.27.1 Examples**

```
.PARAM Vthresh = 2.4
.PARAM Vthresh = \{ (Vhigh+Vlow) /2}
.PARAM F0 1k Alpha 1 C1 {2*c2}
.PARAM R1 {2/(2*pi*freq*C1*alpha}
```
#### **6.27.2 Netlist Order**

.PARAM statements that resolve to a constant are order independent; they can be placed anywhere in a netlist. They can even be placed after another .PARAM expression that depends on its value (but note this does *not* apply in subcircuits). .PARAM statements that are defined as an expression that depends on other .PARAMs also defined as an expression must be placed in sequential order. For example, the following is OK:

```
.PARAM C2 {C1*alpha*alpha/4}
.PARAM C1 1n
.PARAM alpha 1
.PARAM R1 {2/(2*PI*F0*C2*alpha}
```
The first .PARAM depends on alpha and  $c1$  which are defined later in netlist. This is OK (as long as it is *not* in a subcircuit) because icodealpha and  $C_1$  are constants. The fourth .PARAM depends on  $C_2$ , which is defined as an expression. The definition for must - and does in the above example - come before the definition of  $R1$ . The following would yield an error as the definition for  $C2$  comes after the definition of  $R1$ 

```
.PARAM R1 {2/(2*PI*F0*C2*alpha}
.PARAM C1 1n
.PARAM alpha 1
.PARAM C2 {C1*alpha*alpha/4}
```
Note that .PARAMs inside subcircuits are local to the subcircuit. This is explained in next section.

### **6.27.3 Subcircuit Parameters**

Parameters may be declared within sub circuits. E.g

```
.subckt ADevice n1 n2 n3 n4
.PARAM Vthresh 3.5
...
...
ends
```
In the above example, in reference to Vthresh within the subcircuit would use the value declared by the .PARAM declared inside the subcircuit. That value would not be available outside the subcircuit definition. Parameters may also be passed to subcircuits. E.g.

X1 1 2 3 4 ADevice : threshold=2.4

or

X1 1 2 3 4 ADevice **params**: threshold=2.4

Any reference to threshold within the subcircuit definition would use that value.

Default values for parameters may also be specified in subcircuit definition:

```
.subckt ADevice n1 n2 n3 n4 params: threshold=2.4
.ends
```
If that subcircuit is called without specifying threshold the default value of 2.4 will be used. Note that it is not compulsory to declare default values.

### **6.27.4 Using .PARAM in Schematics**

.PARAM statements may be appended to the netlist created by the schematic editor. For information on how to do this, refer to [Adding Extra Netlist Lines.](#page-17-0)

### **6.27.5 .PARAM in Libraries**

.PARAM statements may be included in libraries specified using .LIB or by global definitions. SIMetrix will search such libraries for any parameters used in expressions that are not found in the netlist.

# **6.28 .POST\_PROCESS**

**.POST\_PROCESS** scriptname [arguments]

Invokes the SIMetrix script *scriptname* at the end of a successful simulation. If present arguments will be passed to the script as a single string.

*scriptname* may the name of an embedded file defined using .FILE and .ENDF. For example, the following will cause the text "Simulation Complete" to be displayed in the command shell when the run is complete:

```
.FILE on_complete
Echo "Simulation Complete"
.ENDF
.POST_PROCESS on_complete
```
.POST\_PROCESS may be used to perform measurements on simulation results for display in the command shell or written to a file.

.POST\_PROCESS scripts will function even if the simulator is operating in a standalone mode in which case any displayed messages created from, for example, Echo or Show, will be directed to the simulator's output device. In console mode, this would be the console or terminal and in standalone GUI mode, this would be the message window in the simulator status box. As there is no environment available in the standalone mode, not all script commands and functions will be available.

For information about the SIMetrix script language, please refer to the SIMetrix script reference manual.

#### **6.28.1 Important Note**

When using .FILE and .ENDF with the SIMPLIS simulator, the text "SIMPLIS PASS THRU" must be placed at the end of the .FILE statement:

```
.FILE on_complete SIMPLIS_PASS_THRU
Echo "Simulation Complete"
.ENDF
.POST_PROCESS on_complete
```
## **6.29 .PRINT**

**.PRINT TRAN**|**AC**|**DC**|**NOISE**|**TF** vector|{expression} ...

Instructs the simulator to output selected simulation data to the list file in tabulated form.

Where:



### **6.29.1 Notes**

A traditional SPICE2 command, this was not supported by SIMetrix until release 4.0. It is SPICE2 compatible but also supports some additional features:

- NOISE and TF results may be output as well as TRAN, AC and DC
- You can put expressions as well as single values enclosed in '{' and '}'. E.g.

**.PRINT** TRAN {vout-q5\_c}

You can use the SPICE2 style method of accessing single voltages, differential voltages and device currents. These are of the form:

#### Single ended voltage

funcname(nodename)

#### Differential voltage

funcname(nodename, nodename)

#### Device current

funcname(device\_name)

#### Where:



Available functions:





.PRINT statements may be placed inside a subcircuit definition in which case the device and node names refer to local devices and nodes. Output will be listed *for every instance of the subcircuit.*

For transient analysis the results are displayed at the interval specified by the time step parameter on the .TRAN statement. If this is zero or omitted, it defaults to (tstop-tstart)/50. The data is created by interpolation unless the NORAW option (see [.OPTIONS\)](#page-250-0) is specified in which case a time step is forced at the time step interval.

### **6.29.2 Examples**

```
.PRINT TRAN V(VOUT)
.PRINT TRAN VOUT
.PRINT TRAN V(VPos, VNeg)
.PRINT TRAN {Vpos-VNeg}
.PRINT AC VDB(VOUT)
```
# <span id="page-276-1"></span>**6.30 .PROBE**

```
.PROBE
.PROBE list_of_vectors
```
*list\_of\_vectors* List of vector names in form V(*node*), I(*source*), I*pin*(*device\_name*) or W(*device\_name*)

.PROBE enables the creation of a PSpice-compatible .DAT file which can be used to interface with other tools that accept this format.

The name of the data file created is the same as the netlist but with a .DAT extension.

# <span id="page-276-0"></span>**6.31 .SENS**

**.SENS** V(nodename [,refnodename])| **I**(sourcename)

This statement instructs the simulator to perform a DC sensitivity analysis. In this analysis mode, a DC operating point is first calculated then the linearised sensitivity of the specified circuit voltage or current to every model and device parameter is evaluated. The results are output to the list file and they are also placed in a new data group. The latter allows the data to be viewed in the message window (type Display) at the command line and can also be accessed from scripts for further analysis.

The number format used in the list file can be controlled by the SENSUSEEXPFORMAT option. By default engineering format is used but this can be changed to exponential format with the setting:

**.options** SENSUSEEXPFORMAT

Instead of the results being written to the list file, they may alternatively be written to a text file using the SENSFILE option:

**.options** SENSFILE=<filename>

# <span id="page-277-0"></span>**6.32 .SETSOA**

```
.SETSOA [ LABEL=label ] [ MODEL=modelname | INST!=instname ] [DEVICE=device]
  [!DERATING=derating] [MEAN] [ ALLOWUNUSED ] [ ALLOWWILD ]
  expr1=( min1, max1[, xwindow1] ) [ expr2=( min2, max2[, xwindow2] ) ... ]
```
Defines a Safe Operating Area (SOA) specification. If SOA testing is enabled the simulator will check simulated results against this specification and record any violations. See [.OPTIONS](#page-250-0) setting SOAMODE for details on how to enable SOA tests.

The results of SOA testing are output to the list file by default and can optionally also be displayed in the command shell message window, or console window if run in non-GUI mode. They are also always available via a script function GetSOAResults(). See [.OPTIONS](#page-250-0) setting SOAOUTPUT for more details.



*expr1*, *expr2*... Expression to be evaluated and compared against minimum and maximum specs. This expression can access simulation results using access variables. The format and scope of these variables depends on whether MODEL, INST or neither is specified.

If neither is specified, the expression can use the global access variables defined below:

<b>Syntax</b>	<b>Function</b>	<b>Example</b>
nodename	Voltage on node	VOUT - voltage on node VOUT
n(nodename)	Voltage on node	$n(VOUT)$ - voltage on node <b>VOUT</b>
instname#param	Instance parameter	M2#vdsat - vdsat value for M2
		$Q23\text{\#c}$ - current in collector of O <sub>2</sub> 3
paramname	Parameter defined using .PARAM	
$\mathbf{r}$ . $\mathbf{r}$ , $\mathbf{r}$ , $\mathbf{r}$ , $\mathbf{r}$ , $\mathbf{r}$		

If there is a clash between a *paramname* and *nodename*, that is if the same name could refer to either a node or a parameter, then the parameter name takes precedence. To access the node in this case, use the n(*nodename*) syntax.

Use the following values if MODEL or INST is specified. In each case (excepting the global access variable) the variable accesses a quantity for the instance being processed. With INST this will be the single instance specified by *instname*. With MODEL all instance belonging to the model specified by *modelname* will be processed.



Note that currently the use of V() and I() is not accepted and will result in an error message being displayed.



### **6.32.1 Examples**

Test the voltage on the 'p' pin of R1. Will fail if it exceeds 0.5V

```
.setsoa INST=R1 vp=(*,0.5)
```
Test the power dissipation of R2. Fails if it exceeds 0.5mW

**.setsoa** INST=R2 pow=(\*,0.5m)

Test the current into pin 'p' of R3. Fails if it exceeds 0.5mA

**.setsoa** INST=R3 ip=(\*,0.5m)

Test the voltage across R4. Fails if it exceeds 0.85V for at least 100uS. Will be reported using label "%INST%, high", which resolves to "R4, high"

**.setsoa** LABEL="%INST%, high" INST=R4 vd=(\*,0.85,100u)

Test the voltage across R4. Fails if it exceeds 0.7V for at least 500uS

**.setsoa** LABEL="%INST%, low" INST=R4 vd=(\*,0.7,500u)

Tests voltage between 'c' and 'e' pins for all instances of model N1. Fails if voltage drops below -0.5V or exceeds 25V

**.setsoa** MODEL=N1 vce=(-0.5,25)

Tests power all devices of type resistor. Fails if this exceeds 0.25W.

**.setsoa** INST=\* ALLOWWILD DEVICE=resistor pow=(\*,0.25)

Tests the mean power in instance Q1. Fails if it exceeds "2\*bjtderating". "bjtderating" must be defined using a .PARAM statement.

```
setsoa LABEL="%INST%, pow(q1)" INST=Q1 MEAN pow=(*, 2)derating=bjtderating
```
Calculates the expression "n(c)\*(q1#c-d1#p)+n(b)\*q1#b+n(e)\*(q1#e+d1#p)" and fails if its mean exceeds 1.0. Violations will be reported using label "%SUBCKT%, power". Statement is intended to be placed in a subcircuit definition block and "%SUBCKT%" will resolve to the reference of the subcircuit call.

```
.setsoa LABEL="%SUBCKT%, power" MEAN "n(c)*(q1#cd1#
p) +n(b) *q1#b+n(e) * (q1#e+d1#p)" = (*,1)
```
# **6.33 .STEP**

```
.STEP [LIN] TEMP start stop step
.STEP DEC|OCT TEMP start stop steps_per_interval
.STEP [LIN] PARAM param_name start stop step
.STEP DEC|OCT PARAM param_name start stop steps_per_interval
.STEP [LIN] model_type model_name(model_parameter) start stop step
.STEP DEC|OCT model_type model_name(model_parameter) start stop steps_per_interval
.STEP [LIN] source start stop step
.STEP DEC|OCT source start stop steps_per_interval
```


The .STEP statement provides compatibility with other simulators and is not expected to be used for other purposes. Multi-step analyses would usually be defined using the SWEEP keyword on the same line as the analysis statement. See [Multi Step Analyses](#page-217-0) for further details.

.STEP defines a single level multi-step analysis and must be accompanied by an analysis statement (.dc, .ac, .tf, .noise or .tran).

### **6.33.1 Single Step Sweeps - Interaction with .PROBE**

.STEP can be used to define AC, NOISE and TF sweeps that sweep a variable other than frequency. It is neither necessary nor recommended to use .STEP to do this with SIMetrix, but it is the only way to achieve this in some other simulators.

For example, the following runs an AC analysis while sweeping he current source I1 at fixed 100kHz frequency:

```
.AC LIN 1 100k 100k
.STEP DEC I1 1u 100m 25
```
The AC analysis specifies just a single point at 100kHz while the .STEP statement varies I1 from 1u to 100m. In SIMetrix this will do exactly the same analysis as the following:

**.AC** DEVICE=I1 DEC 25 1u 100m F=100000

However, the .AC/.STEP analysis statements shown above will behave differently if a [.PROBE](#page-276-1) statement is present in the netlist. .PROBE enables the creation of a PSpice format .DAT data file. The .DAT format does not support swept variables other than frequency but does support multiple single point analyses. So if .PROBE is present the above .STEP/.AC combination will perform multiple single point AC analyses which will create compatible data in the .DAT file.

### **6.33.2 Examples**

Step voltage source VDC from 0 to 5 in 0.1 steps

**.STEP** VDC 0 5 0.1

Step parameter R1 from 1k to 10k in steps of 500

**.STEP** PARAM R1 1k 10k 500

Step temperature from 0 to 100C in 5C steps

**.STEP** TEMP 0 100 5

Step current source I1 from 1uA to 100mA logarithmically with 50 steps per decade

```
.STEP DEC I1 1u 100m 50
```
## **6.34 .SUBCKT and .ENDS**

```
.SUBCKT subcktname n1 [ n2 ]...
+ [ [params:] param_name1 [=] param_value1
+ [param_name2 [=] param_value2]...]
```
This statement begins a subcircuit definition.



IMPORTANT: Either the *params:* specifier or the first '=' may be omitted *but not both*. If both are omitted it becomes impossible for the netlist scanner to tell the difference between parameter names and node names.

```
.ENDS [ subcktname ]
```
Terminates a subcircuit definition. *subcktname* may be added for clarity but will be ignored by SIMetrix.

A subcircuit consists of a .subckt statement followed by a series of device or model descriptions and terminating in a .ends statement. A subcircuit is a circuit that can be called into the main circuit (or indeed another subcircuit) by reference to its name. The .subckt statement is used to define the subcircuit while a subcircuit call - an 'X' device - is used to create an instance of that subcircuit. Subcircuits have a number of uses:

- To repeat a commonly used section of circuit.
- To hide detail from the main circuit to aid circuit readability.
- To distribute models of integrated devices such as op-amps.

For a detailed discussion see [Subcircuits.](#page-46-0)

Subcircuit definitions usually reside in a text file and are read in as libraries. See *User's Manual* for further details.

## **6.35 .TEMP**

```
.TEMP temperature
```
This statement sets the default simulation temperature. Some devices can override this on a per instance basis. Units are degrees centigrade.

## **6.36 .TF**

```
.TF inner_sweep_spec [ V ] pos_out_node [ VN ] neg_out_node
+ [[ INSRC ] in_source ] [ F frequency ] [RUNNAME=runname]
 [SWEEP outer_sweep_spec ]
.TF inner_sweep_spec I source [ INSRC in_source ]
+ [ F frequency ] [RUNNAME=runname] [SWEEP outer_sweep_spec ]
```
#### Spice Compatible:

```
.TF V( pos_out_node [, neg_out_node ]) in_source
.TF I (source) [ INSRC ] in_source
```
This statement instructs the simulator to perform a small signal transfer function analysis.





### **6.36.1 Notes**

The SIMetrix transfer function analysis remains syntax compatible with the SPICE version but is substantially enhanced. The SPICE version performs the analysis at a single point with frequency = 0. The SIMetrix implementation performs a swept analysis using the same sweep algorithm used for AC, DC and NOISE.

Transfer function analysis is similar to AC analysis in that it performs a swept small signal analysis. However, whereas AC analysis calculates the response at any circuit node from a (usually) single input source, transfer function analysis calculates the individual responses from each source in the circuit to a single specified output node. This allows, for example, the series mode gain, common mode gain and power supply rejection of an amplifier to be measured in one analysis. The same measurements could be performed using AC analysis but several of them would need to be run. Transfer function mode also calculates output impedance or admittance and, if an input source is specified, input impedance.

The names of the output vectors will be of the form

```
Input voltage, output voltage
source_name#Vgain
Input voltage, output current
source_name#Transconductance
Input current, output voltage
source_name#Transresistance
Input current, output current
source_name#Igain
```
Output impedance for voltage out will be called Zout. For a current output, the output admittance will be calculated and will be named Yout.

If an input source is specified the input impedance will be calculated and called Zin.

Note that although the syntax for .TF retains compatibility with SPICE and earlier versions of SIMetrix, the output provided is slightly different. Firstly, the data is complex even if F=0 and secondly the names of the output vectors are different as detailed above.

#### **6.36.2 Examples**

SPICE compatible. Outputs results at DC.

**.TF** V(Vout) Vin

As above but decade sweep from 1k to 100k

**.TF** FREQ DEC 25 1K 100K V(Vout, 0) Vin

Note that in the above example the '0' in V(Vout, 0) is compulsory. If is omitted, Vin will be assumed as the reference node.

# **6.37 .TRACE**

**.TRACE** vector\_name [vector\_name ...] graph\_id

Set up a *trace*. This is graph plot that is updated as the simulation runs.

Where



*graph\_id* is an arbitrary number that makes it possible to direct traces to different graphs. Two traces with the same id will be always be put in the same graph. Traces from subsequent simulations with that id will also go to that graph if it still exists otherwise a new one will be created. To force two traces to go to separate graphs, use different id's. Note that it doesn't matter what the id's value actually is - it could be 1 or 100 - as long as traces that must go to the same graph use the same value.

Note that the *AutoAxis* feature available for normal plotting also works for Traces. So if a current and voltage trace are both directed to the same graph, separate axes will be created for them.

### **6.37.1 Examples**

```
.trace v1_p 1 q1#c 1
```
In the above example a voltage -  $v1_p$  - and a current - q1#c - will both be traced on the same graph. As they have different units, the AutoAxis feature will force the curves to two different y axes.

**.trace** v1\_p 1 q1#c 2

In this example the voltage and current traces will be directed to different graph sheets.

### **6.37.2 Notes**

The .TRACE statement has now been largely superseded by the .GRAPH statement (see [.GRAPH\)](#page-227-0), which is much more flexible. However, the .TRACE statement is still useful for specifying multiple traces on a single line. .GRAPH can only specify one signal at a time.

# <span id="page-285-0"></span>**6.38 .TRAN**

```
.TRAN tstop
```
#### OR

```
.TRAN tstep tstop [ tstart [ tmaxstep ]] [ UIC ]
+ [SNAPSTEP sstart sstop sstep]
+ [SNAPSHOT slist]
+ [SNAPMODE=DCOP|SAVESTATE|ALL]
+ [FAST=fast_start] [RTNSTEP=rtnstep [RTNSTOP=rtnstop]
+ [RTNSTART=rtnstart] [RTNMODErtnmode]
+ [RUNNAME=runname]
+ [PAUSEATEND]
+ [STARTUP=startuptime]
+ [SWEEP sweep_spec ]
```
This statement instructs the simulator to perform a transient analysis. In this mode the simulator computes the behaviour of the circuit over the specified time interval. The circuit's currents and voltages are calculated at discrete time points separated by a variable time step. This time step is adjusted automatically by the simulator according to circuit activity. The circuit may contain any number of time varying voltage and current sources (stimuli) to simulate external signals, test generators etc.





## **6.38.1 .OPTION settings**

Some transient parameters are set using the [.OPTIONS](#page-250-0) statement:



### **6.38.2 Fast Start**

If the FAST parameter is specified, the simulation will begin with a number of tolerances and internal parameters altered to speed up the simulation at the expense of accuracy. Just before the end of the fast start period, these tolerances and parameters will be gradually restored to their normal values. Fast start is an aid for simulating circuits such as switching power supplies and oscillators for which the initial start up period is not of interest but takes a long simulation time. Note that although the fast start interval can run sometimes as much as twice as quickly as normal, the fact that accuracy is impaired can mean that the final steady state reached may not be very accurate. This means that after the fast start period, an additional settling time may be required for full accuracy to be reached.

Fast start sets the values of POINTTOL and RELTOL according to the value specified by FASTPOINTTOL and FASTRELTOL respectively.

### <span id="page-287-0"></span>**6.38.3 Snapshots**

This feature allows the state of a simulation to be saved at user specified times during a transient analysis. The states saved can subsequently be reloaded to perform small signal AC analyses.
This allows the small signal response of a circuit to be examined at any point during a transient analysis. This is especially useful in situations where a circuit is found to be unstable in a transient run but this instability cannot be reproduced at the operating point usually derived for an AC analysis.

The bias point information at the snapshot time may also optionally be saved. This information is output to the list file.

To specify snapshot output, specify either the SNAPSHOT or SNAPSTEP keywords with their associated parameters.

To initialise a small signal analysis with snapshot data, you must specify the SNAPSHOT step mode of a multi-step analysis. See [Multi Step Analyses](#page-217-0) for details.

# **6.39 .VAR**

```
.VAR varname=value
.VAR varname={expression}
```
.VAR is used to define preprocessor variables. The preprocessor is tool that preforms netlist transformation prior to being presented to the simulator. It is not normally invoked for SIMetrix simulations but can be selctively applied to subcircuit models. For more information see [Subcircuit Preprocessing.](#page-48-0)

You can pass parameters to a subcircuit that define a vars: variable list. The values of those parameters can themselves refer to parameters define by .VAR.

The multi-level capacitor and inductor devices use the preprocessor and have a number of parameters such as QTY for quantity. Thes can be parameterised then defined using .VAR.

# **6.40 .VECALIAS**

.VECALIAS aliasname aliasvalue [ phystype ]

This statement creates an alias vector in the simulation data group. An alias vector is a string that represents an expression that resolves to some value. They are generated automatically in some simulations to represent currents in sub-circuit pins that are the sum of currents of connected devices. The .VECALIAS statement allows alias vectors to be created explicitly.



.VECALIAS is used by hierarchical models generated by the Netlist to Schematic converter

# **6.41 Real Time Noise Analysis**

This is an extension of transient analysis rather than a separate analysis mode. When activated, real time noise sources are added to all noisy devices with a magnitude and frequency distribution calculated using the same equations used for small signal analysis. This allows noise analysis to be performed on sampled data systems and oscillators.

To use real time noise analysis, the following parameters may be added to the .TRAN analysis line.



The parameters added to the .TRAN line *must* be named in the same way as .MODEL parameters are named.

#### **6.41.1 Example**

**.TRAN** 0 1m RTNstep=1u RTNstart=500u

Analysis time 1m, RTN step size 1u, real time sources start at 500u. The step size parameter - i.e. the first parameter on the .TRAN line - *must* be supplied if real time noise parameters are to be included. This is only to comply with the syntax rules not because the step size is needed for any other purpose. In most cases, just set it to zero as in the above example.

#### **6.41.2 Test Results**

To test real time noise and verify it's accuracy we ran a test on a number of circuits which compare AC noise with real time noise. The procedure was to run real time noise analysis 50 times then plot the averaged Fourier spectrum. This test was repeated for different transient run times and step sizes to build a noise spectrum over several decades. The graph below is the result of one such test. This was carried out on the BSIM3 buffer circuit provided in one of the examples except that a value for AF - the flicker noise parameter - was added to the models. As can be seen in the graph below the real time noise results strongly follow the AC noise results.

Similar tests were performed on circuits containing each of the major noise generating devices including diodes, BJTs, JFETs, resistors (including its flicker noise parameter) and also the NXP MOS9 and MEXTRAM devices. All showed results similar to below with a close similarity between AC noise and real time noise.



### **6.41.3 Real Time Noise Notes**

#### **Small-signal Noise**

Traditional noise analysis operates as a small-signal mode. This analysis mode is fast and provides detailed information about noise sources. However, small-signal noise has a number of drawbacks as follows:

- Small signal noise assumes small signal linear operation about a single operating point
- Small signal noise assumes the noise itself does not disturb the operating point significantly
- Small signal noise assumes the noise can be treated as independent of the signal
- It is often difficult or impossible to determine if the small-signal assumptions are valid

As a consequence, small-signal noise is not always an appropriate analysis method. It is usually inappropriate for mixers, switched capacitor circuits and sample-holds amongst others.

#### **Real Time Noise**

Real Time Noise is real noise in the time domain. Randomly generated noise signals are applied to noisy elements in the circuit. No small signal linear assumptions are made and this mode may be used to analyse noise for any type of circuit.

Real Time Noise is implemented by connecting PWL noise sources in place of noise sources used in small signal noise analysis and using same equations to set magnitude.

For example, the shot noise in a diode is modelled by a simple current source:



Each white noise source generates a PWL waveform where each point has a random value with a Gaussian distribution. The following picture shows a typical waveform:



The frequency distribution of the real time noise source can be determined by this equation:

$$
\left[\frac{\sin\left(\frac{\pi.f}{f_0}\right)}{\frac{\pi.f}{f_0}}\right]^2
$$

where f is frequency and  $f0 = 1/r$ tnstep

The following plot shows the distribution for a step size of 100ps



The above describes how white noise sources are implemented. It is also necessary to implement flicker noise which has a noise distribution that varies with frequency. This is done by summing multiple PWL sources with increasing step size.

#### **RTN Mode**

Noise sources are not fixed like regular signal sources. Their amplitudes vary according to device bias conditions. But they can be treated like regular signal sources provided their amplitude is determined and fixed at the start of each real-time noise step. While simple, this method can introduce serious errors in situations where the operating point changes substantially in a time less than the noise step. This is illustrated below:



When the switch in the above circuit switches off, its conductance falls dramatically, but the noise current is set according to the on-state. This introduces gross errors as shown above.

This problem can be overcome by ensuring that the noise source is modulated on each *time step* not just at each *noise step*. If we do this, the sources can no longer be considered as fixed as they are now interfering with the device operating point. This introduces an error in the calculation of the device's partial derivative which in turn can impair convergence. However, in practice the error is small and has never been identified as a problem.

Note that devices implemented from Verilog-A code do not suffer from the problem as the SIMetrix Verilog-A compiler automatically extracts the exact derivative.

The two alternative methods described above can be selected using the RTNMODE option. RTNMODE=1 is the fixed source option whereas RTNMODE=0 is the modulated source option.

# **Chapter 7**

# **Monte Carlo, Sensitivity and Worst-case**

## **7.1 Overview**

Monte Carlo analysis is a procedure to assess manufacturing yields by repeating simulation runs with varying applied random variations to component parameters.

Sensitivity analysis repeats runs while perturbing a single parameter for each step. This allows the sensitivity to that parameter of any number of measurements to be evaluated. This makes it possible to identify components and parameters that may require a tight tolerance to maintain a particular specification, or in some cases identify instabilities in the design.

Worst-case analysis attempts to find the combination of component and parameter variances which will lead to the worst possible result. It assigns each component or parameter with a value that is either at the positive extreme or the negative extreme. The decision as to which to use is obtained from the results of a prior sensitivity analysis using the sign of each sensitivity value.

Both Monte Carlo and worst-case may be used to assess production yield and reliability. For many applications, Monte Carlo produces the most realistic results but rarely locates the extremes that are theoretically possible even if statistically unlikely.

It should be noted that worst-case analysis is not guaranteed to locate the worst possible result. The algorithm assumes that the relationship between component or parameter variation and the measured result is linear. This is almost never the case in practice.

The implementation of these analysis modes in SIMetrix has been designed to be quick to set up for simple cases while still providing the required flexibility for more advanced requirements as might be required for integrated circuit design.

SIMetrix offers a high-degree of flexibility for tolerance specification. It is possible, for example, for different model parameters to be dependent on a single random variable. This makes it possible to model the fact that a number of model parameters might be dependent on a single physical characteristic, for example, the base width of a bipolar transistor. Of course, *lot* tolerances are also implemented accounting for the matching of devices in integrated circuits and other multiple components built onto a common substrate. However, in many products, lot tolerances can only be applied to the same type of device. In SIMetrix it is possible to model parametric relationships between different types of device which occur in integrated circuits but which are rarely taken into account.

As well as conventional multiple step Monte Carlo, sensitivity and worst-case analyses, single step sweeps may also be performed. These are available for the four swept modes, .AC, .DC, .NOISE and .TF. For example, a Monte Carlo analysis of the DC offset voltage of an amplifier can be performed using a single run of .DC using a special sweep mode. This is dramatically faster than the alternative of repeated .OP runs. This type of analysis can also be used to analyse the gain of an amplifier at a single frequency using .AC or .TF or even the noise, again at a single frequency, using .NOISE.

For sensitivity analysis, each point of an AC,DC, Noise or TF analysis would be a single perturbation case. This swept mode may be used, for example to find the sensitivity of an amplifier at a specified single frequency in a single run. For large circuits which have thousands of parameters, this can make sensitivity analysis practical when otherwise it might not be.

Note that the sensitivity analysis described in this chapter is not the same as the [.SENS](#page-276-0) DC sensitivity analysis. .SENS perturbs every parameter in the circuit and uses an approximate matrix based algorithm to determine DC sensitivity only.

# **7.2 Monte Carlo Analysis**

#### **7.2.1 Multi-step**

Monte Carlo runs are invoked in the same way as multi-step analyses (see [General Sweep Specification\)](#page-215-0). The basic syntax is:

```
.analysis_name analysis_parameters SWEEP MONTE num_runs NUMCORES=num_cores
```
Where:



#### **Examples**

Run 10 Monte Carlo runs for 1mS transient analysis

**.TRAN** 1m SWEEP MONTE 10

Run 1000 Monte Carlo steps for 1mS transient analysis using 4 processor cores. This will split the 1000 steps into 4 cores with each running 250 steps

**.TRAN** 1m SWEEP MONTE 1000 NUMCORES=4

100 Runs of a DC Sweep

**.DC** V1 0 5 0.01 SWEEP MONTE 100

AC sweep of voltage source V5 from -300mV to 300mV. Repeat 50 times

**.AC** DEVICE=V5 LIN 100 -300m 300m F=100000 SWEEP MONTE 50

#### **7.2.2 Single Step Sweep**

Monte Carlo sweep is one of the eight modes available to the swept analysis modes, .AC, .DC .NOISE and .TF. The other modes are explained in [General Sweep Specification.](#page-215-0) The general syntax is:

.analysis name **MONTE** num points analysis parameters

Where:



#### **Examples**

1000 point Monte Carlo sweep.

**.DC** MONTE 1000

AC Monte Carlo sweep 100 steps. Frequency  $= 10K$ . This is useful if - say - you are interested in the gain of an amplifier at one frequency and it needs to lie within a defined tolerance. The analysis defined by the following line will take very little time even for a large circuit.

```
.AC MONTE 100 F=10K
```
#### **7.2.3 Monte Carlo Log File**

Monte Carlo analysis generates an XML data file called an MSW file. (Monte Carlo, Sensitivity, Worst-case). The file contains the values of the parameters actually used in each run along with a seed value used to seed the random number generator.

The front-end can generate a user-readable HTML file from the MSW file.

The generation of the MSW file can be disabled with the NOMCLOG parameter on the analysis line. Note that with single-step sweeps, the generation of this file can significantly affect the overall simulation time.

The 'Seed' values displayed for each run at the top are the values used to seed the random number generator. These can be used to set the SEED option in order to repeat a particular random set. See below for more details.

#### **7.2.4 Seeding the Random Number Generator**

The random variations are created using a pseudo random number sequence. The sequence can be seeded such that it always produces the same sequence of numbers for a given seed. In Monte Carlo analysis, the random number generator is seeded with a new value at the start of each run and this seed value is displayed in the log file (see above). It is also possible to fix the first seed that is used using the SEED option. This makes it possible to repeat a run. To do this, note the seed value of the run of interest then add the line:

**.OPTIONS** SEED=seed\_value

For example if you wanted to repeat run 2 in the above example you would add this line:

**.OPTIONS** SEED=1521158126

The first run of each Monte Carlo analysis will use the same random values as run 2 above. Note this assumes that only changes in values are made to the circuit. Any topology change will upset the sequence.

## **7.3 Sensitivity and Worst-case Analyses**

#### **7.3.1 General Operation**

Sensitivity analysis repeats an analysis for each defined tolerance parameter. In each case the chosen parameter is perturbed by the tolerance range scaled by a fixed scaling parameter called "span". For example, a circuit which has four resistors with a 2% tolerance defined will run four times with each resistor perturbed in turn by +2% if span is set to 1.0.

One or more sensitivity measurement functions may be defined and these will be evaluated after the sensitivity analysis is completed. The results of evaluating these functions, along with the perturbation data is stored in an XML format data file, called the MSW file (Monte Carlo, Sensitivity, Worst-case). The MSW file is used as the input to a subsequent worst-case analysis and may also be used with front end tools to display sensitivity data such as deviation from nominal and normalised sensitivity values.

Although it usual to specify sensitivity measurement functions using .SENSMEAS statements in the simulation netlist, it is also possible at the script level to add the results of additional sensitivity measurements after the simulation has completed. This can be done with the AppendSensitivityData script function *Script Reference Manual/Function Reference/AppendSensitivityData*.

Worst-case analysis assumes that by setting each component or parameter at one or other extreme, that is either +tolerance or -tolerance, the worst possible result will be obtained. This isn't guaranteed to be the case, but this method does tend to locate results that are substantially outside the limits predicted by a Monte-Carlo analysis. To decide whether or not to use the +tolerance or -tolerance value, the results of a prior sensitivity analysis are used. The sign of the sensitivity to the sensitivity measurement function for each parameter is all that is needed.

Worst-case analysis also generates an MSW file that is used by the front-end to display a worst-case report.

Both Sensitivity and worst-case analyses may be run in both multi-step and single-step modes. Multi-step sensitivity and worst-case may be used with Transient, AC, DC, transfer function and noise analyses. Single-step sensitivity and worst-case may be used with AC, DC, transfer function and noise analyses.

#### <span id="page-297-0"></span>**7.3.2 Multi-step**

Sensitivity analyses and worst-case analyses are invoked in the same way as other multi-step analyses (see [General Sweep Specification\)](#page-215-0). As worst-case analyses depend on a prior sensitivity analysis, it is usual for both analysis specifications to be included together. In addition, at least one sensitivity measurement function will be required if both sensitivity and worst case are run together. See [Sensitivity Measurement](#page-299-0) [Functions.](#page-299-0)

The basic syntax for sensitivity and worst-case analysis is described below:

Sensitivity Analysis

```
.analysis_name analysis_parameters SWEEP SENS [SENSID sensid]
[SPAN span] [OUTFILE sens_outfile] [NUMCORES num_cores]
```
Worst-case Analysis

```
.analysis_name analysis_parameters SWEEP WC [SENSID sensid]
[INFILE sens_infile] [OUTFILE wc_outfile] [WCID wcid]
```


### **Examples**

Run a sensitivity analysis on a 200us transient analysis.

**.TRAN** 200u SWEEP SENS

Run a sensitivity and worst-case analysis on a 200us transient analysis. This would also need a sensitivity measurement function for the worst-case analysis to run. See [Sensitivity Measurement Functions](#page-299-0)

**.TRAN** 200u SWEEP SENS **.TRAN** 200u SWEEP WC

Run a DC sensitivity analysis followed by a worts-case analysis on DC sweep. Sensitivity uses a 0.1 span meaning that the sensitivity perturbation will be 10% of the tolerance of each parameter.

**.dc** v1 -100m 100m 2m SWEEP SENS span=0.1 **.dc** v1 -100m 100m 2m SWEEP WC

#### **7.3.3 Single Step Sweep**

Sensitivity and worst-case single-step sweep analyses run each case as a single point. This is distinct from a multi-step analysis which runs a complete multi-point analysis for each sensitivity case.

The basic syntax for single-step sensitivity and worst-case analysis sweeps is described below:

Sensitivity Analysis

.analysis\_name **SENS** [**SENSID** sensid] [**SPAN** span] [**OUTFILE** sens\_outfile] analysis\_parameters

Worst-case Analysis

```
.analysis_name WC [SENSID sensid] [INFILE sens_infile] analysis_parameters
[OUTFILE wc_outfile] [WCID wcid]
```
See [Multi-step sensitivity](#page-297-0) for details of the meaning of the above parameters.

#### **Examples**

Run a sensitivity on an AC analysis at 1Meg frequency

**.AC** SENS F=1000000

As above but also run a worst-case analysis. Note this will also need a sensitivity measurement function.

```
.AC SENS F=1000000
.AC WC F=1000000
```
#### <span id="page-299-0"></span>**7.3.4 Sensitivity Measurement Functions**

A Sensitivity measurement function defines a quantity whose sensitivity to circuit parameters is to be measured. Any number of sensitivity measurement functions may be defined. The results of the function evaluation is stored in a datafile that sensitivity analyses always generate. This datafile, in XML format, is used as the input to worst-case analysis and also as input to front end tools that can display the final sensitivity data.

The syntax for each sensitivity measurement function is as follows:

```
.SENSMEAS id expression
```
*id* identifier corresponding to the sensid parameter defined for sensitivity analyses or wcid parameter for worst-case analyses. Usually this is set to one of the defaults defined for each analysis type. These are listed in [Multi-step Sensitivity.](#page-297-0) *expression* Expression to evaluate. For multi-step analyses this must be a function that returns a scalar measurement from a vector. For example the Mean1() function returns the mean of a vector. For single step analyses, this would usually simply be the name of a vector - e.g. VOUT with no function applied as the measurement for each case is a single element of the vector. For AC analyses it will be necessary to apply a complex-real conversion function such as mag(),  $db$ (), phase, re() or im()

# **7.4 Specifying Tolerances**

#### **7.4.1 Overview**

Monte Carlo, sensitivity and worst-case analyses require tolerances to be specified for one or more component parameters. Monte Carlo will apply a random value to the parameter that satisfies the tolerance specification. Sensitivity analysis will perturb the parameter at the positive tolerance value scaled by the span parameter. Worst-case analysis will perturb each parameter at either the positive tolerance extreme or the negative tolerance extreme according to the results obtained from a prior sensitivity analysis.

Tolerances for Monte Carlo, sensitivity and worst-case analyses may be specified by one of the following methods:

- 1. Using a distribution function in an expression.
- 2. Using the device parameters TOL, MATCH and LOT

Method 1 above is the most general and flexible. TOL, MATCH and LOT parameters are provided primarily for backward compatibility but may also be more convenient in some circumstances.

#### <span id="page-300-0"></span>**7.4.2 Distribution Functions**

To specify the tolerance for a model or device parameter, define the parameter using an expression (see [Using Expressions\)](#page-32-0) containing one of the following functions:



Each of the above functions takes a single argument that specifies the tolerance. The return value is 1.0 +/ tolerance with the exception of GAUSS and GAUSSL. See [Gaussian Distributions](#page-303-0) for details. In analyses other than Monte Carlo, sensitivity or worst-case, all of the above return unity.

The graphs below show the characteristics of the various distributions. The curves were plotted by performing an actual Monte Carlo run with 100000 steps. Note that with sensitivity and worst-case analyses, only the extreme values defined by the tolerance are used.







UNIF



WC

### **User Defined Distribution**

Customised distributions may be defined using the Distribution2 function (or its alias UD2).

Distribution2 may take any number of arguments defined as follows:



Custom distributions can be conveniently defined using the [.FUNC](#page-226-0) function definition statement. For example, the following defines a binomial distribution:

**.FUNC** binomial(a) = {distribution2(a, -1,1, -0.5,1, -0.5,0, 0.5,0, 0.5,1, 1,1)}

The function 'binomial()' can subsequently be used in the same way as other distribution functions. This would have a distribution as shown in the following graph:



#### <span id="page-303-0"></span>**Gaussian Distributions**

The standard Gaussian distribution functions (GAUSS(), GAUSSL()) return a random variable with a true Gaussian distribution where the tolerance value represents the  $3\sigma$  spread. This can return values that are outside the tolerance specification albeit with low probability. For example GAUSS(0.1) can return values >1.1 and less than 0.9 as defined by the Gaussian distribution. For specifying actual components this is not usually exactly correct as most components are tested at production and devices outside the specified tolerance will be rejected.

This type of component can instead be specified using the GAUSSTRUNC() distibution function. This rejects values outside the specified range expressed as a multiple of  $\sigma$ . Syntax for the GAUSSTRUNC() function is:

GAUSSTRUNC(tolerance, sigma\_multiplier)

Where:



Use the GAUSSIGMA functions if you need to specify a non-truncated Gaussian distribution with a spread that is other than  $3\sigma$ . For Monte Carlo analysis GAUSSSIGMA(tol, sigma) is equivalent to GAUSS(tol/sigma\*3) but GAUSS(tol/sigma\*3) will not give the correct range of values for sensitivity and worst case analyses. In sensitivity and worst case analyses, GAUSSSIGMA(tol,sigma) is equivalent to GAUSS(tol).

#### **Examples**

Apply 50% tolerance to BF parameter of BJT with gaussian distribution.

```
.MODEL NPN1 NPN IS=1.5e-15 BF={180*GAUSS(0.5)}
```
A production tested 4.7K $\Omega$  2% resistor with a 3 $\sigma$  distribution:

```
R1 n1 n2 {4.7K*GAUSSTRUNC(0.1,3)}
```
#### **Lot Tolerances**

The *lot* versions of the functions specify a distribution to be applied to devices whose tolerances track. These functions will return the same random value for all devices that reference the same model.

Note that the same effect as LOT tolerances can be achieved using random variables and subcircuits. For details see [Creating Random Variables](#page-305-0)

#### **Lot Tolerance Examples**

Specify 50% uniform lot tolerance and 5% gaussian device tolerance for BF parameter

**.MODEL** NPN1 NPN IS=1.5E-15 BF={180\*GAUSS(0.05)\*UNIFL(0.5)}

Here is an abbreviated log file for a run of a circuit using 2 devices referring to the above model:



For the four runs BF varies from 91 to 245 but the two devices never deviate from each other by more than about 2.7%.

#### **Notes**

The tracking behaviour may not be as expected if the model definition resides within a subcircuit. When a model is defined in a subcircuit, a copy of that model is created for each device that calls the subcircuit. Here is an example:

```
XQ100 VCC INN Q100_E 0 NPN1
XQ101 VCC INP Q101_E 0 NPN1
.SUBCKT NPN1 1 2 3 SUB
Q1 1 2 3 SUB N1
Q2 SUB 1 2 SUB P1
.MODEL N1 NPN IS=1.5E-15 BF=\{180*GAUSS(0.05)*UNIFL(0.5)\}.ENDS
```
In the above, XQ100 and XQ101 *will not track*. Two devices referring to N1 *inside* the subcircuit definition would track each other but different instances of the subcircuit will not. To make XQ100 and XQ101 track, the definition of N1 should be placed outside the subcircuit. E.g.

```
XQ100 VCC INN Q100_E 0 NPN1
XQ101 VCC INP Q101_E 0 NPN1
.SUBCKT NPN1 1 2 3 SUB
Q1 1 2 3 SUB N1
```

```
Q2 SUB 1 2 SUB P1
.ENDS
.MODEL N1 NPN IS=1.5E-15 BF={180*GAUSS(0.05)*UNIFL(0.5)}
```
### <span id="page-305-0"></span>**Creating Random Variables**

It is possible to place distribution functions in .PARAM expressions to create a random variable. This provides a means of describing a relationship between different devices or different parameters within the same device.

Random variables may be created at the top level in which case they will be global and have the same value wherever they are used. Random variables may also be created inside subcircuit definitions. In this case they are local to the subcircuit and will have the same value for all devices and parameters *within* the subcircuit but a different value for different instances of the subcircuit.

Example 1 In this example we make a BJT model using a subcircuit. The random variable is created inside the subcircuit so will have the same value for parameters defined in the subcircuit but will have different values for multiple instances

```
.subckt NPN1 c b e
\textbf{PARAM} \text{rv1} = UNIF(0.5)
Q1 c b e NPN1
.MODEL NPN1 NPN BF={rv1*180} TF={1e-11*rv1}
.ends
```
For all devices using that model, BF and TF will always have a fixed relationship to each other even though each parameter can vary by +/-50% from one device to the next.

Here is the log of a run carried out on a circuit with two of the above devices:

```
Run 1 Run 2
Run 1: Seed=1651893287
Run 1
Device Nom. Value (Dev.)
Q1.Q1:bf 180 148.83033746 (-17.3164792%)
Q1.Q1:tf 10p 8.268352081p (-17.3164792%)
Q2.Q1:bf 180 129.69395145 (-27.9478048%)
Q2.Q1:tf 10p 7.205219525p (-27.9478048%)
Run 2: Seed=763313972
Run 2
Device Nom. Value (Dev.)
Q1.Q1:bf 180 265.86053442 (47.7002969% )
Q1.Q1:tf 10p 14.77002969p (47.7002969% )
Q2.Q1:bf 180 186.41647487 (3.564708261%)
Q2.Q1:tf 10p 10.35647083p (3.564708261%)
```
Notice that the BF and TF parameters always deviate by exactly the same amount for each device. However, the two devices do not track each other. If this were needed we would define the random variable outside the subcircuit at the netlist's top level:

```
\textbf{PARAM} \text{rv1} = \text{UNIF}(0.5).subckt NPN1 c b e
Q1 c b e NPN1
.MODEL NPN1 NPN BF = \{rv1*180\} TF = \{1e-11*rv1\}.ends
```
Here is the log for the above:

```
Run 1: Seed=1608521901
Run 1
Device Nom. Value (Dev.)
Q1.Q1:bf 180 249.54358268 (38.63532371%)
Q1.Q1:tf 10p 13.86353237p (38.63532371%)
Q2.Q1:bf 180 249.54358268 (38.63532371%)
Q2.Q1:tf 10p 13.86353237p (38.63532371%)
Run 2: Seed=80260241
Run 2
Device Nom. Value (Dev.)
Q1.Q1:bf 180 116.33087232 (-35.3717376%)
Q1.Q1:tf 10p 6.46282624p (-35.3717376%)
Q2.Q1:bf 180 116.33087232 (-35.3717376%)
Q2.Q1:tf 10p 6.46282624p (-35.3717376%)
```
#### **7.4.3 Hspice Distribution Functions**

SIMetrix supports the Hspice method of defining tolerances. This feature needs to be enabled with an option setting; see [Enabling Hspice Distribution Functions.](#page-307-0) The Hspice method uses random variables created using a special .PARAM syntax in one of the following form:

```
.PARAM parameter_name [=] AGAUSS(nominal, abs_variation, sigma, [multiplier]) ...
.PARAM parameter_name [=] AUNIF(nominal, abs_variation, [multiplier]) ...
.PARAM parameter_name [=] GAUSS(nominal, rel_variation, sigma, [multiplier]) ...
.PARAM parameter_name [=] UNIF(nominal, rel_variation, [multiplier]) ...
```
Where:



Random variables created using the above method do not behave in the same way as regular parameters created using the native SIMetrix distribution functions. They actually behave like function calls and return a different value *each time they are used*. Random variables created using .param and a native distribution function are evaluated just once and always return the same value. Internally, the above are implemented using a .FUNC definition to define a function with no arguments.

For example, the following are both quite legal:

**.PARAM**  $rv1 = UNIF(10,1)$ **.PARAM**  $rv2 = 'UNIF(10,1)'$  The first (rv1) will provide a nominal value 10.0 +/- 1.0 with a new value calculated each time it is used. The second (rv2) is a native SIMetrix distribution function, will produce a value varying from -9.0 to +11.0 and will always have the same value. With the above definitions for rv1 and rv2, consider the following regular .PARAM statements:

```
PARM \text{ rand1} = rv1.PARAM rand2 = rv1PARAM rand3 = rv2.PARAM rand4 = rv2
```
rand1 and rand2 will have *different* values. rand3 and rand4 will have the same values.

#### <span id="page-307-0"></span>**Enabling Hspice Distribution Functions**

Hspice distribution functions need to be enabled with an option setting as follows:

**.OPTIONS** MCHSPICE

This setting also has the same effect:

**.OPTIONS** HSPICECOMPATIBILITY=1

Important: This option also changes the way Monte Carlo sensitivity and worst-case analyses operate in a fundamental way by disabling *model spawning*. This is a process which gives each instance its own separate copy of its model parameters and allows 'dev' (or 'mismatch') tolerances to be implemented. Without *model spawning* dev tolerances cannot be implemented except by giving every instance their own copy of a model.

With the Hspice method this can only be done easily by wrapping up .MODEL statements inside a .SUBCKT definition. Each instance will then effectively get its own .MODEL statement and mismatch parameters can be defined.

#### **7.4.4 TOL, MATCH and LOT Device Parameters**

These parameters may be used as a simple method of applying tolerances to simple devices such as resistors. The TOL parameter specifies the tolerance of the device's value. E.g.

```
R1 1 2 1K TOL=0.05
```
The above resistor will have a tolerance of 5% with a gaussian distribution by default. This can be changed to a uniform distribution by setting including the line:

**.OPTIONS** MC\_ABSOLUTE\_RECT

in the netlist.

Multiple devices can be made to track by specifying a LOT parameter. Devices with the same LOT name will track. E.g.

```
R1 1 2 1K TOL=0.05 LOT=RES1
R2 3 4 1k TOL=0.05 LOT=RES1
```
R1 and R2 in the above will always have the same value.

Deviation between tracking devices can be implemented using the MATCH parameter. E.g.

R1 1 2 1K TOL=0.05 LOT=RES1 MATCH=0.001 R2 3 4 1k TOL=0.05 LOT=RES1 MATCH=0.001

R1 and R2 will have a tolerance of 5% but will always match each other to 0.1%. MATCH tolerances are gaussian by default but can be changed to uniform by specifying

**.OPTIONS** MC\_MATCH\_RECT

The default distributions for tolerances defined this way are the logarithmic versions as described in [Distribution Functions.](#page-300-0) To use a linear distribution, add this statement to netlist (or F11 window in the schematic editor):

**.OPTIONS** mcUseLinearDistribution

If using device tolerance parameters, note that any absolute tolerance specified must be the same for all devices within the same lot. Any devices with the same lot name but different absolute tolerance will be treated as belonging to a different lot. For example if a circuit has four resistors all with lot name RN1 but two of them have an absolute tolerance of 1% and the other two have an absolute tolerance of 2%, the 1% devices won't be matched to the 2% devices. The 1% devices will however be matched to each other as will the 2% devices. This does not apply to match tolerances. It's perfectly OK to have devices with different match tolerances within the same lot.

# **Chapter 8**

# **Optimisation**

## **8.1 Introduction**

Optimisation is the process of adjusting a design in order to maximise or minimise some measured characteristic, for example, power consumption or bandwidth. The SIMetrix simulator includes an optimisation feature that will perform this process automatically once the characteristic to be optimised (the 'objective function') has been defined along with the parameters that may be varied during the optimisation process. In addition, any number of constraints may also be defined. A constraint is an inequality relationship to define some measurement to be above or below a specified value. For example, the objective function might be to minimise power consumption (the objective) of an amplifier but retaining a minimum bandwidth and maximum noise factor (the constraints).

The SIMetrix optimiser operates in the simulator process and an optimisation analysis maybe defined entirely in the netlist. The SIMetrix GUI has additional features to help set up an optimisation analysis and view the results.

# **8.2 Optimiser Modes**

The SIMetrix simulator can run an optimisation analysis in two different ways.



#### **8.2.1 Single analysis mode**

The syntax for the single-analysis mode is described in the [Multi-step Analysis](#page-219-0) reference.

In addition to the analysis statement, all optimiser analyses must define at least one [.OPTSPEC](#page-271-0) statement. An .OPTSPEC statement defines the objective function, that is the function that is to be maximised or minimised and may also define constraints.

See the following section for an example that demonstrates this mode of operation.

#### **8.2.2 Single analysis mode - Example**

The following example extracts the parameters of a diode model to an I-V curve obtained from a data sheet. The diode's data is defined using the [.DATA](#page-222-0) statement.

#### Here is the complete listing:

```
V1 V1_P 0 5
D1 V1_P 0 DUT
.model DUT d RS={RS} IS=1e-8 IKF={IKF} N={N}
.TEMP 100
** This is called by .post_process and plots the final result
.file finish
      Let data = Diode data
      ** Plot reference
      plot /ylog /xlog /name Target data
      Let res = OptimiserSimulatorResults()
      Let bestIndex = res[2]-1curve /name "Best fit" d1#p[bestIndex]
.endf
.post_process finish
.dc v1 400m 1.4 100m analysis_id=dc_0 sweep opt
+ optparams=[RS,IKF,N]
+ optinitvals=0.01,0.1,1
+ optminvals=1e-06,0.001,0.1
+ alg=NELDER_MEAD
+ abstol=1e-09
+ reltol=0.001
+ show_progress
+ results_file="diode-test_results.sxopt"
.optspec measure="CurveFitLog(Diode_data,d1#p)" type=minimise analysis_id=dc_0
.data Diode_data format=XY
+ 0.2 0.017530716724236
+ 0.254901960784314 0.0357202832826342
+ 0.309803921568627 0.0727830275203565
+ 0.364705882352941 0.14827729430306
+ 0.419607843137255 0.299668595377245
+ 0.474509803921569 0.589675601217673
+ 0.529411764705882 1.10904794310676
+ 0.584313725490196 1.97923148874408
+ 0.63921568627451 3.35105785726025
+ 0.694117647058824 5.38251036969293
+ 0.749019607843137 8.20132439386704
+ 0.803921568627451 11.8538062030208
+ 0.858823529411765 16.2514356239684
+ 0.913725490196078 21.1880160385802
+ 0.968627450980392 26.4796478563484
+ 1.02352941176471 31.9973234288307
+ 1.07843137254902 37.7095034055593
+ 1.13333333333333 43.7173003655197
+ 1.18823529411765 50.1648407603598
+ 1.24313725490196 57.1465442469968
+ 1.29803921568627 64.8085898417056
+ 1.35294117647059 73.3707911567976
+ 1.4078431372549 83.0553217690679
+ 1.46274509803922 94.0181558001952
+ 1.51764705882353 106.428022091678
+ 1.57254901960784 120.475920740442
+ 1.6 128.180625221171
```
The actual circuit is defined by the first 4 lines. The .file/.endf and .post\_process statements define a post processing script that plots the final result on completion.

#### **Analysis and Optimiser Definition**

The optimiser analysis is defined by these lines:

```
.dc v1 400m 1.4 100m analysis_id=dc_0 sweep opt
+ optparams=[RS,IKF,N]
+ optinitvals=0.01,0.1,1
+ optminvals=1e-06,0.001,0.1
+ alg=NELDER_MEAD
+ abstol=1e-09
+ reltol=0.001
+ show_progress
+ results_file="diode-test_results.sxopt"
.optspec measure="CurveFitLog(Diode_data,d1#p)" type=minimise analysis=dc_0
```
The first line starts:

**.dc** v1 400m 1.4 100m

and defines a DC sweep which sweep V1 from 0.4V to 1.4V in steps of 0.1V.

analysis\_id=dc\_0

defines the analysis id. This is important as it links the analysis statement to a corresponding .OPTSPEC statement. .OPTSPEC statements make measurements but need to know which analysis data to apply it to. This is the purpose of the analysis\_id parameter. The value used is arbitrary.

sweep opt

defines an optimiser analysis

```
+ optparams=[RS,IKF,N]
+ optinitvals=0.01,0.1,1
+ optminvals=1e-06,0.001,0.1
```
define the parameters. The first line defines the parameter names and these work the same way as parameters defined using .PARAM. optinitvals is compulsory and defines the values the optimiser will use for the first run. optminvals sepcifies the minimum values that the optimiser will use for those parameters. This is optional. There is also optmaxvals which defines the maximum values allowed. The optimiser will not set the parameters to values outside those specs.

```
+ alg=NELDER_MEAD
```
defines the optimisation algorithm. See [Algorithms](#page-316-0) for more information.

```
+ abstol=1e-09
+ reltol=0.001
```
are stop criteria. abstol specifies an absolute tolerance for the change in objective function. The exact interpretation of the tolerance parameters depends on the algorithm, but typically when the objective function improvement between iterations is less than abstol, the optimiser analysis will complete. For reltol the optimisation analysis completes when the relative value between iterations falls below the reltol value.

```
+ show_progress
```
Instructs the optimiser to write a message for each iteration. The message will be written to the display device. When running in GUI mode, this is the front end's command shell. If running from a command prompt, this is the command prompt window.

+ results\_file="diode-test\_results.sxopt"

This specifies the results file. The results file is an XML file that contains the entire specification of the optimisation analysis along with the full results.

#### **Objective Function Definition**

**.optspec** measure="CurveFitLog(Diode\_data,d1#p)" type=minimise analysis\_id=dc\_0

This line defines the objective function. Objective functions have the  $t_{\text{vpe}}$  parameter set to minimise or maximise and there must be one and one-only objective function for an optimiser analysis. The measure parameter defines the expression which is evaluated and in this case minimised.  $\text{CurrentLog}$  is a function which compares two vectors and returns a normalised value representing the difference between the two vectors. 0 means they are identical. 1.0 will be returned if one curve is the exact reciprocal of the other. CurveFitLog is one of a family of functions, the others are CurveFit, CurveFitLogX and CurveFitLogY. For full documentation see *Script Reference Manual/Function Reference/CurveFit*.

analysis\_id=dc\_0 defines the analysis that the measurement is associated with and must match up with an analysis\_id parameter defined in an analysis statement. In this case it is the **.DC** analysis defined above.

Diode\_data refers the **.DATA** statement that defines the reference curve we are attempting to match.

#### **8.2.3 Multi-analysis Mode**

The multi-analysis optimiser mode is defined using the [.OPTIMISER](#page-249-0) statement. The .OPTIMISER statement defines the optimiser configuration but also needs at least one additional analysis statements such as [.TRAN](#page-285-0) or [.AC.](#page-220-0)

In addition to the .OPTIMISER statement and analysis statements, all optimiser analyses must define at least one [.OPTSPEC](#page-271-0) statement. An .OPTSPEC statement defines the objective function, that is the function that is to be maximised or minimised and may also define constraints.

#### **8.2.4 Multi-analysis Mode - Example**

The following is a direct netlist only version of the amp-700 example shown in the User's Manual. This is a bipolar transistor differential amplifier. Its behaviour is governed by four parameters that decide the values of a number of resistors in the design. Our objective is to minimise its power consumption while maintaining a minimum bandwidth, gain and signal distortion.

The complete netlist is shown below:

```
** Differential amplifier
** Circuit definition
V1 V1_P 0 0 AC 1 0 Sin(0 500m 500k 0 0)
V2 0 R11_N 15
R1 R1_P 0 1K
V3 V3_P 0 15
R2 R8_N R11_N 5k
R3 Q2_E R3_N {Rtail}
R4 V3_P R4_N {Rcoll}
R5_V3_P R5_N {Rcoll}
R6 Q3_E R3_N {Rtail}
R7 Q1_E R11_N {Rcurr}
R8 0 R8_N 50k
R9 R9_P V1_P 1K
R10 VOUT 0 10k
R11 Q7_E R11_N 100
R12 V3_P R12_N {Routput}
R13 V3_P R13_N {Routput}
R14 Q4_E R11_N 100
Q1 R3_N R8_N Q1_E 0 N1
Q2 R4_N R1_P Q2_E 0 N1
Q3 R5_N R9_P Q3_E 0 N1
Q4 VOUT Q5_C Q4_E 0 N1
Q5 Q5_C R5_N R12_N 0 P1
Q6 VOUT R4_N R13_N 0 P1
```

```
Q7 Q5_C Q5_C Q7_E 0 N1
.MODEL N1 NPN IS=3.8E-16 BF=220 BR=0.7
+ ISE=1.8E-16 IKF=1.7E-2 NK=0.75 IKR=3E-2 NE=1.4 VAF=60
+ VAR=7 RC=63.4 RB=300 RE=19.7 XTB=1.17 XTI=5.4
+ TF=1.5E-10 TR=6E-9 XTF=0.3 VTF=6 ITF=5E-5 CJE=0.21E-12
+ MJE=0.33 VJE=0.7 ISC=5E-12 KF=2E-13 AF=1.4
.MODEL P1 PNP IS=1E-15 BF=100 CJE=0.175E-12 XTI=5.4
+ MJE=0.38 VJE=0.6
** OPTIMISER Definition
.optimiser
+ optparams=[rcurr,rtail,rcoll,routput]
+ optinitvals=[1000,1000,10000,10000]
+ optminvals=[50,50,100,100]
+ optmaxvals=[20000,20000,50000,50000]
+ alg=COBYLA
+ abstol=1e-09
+ reltol=0.001
+ iterlim=25
+ results_file="amp-700_results.sxopt"
+ show_progress
** AC Analysis
.ac dec 25 1k 1000000000 analysis_id=ac_0
** Transient analysis
.tran 0 10u 0 10n analysis_id=tran_1
** .OPTSPEC definitions
** Objective function
.optspec
+ measure="-(v3#p+v2#p)"
+ type=minimum
+ analysis_id=ac_0
+ op
+ label="Supply_current"
** Constraint functions
.optspec
+ measure="lpbw(vout, 3)"
+ type=constraint_minimum
+ analysis_id=ac_0
+ value=2.5e+08
+ label="Bandwidth"
.optspec
+ measure="yatx(db(vout),1meg)"
+ type=constraint_minimum
+ analysis_id=ac_0
+ value=20
+ label="Gain_at_1meg"
.optspec
+ measure="MeasureDistortion(vout)"
+ type=constraint_maximum
+ analysis_id=tran_1
+ value=0.01
```

```
+ label="Distortion"
```
Two analyses are defined: an AC frequency sweep and a transient analysis. The AC sweep is used to measure the gain and frequency response and the transient analysis is used to measure the distortion. The current consumption is measured using the operating point analysis that is part of the AC analysis mode.

The following paragraphs explain the optimiser definition found in the above netlist.

#### **Optimiser Definition**

#### **.optimiser**

- + optparams=[rcurr,rtail,rcoll,routput]
- + optinitvals=[1000,1000,10000,10000]
- + optminvals=[50,50,100,100]
- + optmaxvals=[20000,20000,50000,50000]
- + alg=COBYLA
- + abstol=1e-09
- + reltol=0.001
- + iterlim=25
- + results\_file="amp-700\_results.sxopt"
- + show\_progress

#### The first parameter:

```
+ optparams=[rcurr, rtail, rcoll, routput]
```
Defines the names of the parameters. These work in the same way as parameters defined using [.PARAM.](#page-272-0) The next line:

```
+ optinitvals=[1000,1000,10000,10000]
```
is compulsory and defines the values the optimiser will use for the first simulator run. The values are in the same order as the parameter names. The next two lines:

```
+ optminvals=[50,50,100,100]
+ optmaxvals=[20000,20000,50000,50000]
```
define minimum and maximum limits for the parameters. The optimiser will not use values outside those limits.

+ alg=COBYLA

Defines the algorithm to be used. See [Algorihms](#page-316-0) for more information. The lines:

```
+ abstol=1e-09
+ reltol=0.001
+ iterlim=25
```
define stop criteria. The optimisation process will complete when one of those criteria is met. abstol specifies an absolute tolerance for the change in objective function. The exact interpretation of the tolerance parameters depends on the algorithm, but typically when the objective function improvement between iterations is less than abstol, the optimiser analysis will complete. For reltol the optimisation analysis completes when the relative value between iterations falls below the reltol value. iterlim defines the maximum number of iterations; when the iteration count exceeds this value, the optimiser will stop.

+ results\_file="amp-700\_results.sxopt"

This specifies the results file. The results file is an XML file that contains the entire specification of the optimisation analysis along with the full results.

+ show\_progress

Instructs the optimiser to write a message for each iteration. The message will be written to the display device. When running in GUI mode, this is the front end's command shell. If running from a command prompt, this is the command prompt window.

#### **Analysis statements**

```
.ac dec 25 1k 1000000000 analysis_id=ac_0
.tran 0 10u 0 10n analysis_id=tran_1
```
The above are analysis statements. For details see [.AC](#page-220-0) and [.TRAN.](#page-285-0) The important part for optimisation is the analysis\_id parameters. These are compulsory for optimisation analysis but not required otherwise. The analysis\_id parameters link the analysis to an [.OPTSPEC](#page-271-0) statement.

#### **Objective and Constraint Definition**

The remaining statements are **.OPTSPEC** statements and these define the objective and constraint functions.

```
** Objective function
   .optspec
   + measure="-(v3#p+v2#p)"
   + type=minimum
   + analysis_id=ac_0
   + op
   + label="Supply_current"
   ** Constraint functions
   .optspec
   + measure="lpbw(vout, 3)"
   + type=constraint_minimum
   + analysis_id=ac_0
   + value=2.5e+08
   + label="Bandwidth"
   .optspec
   + measure="yatx(db(vout),1meg)"
   + type=constraint_minimum
   + analysis_id=ac_0
   + value=20
   + label="Gain_at_1meg"
   .optspec
   + measure="MeasureDistortion(vout)"
   + type=constraint_maximum
   + analysis_id=tran_1
   + value=0.01
   + label="Distortion"
The first definition:
```

```
.optspec
+ measure="-(v3#p+v2#p)"
+ type=minimum
+ analysis=ac_0
+ op
+ label="Supply_current"
```
is the objective function. There must be one and one-only objective function. The measure parameter is the actual expression that is calculated. In this case it is calculating the currents into V3 and V2. The focus of the optimisation is the power consumption but in this case both voltage sources are the same voltage so we simply seek to minimise the total current.

The type parameter must be either minimum or maximum for an objective function. In this it is minimum meaning that the optimiser will seek to minimise this value.

The analysis\_id links this measurement to the analysis line with the same analysis\_id namely the **.AC** statement shown above.

The  $_{\text{op}}$  parameter specifies that the measurement should use the operating point data for the specified analysis.

Finally the label parameter defines a label that will be used to identify the measurement in the final report, in progress messages and in any error messages that may be output.

The remaining three **.OPTSPEC** statements are constraint functions. The optimiser will attempt to minimise the objective while complying with the constraints. Constraints are identified by the  $type$  parameter

having the value constraint\_minimum or constraint\_maximum. constraint\_minimum means that the optimiser will attempt to not allow the measurement to fall below the value of the value parameter while constraint\_maximum means that the optimiser will attempt to not allow the measurement to rise above the value of value.

# <span id="page-316-0"></span>**8.3 Algorithms**

The optimiser algorithms are provided by the free/open source library NLopt developed and maintained by Steven G. Johnson who is professor of Applied Mathematics and Physics at MIT.

The library contains over 20 optimiser algorithms, however, we have currently only implemented "Derivative-free" optimisation algorithms.That is algorithms that do not require the calculation of the partial derivatives (or sensitivities) of each objective and constraint with respect to every parameter. The calculation of each derivative requires one additional simulation run for each parameter and so is in general expensive. However, algorithms that do require derivatives to be calculated, usually converge much more quickly.

#### **8.3.1 List of Available Algorithms**

Here is a complete list of currently available algorithms. Use the value in the Code column as the value of the alg parameter for the **.OPTIMISER** statement or single-analysis optimiser statement.





## **Augmented Lagrangian**

The augmented Lagrangian algorithm is a derivation of Lagrangian multipliers and is used to convert a constrained problem into an unconstrained problem. Each of the unconstrained local optimiser methods have augmented Lagrangian variations that have the suffix \_AL. **Important:** the augmented Lagrangian method does not normalise the constraints. To get the constraint functions to work with any of these methods, it is necessary to apply appropriate scaling to each constraint function. This is not the case with the COBYLA algorithm which supports constraints directly and does not require special scaling.

# **Chapter 9**

# **Convergence, Accuracy and Performance**

### **9.1 Overview**

In transient and DC analyses, an iterative method is used to analyse the circuit. Generally, iterative methods start with an initial guess for the solution to a set of equations and then evaluate the equations with that guess. The result of that evaluation is then used to derive a closer estimate to the final solution. This process is repeated until a solution is found that is within the error tolerance required. SIMetrix and SPICE use Newton-Raphson<sup>[1](#page-318-0)</sup> iteration which usually converges extremely rapidly. However, there are occasions when this process is either unreasonably slow or fails altogether. Under these circumstances the simulation will abort.

SIMetrix offers superior convergence which has been achieved as a result of the following developments to the simulator core:

- Automatic pseudo transient analysis algorithm for operating point solution. See below for details.
- Advanced iteration algorithm reduces numerical noise
- Enhancements to GMIN and source stepping algorithms to use a variable step size. (The standard SPICE3 variants use a fixed step).
- Junction GMIN DCOP Convergence Method
- Proprietary enhancements to transient analysis algorithm.
- Optional extended and quad precision solvers
- New matrix solver
- Improvements to device models.

With these improvements, convergence failure with SIMetrix is extremely rare. However, it is impossible to eliminate this problem altogether and there still remain some circuits which fail.

In this chapter we explain some of the causes of non-convergence and some of the strategies SIMetrix uses to prevent it. Also explained is what to do in the rare event that convergence fails.

# **9.2 DC Operating Point**

<span id="page-318-0"></span><sup>&</sup>lt;sup>1</sup>Sir Isaac Newton 1642-1727 and Joseph Raphson 1648-1715

#### **9.2.1 Overview**

As explained in [DC Operating Point Algorithms,](#page-326-0) SIMetrix has four different algorithms at its disposal to solve the DC operating point. For this analysis mode to fail, and assuming the default settings are being used, all four algorithms must fail.

The following sections describe the possible reasons for failure of each mode and what can be done about them.

The general procedure is as follows:

- 1. Check your circuit. Check that all components are the correct way around and have the correct values. Make sure you haven't used 'M' when you meant 'Meg'.
- 2. Refer to section [Source and GMIN Stepping](#page-319-0) and see if GMIN or source stepping can be made to work.
- 3. Refer to section [Pseudo Transient Analysis](#page-319-1) to get pseudo transient analysis converging.
- 4. Contact technical support. We don't officially offer a convergence fixing service and reserve the right to decline help. However, we are always interested in non-converging circuits and usually we will look at your circuit to see if we can identify the problem.

#### <span id="page-319-0"></span>**9.2.2 Source and GMIN Stepping**

By default, if these modes fail, SIMetrix will carry on and attempt pseudo transient analysis. It will not do so only if instructed not to using the dcopSequence option (See [Controlling DC Method Sequence\)](#page-327-0). Pseudo transient analysis usually succeeds but sometimes can take a long time so you may prefer to get one of these methods working instead. Also, if pseudo transient analysis fails it is desirable to first see if GMIN or source stepping can be made to work.

There are a few options you can set to encourage these modes to converge. These are



It is only worth changing gminMaxIters or sourceMaxIters if the iteration limit is actually being reached. Often GMIN and source stepping fail to converge before the iteration limit is reached. To find out, select the menu **Simulator | Show Statistics**. This displays, amongst other things, the number of iterations used for GMIN and/or source stepping. If they exceed 1000 then the iteration limit has been reached. This means that GMIN/source stepping may have succeeded if it had been given a chance.

#### <span id="page-319-1"></span>**9.2.3 Pseudo Transient Analysis**

Pseudo transient analysis is the most powerful method that SIMetrix uses and it is rare for it to fail. It is not however infallible and can go wrong for the following reasons:

- 1. The transient analysis itself failed to converge. (This is rare)
- 2. The circuit oscillates

#### **Convergence failure in pseudo transient analysis**

You will get the error message

Cannot find DC operating point No convergence in pseudo transient analysis

The reasons why this may happen are the same as for transient analysis and are covered in [Fixes for](#page-325-0) [Transient Non-convergence.](#page-325-0)

#### **Circuit oscillation**

You will see the message

Cannot find DC operating point Iteration limit exceeded in pseudo transient analysis

The circuit can oscillate because:

- 1. It is designed to i.e. it is or has an oscillator
- 2. It is supposed to be stable but passes an unstable region during supply ramping
- 3. It is supposed to be stable but has a fault in its design
- 4. It is stable but is made unstable by the capacitors added during the pseudo transient analysis

#### **If the circuit is an oscillator**

If 1. then you must disable the oscillator during the DC solution. You can do this by one of the following methods:

- 1. Apply an initial condition to a point on the circuit that will break the oscillator's feedback loop.
- 2. Use the capacitor/inductor PTAVAL parameter to change its value during pseudo transient analysis. This parameter can be applied to a component or components that form part of the oscillator. In the netlist the parameter is applied at the end of the component line. E.g for a capacitor:

C12 N2 N6 1.2n PTAVAL=1

In the above a 1.2n capacitor will take the value of 1 farad during pseudo transient analysis.

#### **The circuit is not supposed to be an oscillator**

If the circuit does not have any intentionally unstable elements then diagnosis of the problem is a little harder. Firstly, you need to rule out 4. above as a possible cause. As explained in [DC Operating Point](#page-326-0) [Algorithms,](#page-326-0) SIMetrix adds its own capacitors to your circuit during pseudo transient analysis in order to overcome potential problems with regenerative action. The problem is that these added capacitors can themselves make a circuit unstable. So the first thing to try is to inhibit the addition of these capacitors. To do this, add the following line to the netlist (See [Adding Extra Netlist Lines](#page-17-0) to find out how to add to a schematic):

**.OPTIONS** PTACONFIG=1

then re-run the simulation.

#### **The circuit is not supposed to be an oscillator but it is**

If this fails, then life gets even more complicated! If it fails with the message

Iteration limit exceeded in pseudo transient analysis

then it is very likely that the circuit is oscillating or entering an unstable region. If a different message is displayed go to [The circuit doesn't oscillate but still doesn't converge.](#page-321-0) To allow diagnosis of what is happening SIMetrix provides a method of analysing the circuit during the pseudo transient ramp. By default, no data is output during pseudo transient analysis but this can be changed as follows:

- 1. Set the analysis mode to DC operating point only.
- 2. Add the simulator option ptaOutputVecs by adding the following line to the netlist:

**.OPTIONS** PTAOUTPUTVECS

3. Now run the simulation for a while or until it stops.

You can now probe the circuit in the normal way to see what is oscillating. Once the oscillation has been fixed, you should be able to simulate the circuit successfully.

#### <span id="page-321-0"></span>**The circuit doesn't oscillate but still doesn't converge**

As there are no added capacitors, there is a risk that pseudo transient analysis can fail for the same reason that GMIN and source stepping sometimes fail. In this case you will get the message:

No convergence in pseudo transient analysis

If this happens your only recourse is the final desperation measure. This is to repeat the simulation with all valid values of ptaConfig from 2 to 15. (You can skip 7 as this is the default). ptaConfig is a simulator option that controls some of the parameters used in pseudo transient analysis. Most circuits pass for all settings but a few are more selective.

#### **Accept Pseudo Transient Unconditionally**

You can specify pseudo transient analysis to be accepted unconditionally at some time after it has started. This is often a good solution to problems caused by circuit oscillation especially if the oscillation is small and unintended. To accept pseudo transient unconditionally, set the option:

**.OPTIONS** PTAACCEPTAT=time

Specify a *time* value that is adequate for the circuit state to settle as much as possible.

#### **9.2.4 Junction Initialised Iteration**

By default, this is the first method to be tried. If it fails, SIMetrix will then attempt source stepping, GMIN stepping and finally pseudo transient analysis. Usually one of these other methods will succeed and it is not worth spending time getting this method to work.

If it does work, however, this is usually the fastest method and this can be put to good use for repetitive runs e.g. Monte Carlo. It can be made to succeed using nodesets (see next section) and with a wisely chosen selection it is possible to speed up repetitive runs. Assuming one of the other methods does complete to a solution, the best way of creating nodesets is by using the SaveRHS command. This is explained in the next section.

### **9.2.5 Using Nodesets**

Nodesets have two uses, one to aid convergence and the other to bias the solution in circuits that have more than one stable state.

Initially nodesets work exactly the same way as initial conditions. The nodeset voltage is applied via a 1 Ohm (by default) resistor and the solution is completed to convergence (by any of the methods). The nodeset is then released and the solution repeated. If the nodeset voltage is close to the actual solution the convergence of the second solution should be rapid.

With SIMetrix, it is rarely necessary to use nodeset's to find the DC solution of a circuit. They can, however, be useful for speeding up the operating point analysis for circuit that have already been solved. You may wish to do this for a Monte-Carlo analysis, for example.

SIMetrix provides a means of creating nodeset's using the SaveRHS command. To make use of this, proceed as follows:

- 1. Run a DC operating point analysis
- 2. Save the solution to a file using the SaveRhs command as follows:

SaveRhs /nodeset RHS.TXT

This will save to the file RHS.TXT a .nodeset statement specifying the solution at each node.

3. Paste the contents of RHS.TXT to the netlist. Alternatively, include the file using the .INC statement. (See [Adding Extra Netlist Lines](#page-17-0) to find out how to add to a schematic).

If you now repeat the DC analysis, you should now find that the solution is very rapid. Depending on the nature of your circuit, you may also find that the solution is found easily even if you modify the circuit. This is not, however, guaranteed.

# **9.3 Transient Analysis**

#### **9.3.1 What Causes Non-convergence?**

There are a number of reasons for convergence failure in transient analysis but most have their root in one of the following:

- 1. Numerical noise (also known as round-off error) is preventing the required accuracy from being reached. SIMetrix has a range of iteration modes that allow the reduction of numerical noise at the expense of simulation run time. See [Numerical Noise and Iteration Modes](#page-322-0)
- 2. The circuit contains discontinuities. This is where a model or a circuit construction can switch abruptly from one state to another with no defined time to do so. This behaviour violates one of the conditions required for the iteration algorithm to guarantee convergence. It can also defeat the algorithm used to estimate the accuracy of modelling reactive components. Discontinuities can be solved either by introducing a smooth behaviour or by defining a finite time to switch states
- 3. Instability. This is where the circuit has an unbounded instability and thus has no finite solution. This can be caused, for example, by positive feedback loops or unrealisable networks.
- 4. Overload. The solution is beyond the numerical range available. A trivial example of this is a PN junction biased by a large voltage. Without any series resistance, the voltage does not need to be very high for the current in the device to exceed the range of the machine.

#### <span id="page-322-0"></span>**9.3.2 Numerical Noise and Iteration Modes**

#### **Numerical Noise**

Numerical noise is one of the major causes of non-convergence in transient analysis. Numerical noise is the noise induced as a result of uncertainly in a calculation due to the limited precision of the arithmetic (sometimes referred to as round-off error). Numerical noise is similar in concept to quantization noise that is prevalent in data converters. Numerical noise increases as the time step reduces due to the behaviour of reactive components and can reach levels that exceed the tolerance parameters that determine when convergence has been reached.

SIMetrix uses two strategies to reduce numerical noise and these are controlled by the iteration mode:

- 1. Use the advanced iteration algorithm. This employ a variation in the iterative equation that lowers the error terms for most practical circuits. It benefits circuits with high voltages or high-side sections. The advanced iteration algorithm has only a minor effect on performance.
- 2. Use a higher calculation precision. Most numerical software including most analog simulators use double precision which is about 16 decimal digits. SIMetrix has options to use extended precision, which is about 19 decimal digits, and **quad** precision which is over 30 decimal digits.

#### **Iteration Modes**

SIMetrix offers 8 iteration modes that provide control over the trade-off between numerical noise and simulation run time. The default mode 1 is the fastest while mode 8 more or less eliminates numerical noise albeit with a significant performance penalty.

The iteration mode is set by the CONV option setting:

**.OPTIONS** CONV=<mode>

Where  $\langle$  mode $\rangle$  is an integer from 0 to 10 as described in the table below.



The value in the Typical numerical noise factor column is the typical reduction in numerical noise compared to mode 0/1. For example, for mode 4 the numerical noise is typically reduced by a factor of 10000 - so the noise will typically be 10000 times lower. Be aware that these are typical values and can vary widely between different circuits and operating conditions.

The above simulation run time factors are typical when using 4 cores. The penalty for the quad precision modes is higher with single core operation.

CONV mode 4 is probably the most useful. It is very effective at solving convergence problems with
difficult circuits and affects performance only a little - typically slowing down the simulation by about 25%.

CONV mode 10 can be useful for circuits that contain large passive networks as is common obtained from parasitic extraction tools. While not offering any convergence benefit, this mode can run significantly faster for such circuits.

### **Advanced Iteration**

Modes 2, 4, 6, 8 and 10 employ the advanced iteration algorithm. This uses a variation in the iterative equation that lowers the error terms for most practical circuits. Advanced iteration is mathematically identical to normal iteration and imposes only a marginal performance penalty.

As well as generally having lower numerical noise, advanced iteration has more dependable error detection. In rare situations, normal iteration can converge on a solution that is inaccurate due to round-off error. Usually round-off error causes numerical noise as explained above but in linear circuits (or linear portions of non-linear circuits) round-off error can be static which means the convergence detection algorithm incorrectly allows an inaccurate result. This effect does not occur with advanced iteration. This can mean that on some occasions advanced iteration fails (correctly) when normal iteration succeeds (incorrectly - resulting in possibly undetected errors).

# **Convergence Mode GUI**

Modes 0, 2, 4, 6, 8 and 10 may be selected through the convergence GUI. See *Users Manual / Analysis Modes / Convergence / Convergence Options / Iteration Mode*

#### **Quad Precision Modes**

CONV modes 5 to 8 use Quad precision. Quad precision uses 128-bit values and enjoys a decimal resolution of over 30 digits. No current windows-compatible microprocessor implements quad precision arithmetic in hardware and consequently quad precision calculations are software implemented.

All quad precision modes enjoy very low levels of numerical noise and more or less eliminate this as a source of transient analysis convergence failure. However the performance penalty is greater than other modes. CONV mode 6 for example, will slow down the simulation typically by about 1.5x to 3x although it can be slower.

Quad precision is not often needed to make a circuit using normal tolerances run; there is usually another way to resolve a convergence problem which doesn't impose a performance penalty. However, if one of these setting does fix the problem, it is likely to be a reliable fix, and the increased run time may be satisfactory trade-off.

Quad precision is also useful for diagnosing convergence problems caused by other factors. With the lower precision modes, numerical noise can often mask the true cause of a convergence problem. With quad precision the real cause is more easily seen.

Of the four quad precision modes, mode 6 is likely to the best choice. Mode 6 also makes use of extended precision where possible to improve performance and is consequently faster than mode 8 which uses quad precision exclusively.

Note that the Simkit devices and BSIM4 versions 4.3 and earlier do not support quad precision. Although circuits containing these devices will run in quad precision mode, there will only be a small improvement in convergence.

It should be noted that the calculation precision does not usually affect the simulation accuracy. This is determined by the tolerance settings especially RELTOL. However, using tighter tolerance parameters increases the sensitivity of the simulator to the effects of numerical noise and so can, and often does, lead to convergence failure. So, using a higher precision mode will allow tighter values of the tolerance parameters to be used.

### **9.3.3 Fix and Improving Transient Convergence**

- 1. Try a higher iteration mode. At the netlist level add **.OPTIONS** conv=<value> where <value> is an integer between 2 and 8. The higher the value the higher the precision but the slower the simulation run time. Modes 5 to 8 use quad precision and have a significant performance penalty. See [Iteration](#page-323-0) [Modes](#page-323-0) for more details. If running from the schematic editor, some modes may be selected using menu **Simulator | Convergence Options...**
- 2. Select menu **Simulator | Convergence Failure Report...**. This will display a report providing information on the cause of failure. For more details of this report, see *User's Manual/Analysis Modes/Convergence/Convergence Failure Report*
- 3. As with DC operating point, check your circuit. In particular, check that you are not doing anything which might cause numerical difficulties such as forward biasing a zero resistance PN junction with a large zero source impedance voltage source.
- 4. Do anything that will prevent small time steps being needed. Gross non-linearities, regenerative loops and high gain loops all require small time-steps if not well damped. It may be that you have left out damping components to simplify the circuit and speed the simulation.
- 5. Avoid *over-idealising*. A common misconception is that simplifying a circuit by removing reactive components such as capacitors will speed up a simulation and make it easier to converge. Capacitors have a number of stabilising effects on simulation and are usually beneficial.
- 6. Avoid using unrealistically large capacitors or inductors and unrealistically small resistors if at all possible. You should especially avoid such components if non-grounded.
- 7. If you have some large capacitors in your circuit, try adding a small amount of ESR using the built-in capacitor ESR parameter rather than a separate resistor.
- 8. If all else fails you can try relaxing some of the tolerances. If your circuit does not have any small (sub- $\mu$ A) currents then set ABSTOL to 1e-9 or 1e-6. You can also increase VNTOL (default 1e-6) to say 1e-3 if your circuit only has large voltages. Increasing RELTOL is the very last thing you should try. In our experience, increasing RELTOL beyond its default value (0.001) is rarely a reliable solution and can make matters worse.
- 9. If you have current maintenance, contact technical support providing us with your full schematic and any models you are using. We can fix most convergence problems.

# **9.4 DC Sweep**

DC sweep is basically a repeated DC operating point and so the issues relating to that mode also apply to DC sweep. However, if you are sweeping a voltage or current source, then an altogether better way of dealing with DC sweep problems is to simulate the DC sweep using transient analysis with a slow ramp.

Using transient analysis to perform DC sweep also resolves problems that can occur with circuits that have regions where there is more than one stable state e.g. bistables or schmitt triggers. Consider sweeping the input voltage of a schmitt trigger circuit. When the input voltage is between the lower and upper thresholds, the circuit has two stable states and the DC algorithm could find either of them. As each step in a DC analysis is initialised with the previous step, it will usually find the correct solution *but this is not guaranteed*. This means that the output could change state even though the input has not passed either threshold. This problem doesn't occur in transient analysis as in this mode the circuit is running as it would in real life.

# **9.5 DC Operating Point Algorithms**

SIMetrix uses five alternative strategies to resolve the DC operating point. These are:

- 1. Junction initialised iteration. This is our name for the standard algorithm sometimes simply known as 'DC Iteration'.
- 2. Source stepping.
- 3. Diag GMIN stepping.
- 4. Junction GMIN stepping.
- 5. Pseudo transient analysis.

These are described in the following sections.

### **9.5.1 Junction Initialised Iteration**

This is the standard algorithm and is sometimes known simply as 'DC iteration'. Each semiconductor junction is initialised with a small voltage and iteration then proceeds until convergence (or otherwise). This method often succeeds and is usually the quickest. However, the starting point is only a bit better than an educated guess and can be so far removed from the real solution that it never has a chance of succeeding. ('Junction initialised iteration' is a name we have coined and you may see it referred to as JI2 elsewhere in this manual and also in messages output by SIMetrix)

#### **9.5.2 Source Stepping**

Source stepping. This method - as with all the remaining methods to be described - belong to a class of convergence strategies known as continuation methods. These all work by repeating the iterative process while gradually varying some circuit parameter. The circuit parameter is chosen so that at its start value the solution is known or trivial and at its final value the solution is the operating point that is required. In source stepping, all the circuit's power sources are gradually ramped up from zero to their final value. While at zero, the circuit's solution is trivial; all the voltages and currents are zero. At the first step, the supplies might be ramped up to 10% of their maximum and the solution iterates to convergence. Then the supplies are increased and the process is repeated. At each step the solution is initialised with the previous solution which, if the steps are small, will be close to the new solution that is required and convergence will therefore be relative easy to achieve.

This method is quite effective and is included in all SPICE based simulators including those derived from SPICE2. However the SPICE versions use a fixed step size, whereas in SIMetrix (since version 2.0), the step size is variable so if a step fails, the step size is reduced and it tries again.

However, even with an arbitrarily small step size, this method can fail if the circuit contains some kind of regenerative action. As the supplies are ramped it is possible for the circuit to abruptly switch from one state to another as in a schmitt trigger. Although circuits such as schmitt triggers do give difficulty, even circuits that do not have such elements can also give trouble.

### **9.5.3 Diagonal GMIN Stepping**

In this method, a large conductance term is added to every diagonal entry of the solution matrix and gradually reduced. This is similar to placing a low value resistor from every node of the circuit to ground but is by no means equivalent. The high conductance term (=low resistance) in the matrix effectively swamps non-linearities and as a result the solution is easy to find. The term is gradually reduced until it is zero.

This method is also effective and sometimes works for circuits for which source stepping fails. It is included with all SPICE3 derived simulators but, as with source stepping, the SPICE variants use a fixed step while SIMetrix uses a variable step.

GMIN stepping suffers from the same problems as source stepping but not always with the same circuits so it always worth trying both approaches.

The received wisdom has always been that GMIN stepping is more effective than source stepping. This has not however been borne out by our own research which has shown the source stepping converges more often and more quickly. For this reason, SIMetrix attempts source stepping before GMIN stepping. This is the reverse of SPICE3 and its derivatives.

### **9.5.4 Junction GMIN Stepping**

The junction GMIN stepping method incrementally steps the conductance across semiconductor junctions. This in effect sweeps the GMIN option parameter.

This method is effective for CMOS IC designs as long as GMIN is implemented as a conductance between drain and source. This is not the default configuration for LEVEL 1 to 3 MOSFETs in which GMIN is implemented as two conductances between the drain and bulk and source and bulk. For other MOSFET models such as BSIM3, the default GMIN is now between source and drain. For designs containing these devices, Junction GMIN Stepping is the first method attempted after JI2. For circuits that do not contain such devices, this method is not attempted at all.

# **9.5.5 Pseudo Transient Analysis**

This method finds the solution using transient analysis. In SIMetrix, a transient analysis is conducted while ramping up all power sources, in effect simulating the action of switching on the power supplies. This is not the same as source stepping as the latter is a pure DC method with all reactive components set to zero. Because reactive components - i.e. capacitors and inductors - are included in transient analysis, effects such as abrupt changes are damped and occur gradually over a finite time. This eliminates the problem - described above - that the DC continuation methods suffer from.

The above assumes, however, that the circuit is well modelled with all reactive elements correctly specified. With integrated circuit design this is usually the case, but for discrete circuits frequently is not. Opamp macro models, for example, consist of many idealised elements that are not always damped by reactive elements. Without such damping, pseudo transient analysis can fail for the same reason as source and GMIN stepping. So, SIMetrix automatically adds additional capacitance to the circuit to prevent this situation from arising.

The end result is a convergence strategy that *nearly always succeeds*. However, it is generally the slowest method so in SIMetrix it is, by default, attempted last.

Although pseudo transient analysis is very powerful it is not completely infallible. Its *Achilles Heel* is oscillation. Because a transient analysis is being performed it is possible for the circuit to oscillate. If this happens, pseudo transient analysis can end up going on forever without ever finding a stable solution. In our experience, however, this is actually rare. A number of steps are taken to damp oscillators so that even circuits that are designed to oscillate still succeed with pseudo transient analysis.

SIMetrix provides a number of facilities to inhibit circuit oscillation during pseudo transient analysis. These are described in [Pseudo Transient Analysis.](#page-319-0)

# **9.5.6 Controlling DC Method Sequence**

You may have a circuit that only succeeds with - say - pseudo transient analysis and so attempting the other methods just wastes time. In this situation, you can force the simulator to attempt this method exclusively. To do this you need to set the two simulator options noOpiter and dcopSequence. noOpiter inhibits the

first method (junction initialised iteration) while dcopSequence controls which and what order the remaining methods are attempted. The value of dcopSequence consists of any combination of SOURCE, GMIN, JUNCGMIN and PTA separated by the pipe symbol: '|'. SOURCE, GMIN, JUNCGMIN and PTA refer respectively to 'source stepping', 'DIAG GMIN stepping', 'Junction GMIN stepping' and 'pseudo transient analysis'. The order in which these words appear in the value of dcopSequence, determines the order in which the corresponding methods will be attempted. So for example:

**.OPTIONS** NOOPITER DCOPSEQUENCE=GMIN|PTA

will force GMIN stepping to be attempted first followed by pseudo-transient analysis. Junction initialised iteration, junction GMIN stepping and source stepping won't be attempted at all. Note that PTA must always be the last entry.

# **9.6 Singular Matrix Errors**

A singular matrix error occurs when the circuit does not have a unique and finite solution. For example, a circuit containing a floating capacitor does not have a unique DC solution as the capacitor can be at any voltage. Also circuits with shorted inductors, voltage sources or a combination of both will fail with this error.

If you get this error, select menu **Simulator | Convergence Failure Report**. This will show any nodes with no DC path to ground - a common cause of singular matrix errors. If this doesn't show the cause, check your circuit generally.

If you think you circuit is OK then it is possible that the error is occurring because during the course of iterating to a solution, some node voltages or device currents reached very high values and the limited accuracy of the machine made it seem that the matrix was singular. This can happen with junction initialised iteration. If this is the case, try setting the option:

**.OPTIONS** NOOPITER

This will inhibit this mode and the simulator will start with source stepping. This method, and the others that follow, don't generally suffer from this problem.

Note that the simulation will abort if a singular matrix is detected in junction initialised iteration. It will not automatically attempt the other methods. This is because, by far the most common reason for singular matrices is circuit error.

# **9.7 Transient Analysis - 'Time step too small' Error**

#### The message:

Timestep too small

is not actually due to non-convergence. It means that, because of the nature of your circuit, to achieve the required accuracy, a time step smaller than the minimum permissible was needed. The default value for the minimum time step is 1e-18 or 1e-9\*max-time-step whichever is the smaller. This error can be fixed by setting a lower value for the minimum time step and can be set in the user interface. See *User's Manual/Analysis Modes/Transient Analysis/Setting up a Transient Analysis/Time Step*.

# **9.8 Accuracy and Integration Methods**

#### **9.8.1 A Simple Approach**

If you wish to increase the accuracy of a simulation, reduce the value of RELTOL. This defaults to 0.001 so to reduce it to say 1e-5 add the following line to the netlist:

**.OPTIONS** RELTOL=1e-5

(The setting of RELTOL is supported by the front end. See *User's Manual/Analysis Modes/Simulator Options/Setting Simulator Options/Tolerances* for details.)

The simulation will run slower. It might be a lot slower it might be only slightly slower. In very unfortunate circumstances it might not simulate at all and fail with a convergence error.

Conversely, you can speed up the simulation by increasing RELTOL but you should not set this to a value higher than around 0.005 as this will degrade accuracy to an unacceptable level.

#### **9.8.2 Iteration Accuracy**

For DC and transient modes, the simulator essentially makes an approximation to the true answer. For DC analysis an iterative method is used to solve the non-linear equations which can only find the exact answer if the circuit is linear. The accuracy of the result for non-linear circuits is determined by the number of iterations; accuracy is improved by performing more iterations but obviously this takes longer. In order to control the number of iterations that are performed an estimate is made of the error by comparing two successive iterations. When this error falls below a predetermined tolerance, the iteration is deemed to have converged and the simulator moves on the next step or completes the run. Most SPICE simulators use something similar to the following equations to calculate the tolerance:

For voltages: TOL = RELTOL \* instantaneous\_value + VNTOL

For currents:  $TOL = RELTOL * instantaneous value + ABSTOL$ 

"instantaneous\_value" is the larger of the current and previous iterations. VNTOL has a default value of  $1\mu$ V so for voltages above 1mV, RELTOL dominates. ABSTOL has a default of 1pA so for currents above 1nA, RELTOL dominates.

The above method of calculating tolerance works fine for many circuits using the default values of VNTOL and ABSTOL. However, SPICE was originally designed for integrated circuit design where voltages and currents are always small, so the default values of ABSTOL and VNTOL may not be appropriate for - say - a 100V 20A power supply. Suppose, that such a PSU has a current that rises to 20A at some point in the simulation, but falls away to zero. When at 20A it has a tolerance of 20mA but when it falls to zero the tolerance drops to ABSTOL which is 1pA. In most situations the 1pA tolerance would be absurdly tight and would slow down the simulation. Most other SPICE products recommend increasing ABSTOL and VNTOL for PSU circuits and indeed this is perfectly sound advice. However, In SIMetrix the tolerance equation has been modified to make this unnecessary in most cases. Here is the modified equation:

For voltages: TOL = RELTOL \* MAX( peak\_value \* POINTTOL, instantaneous\_value ) + VNTOL

For currents: TOL = RELTOL \* MAX( peak\_value \* POINTTOL, instantaneous\_value ) + ABSTOL

peak\_value is the magnitude of the largest voltage or current encountered so far for the signal under test. POINTTOL is a new tolerance parameter and has a default value of 0.001. So for the example we gave above, peak\_value would be 20 and when instantaneous\_value falls to zero the tolerance would be:

 $0.001 * MAX(20 * 0.001, 0) + 1p =$ approx.  $20 \mu A$ 

 $20\mu$ A is a much more reasonable tolerance for a signal that reaches 20A.

The above method has the advantage that it loosens the tolerance only for signals that actually reach large values. Parts of a circuit that only see small voltages or currents - such as the error amplifier of a servo-controlled power supply - would still be simulated with appropriate precision.

POINTTOL can be increased to improve simulation speed. It is a more controlled method than increasing RELTOL. POINTTOL can be raised to 0.1 or even 1.0 but definitely no higher than 1.0.

### **9.8.3 Time Step Control**

The tolerance options mentioned above also affect the time step control algorithm used in transient analysis. In SIMetrix, there are three mechanisms that control the time step, one of which has to be explicitly enabled. These are:

- 1. Iteration time step control
- 2. LTE time step control
- 3. Voltage delta limit

Item 3 above is inactive unless explicitly enabled using the MAXVDELTAREL option setting. See below for details.

### **Iteration Time Step Control**

Iteration control reduces the time step by a factor of 8 if convergence to the specified accuracy cannot be achieved after 10 iterations. (10 by default but can be changed with ITL4 option). If convergence is successful, the time step is doubled. As this mechanism is controlled by the success or otherwise of the iteration it is also affected by the same tolerance options described in the above section about iteration accuracy.

# **LTE Time Step Control**

"LTE time step control" is an algorithm which controls the accuracy of the numerical integration method used to model reactive devices such as inductors and capacitors. These devices are governed by a differential equation. It is not possible in a non-linear circuit to solve these differential equations exactly so a numerical method is used and this - like the iterative methods used for non-linear devices - is approximate. In the case of numerical integration, the accuracy is determined by the time step. The smaller the time step the greater the accuracy but also the longer the simulation time.

The accuracy to which capacitors are simulated is controlled by RELTOL, POINTTOL and two other options namely TRTOL and CHGTOL. The latter is a charge tolerance and has a similar effect to VNTOL and ABSTOL but instead represents the charge in the capacitor. It's default value is 1e-14 which, like ABSTOL and VNTOL is appropriate for integrated circuits but may be too low for PSU circuits with large capacitors. However, the peak detection mechanism controlled by POINTTOL described in the above section also works for the LTE time step control algorithm and it is therefore rarely necessary to alter CHGTOL.

TRTOL is a dimensionless value which defaults to 7. It affects the overall accuracy of the numerical integration without affecting the precision of the iteration. So reducing TRTOL will increase the accuracy with which capacitors and inductors are simulated without affecting the accuracy of the iterative method used to simulate non-linear elements. However, in order for the simulation of reactive devices to be accurate, the non-linear iteration must also be accurate. So, reducing TRTOL much below unity will result in a longer simulation time but no improvement in precision. Increasing TRTOL to a large value, however, may be appropriate in some circumstances where the accuracy to which reactive devices are simulated is not that important. This may be the case in a circuit where there is an interest in the steady state but not in how it was reached.

Inductors are controlled by the same tolerances except CHGTOL is replaced by FLUXTOL. This defaults to 1e-11.

The default LTE time step algorithm used in SIMetrix is slightly different to that used by standard SPICE. The standard SPICE variant is also affected by ABSTOL and VNTOL. The SIMetrix algorithm controls the time step more accurately and as a result offers better speed-accuracy performance.

# **Controlling Digital Logic False Clocking**

A problem that often occurs with analog simulators simulating analog-implemented clocked logic is false clocking of flip-flops or false state changes. These occur if the time step is allowed to get too long. If the time step substantially exceeds the typical gate delay, the circuit is solved as if it were a DC solution. In the case of a flip-flop, which has two states, it is possible for the simulator to converge on the wrong state.

A typical scenario is with asynchronous reset. The reset signal might enter an active state (e.g. low) while the simulator is converging to a solution but the final value is inactive (e.g. high). The plotted result won't show any change of state of the reset signal, but the flip flop will have mysteriously changed state. This can't happen if the time step is sufficiently small as the gate delays will prevent any output state change.

The solution is to control the time step to ensure that when any logic output changes state, the time step is cut back to a level comparable to the typical gate delay.

SIMetrix provides a number of methods of achieving this.

#### **Voltage Delta Limit**

This places a limit on the amount of change allowed in a single timestep for each node. This limit is governed by the option setting MAXVDELTAREL and MAXVDELTAABS and is included to overcome a problem that can cause false clocking of flip-flops. The limit can be calculated from:

MAXVDELTAABS + MAXVDELTAREL\*(node\_voltage)

where node\_voltage is the larger of the node voltage at current time step and the node voltage at the previous time step. The above is calculated for all voltage nodes. If the change in voltage exceeds this limit, the time step is cut back. The option MAXVDELTATIME places a lower limit on the time step when cut back by this mechanism. This should be set to the typical transition time for the logic circuit technology.

The above mechanism is not enabled if MAXVDELTAREL is zero or less and MAXVDELTAREL is zero by default.

Setting MAXVDELTAREL to a value of about 0.4 will usually fix problems of false clocking in flip-flops. However, this will slow down the simulation slightly and it is not recommended that this setting is used in circuits that do not contain flip-flops.

# **Logic Transition Control**

This method is applied to arbitrary sources only which are commonly used to implement logic gates. If an output transitions from a value 0.1 x the maximum voltage detected to 0.9 x the maximum value detected in a single time step, the time step will be cut back to a fixed value which defaults to 1ns. This action only occurs once the maximum detected voltage on the output exceeds 0.5V.

This method is on by default.

Option settings LOGICTRANSLOW, LOGICTRANSHIGH, LOGICTRANSTIME and LOGICTRANSMODE control the behaviour of this function.

### **9.8.4 Accuracy of AC analyses**

The small-signal analysis modes .AC, .TF and .NOISE do not use approximate methods and their accuracy is limited only by the precision of the processor's floating point unit. Of course the DC operating point that always precedes these analysis modes is subject to the limitations described above. Also, the device models used for non-linear devices are also in themselves approximations. So these modes should not be seen as exact but they are not affected by any of the tolerance option settings.

### **9.8.5 Summary of Tolerance Options**

#### **RELTOL**

Default = 0.001. This affects all DC and transient simulation modes and specifies the relative accuracy. Reduce this value to improve precision at the expense of simulation speed. We do not recommend increasing this value except perhaps to run a quick test. In any case, you should never use a value larger than 0.01.

#### **POINTTOL**

Proprietary to SIMetrix. Default  $= 0.001$ . Can increase to a maximum of 1.0 to improve speed with loss of precision. Reduce to 0 for maximum accuracy but note this may just slow down the simulation without really improving precision where it is needed.

#### **ABSTOL**

Default = 1pA. This is an absolute tolerance for currents and therefore has units of Amps. This basically affects the tolerance for very low values of current. Sometimes worth increasing to resolve convergence problems or improve speed for power circuits.

#### **VNTOL**

Default = 1V. Same as ABSTOL but for voltages.

#### **TRTOL**

Default = 7. This is a relative value and affects how accurately charge storage elements are simulated. Reduce it to increase accuracy of reactive elements but there is no benefit reducing below about 1.0. In circuits where there is more interest in the steady state rather than how to get there, simulation speed can be improved by increasing this value.

### **CHGTOL**

Default = 1e-14. Minimum tolerance of capacitor charge. Some convergence and speed improvement may be gained by increasing this for circuits with large capacitors. Generally recommended to leave it alone.

### **FLUXTOL**

Default = 1e-11. Same as CHGTOL except applied to inductors.

#### **9.8.6 Integration Methods - METHOD option**

SIMetrix, along with most other SPICE products use three different numerical integration methods to model reactive elements such as capacitors and inductors. These are Backward Euler, Trapezoidal Rule and Gear. Backward Euler is used unconditionally at various times during the course of a simulation but at all other times the method used is controlled by the METHOD option (as long as ORDER is set to 2 or higher - see below).



The METHOD option can be set to TRAP (trapezoidal - the default) or GEAR. Gear integration can solve a common problem whereby the solution seems to oscillate slightly. An example is shown below.

The plots show the reverse recovery of a diode. The green curve was simulated with the default trapezoidal integration method whereas the red used Gear integration. Note that gear integration introduces a slight overshoot. This is a common characteristic. To find out whether such overshoots are a consequence of the integration or are in fact a real circuit characteristic, you should simulate the circuit with much smaller values of RELTOL (see above). It is also suggested that you switch back to trapezoid integration when using tight tolerances; the oscillation caused by trapezoidal integration disappear if the time step falls below half the time constant of the circuit.

Note, you should not use Gear integration if you are simulating strongly resonant circuits such as oscillators. Gear integration introduces a numerical damping effect which will cause resonant circuits to decay more rapidly than they should. For example:



The above curves are the result of simulating a simple LC circuit that is completely undamped. The top trace was the result of Gear integration and the bottom, trapezoidal. The bottom curve is correct and agrees with theory. The top curve is inaccurate. If the analysis was done with Gear integration but with a smaller value of RELTOL, the damping effect would be less, so for all methods the result is ultimately accurate if the tolerance is made small enough. But trapezoidal gives accurate results without tight values of RELTOL.

### **ORDER option**

This defaults to 2 and in general we recommend that it stays that way. Setting it to 1 will force Backward Euler to be used throughout which will degrade precision without any speed improvement. It can be increased up to a value of 6 if METHOD=GEAR but we have not found any circuits where this offers any improvement in either speed or precision.

# **9.9 Using Multiple Core Systems**

### **9.9.1 Single Step Runs**

SIMetrix will make use of multiple core processors to speed up simulations. It does this by dividing the work for calculating device equations amongst multiple threads each running on its own core. For

example, a circuit with 100 transistors will need the equations governing the transistors to be calculated for each iteration. With a 4 core system, each core can be assigned the equations for 25 transistors to be calculated in parallel which will allow the iteration to complete in less time.

However, only the device equation calculation is subject to multiple core execution. There are many other tasks that are performed during a simulation run that remain *single-threaded*, that is executed in sequence on a single core. For this reason multiple cores will not give a speed up proportional to the number of cores.

### **9.9.2 Using Multiple Cores for Single Step Runs**

SIMetrix will automatically choose how many cores to use for the simulation. For simple circuits it will use a single core and beyond a certain level of complexity it will use all the cores available on a single chip. So if you have a 4-core machine where all 4 cores are implemented on a single processor chip, SIMetrix will use all 4 cores as long as the circuit complexity is sufficient to justify it.

If you have a machine with, for example, 8 cores implemented using 2 4-core processor ICs, SIMetrix will use just one of the ICs so therefore 4 cores.

You can override the number of cores using the mpnumthreads .OPTIONS setting. E.g.:

```
.OPTIONS MPNUMTHREADS=2
```
will force 2 cores to be used as long as the computer system does actually have 2 cores. SIMetrix will not use more threads than there are physical cores available.

Be aware that hyperthreaded logical processors are not counted as a physical processor. So if you have 4 physical cores and 8 logical cores implemented using hyperthreading, SIMetrix will use a maximum of 4 cores.

### **9.9.3 Multi-core Multi-step Simulation**

Multiple core execution does give a very substantial speed improvement when applied to multi-step analyses. This is covered in *User's Manual/Analysis Modes/Multi-step Analyses/Using Multiple Cores for Multi-step Analyses*.

# **9.10 Matrix Solver**

To simulate a circuit, SIMetrix formulates a set of linear equations from the non-linear equations that govern the devices in the circuit. This is part of an iterative algorithm that is repeated successively to converge on the solution to the non-linear system. The linear system of equations is solved using a matrix solver.

SIMetrix has two matrix solvers and you can choose between them. The two solvers are:

- 1. Sparse 1.3 developed by Kenneth Kundert and which is the solver supplied with SPICE 3
- 2. KLU developed by a research group at the University of Florida under Prof. Tim Davis. This was developed for circuit simulation and was moulded to perform well for the type of matrix that circuit simulators tend to generate. The solver makes use of more modern techniques than the original SPICE3 solver which was developed in the 1980s.

SIMetrix uses KLU by default and for most applications this is the better choice. For circuits with more than about 500 nodes it is almost always faster for the following reasons:

1. It has uses superior ordering algorithms. The matrix that arises from circuit simulation problems is sparse which means that nearly all terms are zero. Exploiting sparsity to greatest effect depends on the row and column ordering. KLU makes use of modern research to produce superior ordering to Sparse 1.3

- 2. The factorisation algorithm is superior
- 3. It can be reordered efficiently and rapidly. The optimum matrix ordering that is ideal for DC and long time steps is often different to that needed for small time steps. Sparse 1.3 can not be reordered very efficiently and tends to use the same ordering throughout the simulation. KLU can be reordered much more frequently providing optimal ordering at all times

Although KLU is usually the best choice, Sparse 1.3 can give better results for small circuits. To change the matrix solver use this option:

**.options** spsolver=solver

Where solver is:

KSPARSE for Sparse 1.3

or

KLU for KLU

Currently .SENS analyses always use Sparse 1.3 regardless of the spsolver setting.

# **Chapter 10**

# **Digital Simulation**

# **10.1 Overview**

As well as an analog simulator, SIMetrix incorporates an event driven digital simulator tightly coupled to the analog portion. This system can rapidly and accurately simulate mixed signal circuits containing both analog and digital components. Of course, an analog only simulator can simulate a mixed signal circuit using digital models constructed from analog components, but this approach is slow. The advantage of this mixed-mode approach is that it is dramatically faster, typically in the order of 100 times for pure digital circuits.

The SIMetrix mixed mode simulator is based on the XSPICE system developed by the Georgia Technical Research Institute. Although based on XSPICE, SIMetrix features many enhancements over the original system. See [Enhancements over XSPICE](#page-359-0) for details of these improvements.

If you only use digital models supplied in the device library, then you don't need to know much about the digital simulator in order to use it. Just select the devices you need from the parts browser and simulate in the normal way. This chapter describes some of the inner workings of the simulator including how it interfaces to the analog system. More importantly, perhaps, this chapter also describes how you can design your own digital models.

# <span id="page-337-0"></span>**10.2 Logic States**

The digital simulator is described as '12-state' which means that a digital signal can be in 1 of 12 states. These 12 states are combined from 3 levels and 4 strengths as follows:



Logic levels HIGH and LOW are self-explanatory. UNKNOWN means the signal could be either HIGH or LOW but which is not known at this stage. The start up state of a flip-flop is an example of an UNKNOWN state. Strength refers to the driving force behind the signal. STRONG is the highest with HI-IMPEDANCE the lowest. It is used to resolve conflicts when two outputs are connected together. For example consider a LOW-RESISTIVE signal (as possessed by a pull-down resistor) connected to a

HIGH-STRONG signal There is a conflict between the two logic levels but as they are different strengths, the stronger wins and therefore the resulting level is HIGH.

UNDETERMINED strength means that the strength of the signal is unknown.

#### **10.2.1 State resolution table**

The following table defines how a state is decided when two outputs are connected:



- 0S = LOW-STRONG
- 1S = HIGH-STRONG
- XS = UNKNOWN-STRONG
- 0R = LOW-RESISTIVE
- 1R = HIGH-RESISTIVE
- XR = UNKNOWN-RESISTIVE
- $0Z = LOW-HI-Z$
- $1Z = HIGH-HI-Z$
- XZ = UNKNOWN-HI-Z
- 0U = LOW-UNDETERMINED
- 1U = HIGH-UNDETERMINED

XU=UNKNOWN-UNDETERMINED

# <span id="page-338-0"></span>**10.3 Analog to Digital Interfaces**

At the simulator level, there are two types of node namely analog and digital and they cannot be connected together. At the netlist level it *is* possible to connect analog components to digital outputs and inputs. When SIMetrix sees an analog component connected to a digital signal, it automatically interconnects them using an *interface bridge*. It will use an analog-digital bridge to connect an analog signal to a digital input and a digital-analog bridge to connect to a digital output. If you connect an analog component to a



signal which connects to both digital inputs and outputs both types of bridge will be used and the digital inputs and outputs will be separated from each other as illustrated in the following diagrams.

Circuit that is actually simulated

One problem with the above approach is that the A-D and D-A bridges introduce an additional delay to the signal path which would therefore alter the performance of the digital system even if the analog node does not present any significant load. This is overcome by assigning a negative load to the input of the digital

bridge which in effect reduces the delay of the driving gate. In the above example U2 has a negative input load which reduces the delay of U3.

# **10.3.1 How A-D Bridges are Selected**

When SIMetrix implicitly places an AD bridge in a circuit, it must choose an appropriate model for the bridge. All AD bridges are based on DAC\_BRDIGE and ADC\_BRIDGE models described in [Analog-Digital Interface Bridge,](#page-200-0) and [Digital-Analog Interface Bridge.](#page-207-0) The model is chosen according to the FAMILY parameter assigned to the digital device to which the bridge is connected. The FAMILY parameter along with the associated OUT\_FAMILY and IN\_FAMILY parameters are explained more fully in [Logic families.](#page-340-0) Basically the FAMILY parameter specifies the logic family to which the device belongs e.g. 'HC' for high speed CMOS.

The name of the model used to interconnect digital to analog is always of the form:

family\_name\_dac

and to interconnect analog to digital

family\_name\_adc

For example if the family name is HC the D-A bridge is called HC\_DAC. There is a selection of A-D and D-A bridges in the model library supplied with SIMetrix. (In BRIDGES.LB).

# <span id="page-340-0"></span>**10.4 Logic Families**

The digital simulator only knows about the 12 logic states described in [Logic States.](#page-337-0) It doesn't know anything about threshold voltages or output impedances and consequently cannot directly handle the effects of interconnecting devices from different logic families. It does however feature a mechanism of determining the level of compatibility between families and will raise an error if incompatible devices are interconnected. For example, ECL and high speed CMOS operate at completely different thresholds and cannot be connected except via a special interface gate. SIMetrix knows this so that if you attempt to connect such devices, an error message will be displayed and the simulation will not run. Conversely, it is perfectly OK to drive an LSTTL input from an HC output and SIMetrix will operate normally if you do so. If you drive an HC input from an LSTTL output SIMetrix will issue a warning as, although this may work in practice, it cannot be guaranteed to do so under all circumstances.

Another problem arises when connecting inputs from different logic families together. SIMetrix deals with this by treating groups of inputs as if they were all from the same logic family provided they are compatible. This selected logic family is then used to resolve any output-input conflict as described above. It is also used to select an analog-digital interface bridge as described in [Analog to Digital Interfaces.](#page-338-0)

Groups of outputs from different families are dealt with in the same way as inputs described above.

SIMetrix knows how to resolve these situations by referring to a set of three tables called the 'Logic Compatibility Tables'. A standard set of tables is built in to the simulator but they can also be redefined. See [Logic Compatibility Tables.](#page-341-0)

# **10.4.1 Logic Family Model Parameters.**

There are three model parameters used to specify the logic family to which a device belongs. These are:





The parameters are text strings. Any name may be used that is defined in the logic compatibility tables but you must *not* use the underscore character in a family name. The families supported by the internal tables are listed in [Supported Logic Families.](#page-343-0)

The underscore character is used to define a sub-family that has the same characteristics as the main family as far as logic compatibility is concerned but which will call a different interface bridge when connected to an analog node. This is used to define schmitt trigger devices such as the 74HC14. In an all-digital circuit this behaves exactly like a normal inverter with a slightly longer delay. When the input is connected to an analog system an interface bridge with the appropriate hysteresis is called up instead of the normal interface.

# <span id="page-341-0"></span>**10.4.2 Logic Compatibility Tables**

As explained in the above section, there are three of these. Each table has a row and column entry for each of the logic families supported. These are:

- Resolve In-Out table. Decides what to do when an output is connected to an input from a different family. Possible responses are OK, ERR (error - not permissible) and WARN (OK but give warning to user)
- Resolve In-In table. Decides how to treat the situation when two inputs from dissimilar families are connected. As described above SIMetrix must treat a group of inputs connected together as all belonging to the same logic family for the purpose of deciding an analog interface bridge (see [Analog to Digital Interfaces\)](#page-338-0) and to resolve in-out family conflicts. Possible responses are ROW, COLUMN and ERR. ROW means that the family defining the ROW entry has priority and COLUMN means that the family defining the COLUMN entry has priority. ERR means that it is an error to interconnect these two inputs. You can also enter OK which signifies that the two families are equivalent and it doesn't matter which is chosen. Currently this response is exactly equivalent to ROW.
- Resolve Out-Out table. Works the same way as the Resolve In-In table but used to define output priorities.

The tables can be redefined by specifying a file containing the new definition. If running in GUI mode a new file can be specified at any time using the ReadLogicCompatibility command (*Script Reference Manual/Function Reference/ReadLogicCompatibility*). It can also be specified as the configuration setting CompatTable. The format of this file is described in the following section.

# **10.4.3 Logic Compatibility File Format**

For an example of a compatibility table, see the file COMPAT.TXT which you will find in the SCRIPT directory. This file is actually identical to the built-in definitions except for the UNIV family which cannot be redefined.

The file format consists of the following sections:

- 1. Header
- 2. In-Out resolution table
- 3. In-In resolution table

4. Out-Out resolution table

#### **Header**

The names of all the logic families listed in one line. The names must not use the underscore ('\_') character.

# **In-Out resolution table:**

A table with the number of rows and columns equal to the number of logic families listed in the header. The columns represent outputs and the rows inputs. The entry in the table specifies the compatibility between the output and the input when connected to each other. The entry may be one of three values:



# **In-In resolution table**

A table with the number of rows and columns equal to the number of logic families listed in the header. Both column and rows represent inputs. The table defines how inputs from different families are treated when they are connected. The entry may be one of four values:



### **Out-out resolution table**

A table with the number of rows and columns equal to the number of logic families listed in the header. Both column and rows represent outputs. The table defines how outputs from different families are treated when they are connected. The entry may be one of four values:



### <span id="page-343-0"></span>**10.4.4 Supported Logic Families**

Family name Description TTL - 74 series HC High speed CMOS - 74HC series HCT TTL compatible High speed CMOS - 74HCT series FAST FAST TTL - 74F series LS Low power schottky TTL - 74LS series ALS Advanced low power schottky TTL - 74ALS series 4000-5 4000 series CMOS - 5V operation 4000-10 4000 series CMOS - 10V operation 4000-15 4000 series CMOS - 15V operation ECL10K ECL 10K series ECL10KE ECL Eclipse series AC Advanced CMOS - 74AC series ACT TTL compatible Advanced CMOS - 74ACT series FORCE5 Used for 5V VCC rails. UNIV Universal family - see below

The following logic families are supported by the internal Logic Compatibility Tables.

### **10.4.5 Universal Logic Family**

The internal tables support the concept of a 'Universal logic family'. This is called UNIV and can connect to any logic family without error. This is the default if no FAMILY parameter is supplied.

# **10.4.6 Internal Tables**

The internal tables are documented in the on-line help system. Refer to topic "Internal Tables" which is listed as a keyword in the index tab.

# **10.5 Load Delay**

#### **10.5.1 Overview**

The digital simulator includes mechanisms to model the delay introduced when an output is loaded. Two sources of delay are provided for, namely 'input delay' and 'wire delay'. Input delay is determined by the capacitive input while wire delay is an additional delay caused by the capacitance of the interconnection.

Both input delay and wire delay are affected by the driving outputs 'resistance'.

#### **10.5.2 Output Resistance**

Most devices that have digital outputs have three parameters to define output resistance. Note that the resistance we are referring to here is not an actual analog resistance but a conceptual value that when multiplied by load capacitance provides a delay value.

The three output resistance parameters are: out\_res, out\_res\_pos, out\_res\_neg. out\_res\_pos and out\_res\_neg define the output resistance for positive and negative transitions respectively. out\_res provides a default value for out res pos and out res neg.

### **10.5.3 Input Delay**

Most digital inputs include an 'input\_load' capacitance parameter. The total input delay is obtained by multiplying the sum of all connected input capacitances by the driving output's output resistance as described above.

#### **10.5.4 Wire Delay**

Wire delay is derived from the number of connected inputs following a non-linear relationship defined in a look-up table.

#### **Defining Look-up Table**

The wire delay look-up table must be defined in a file containing pairs of values with one pair per line. The first value in the pair is the number of connections and the second is the capacitance. For example:

```
0 0
1 0
2 1e-12
5 10e-12
10 30e-12
```
Linear interpolation is used to derive missing values.

To specify the wire table used for a simulation, add the line:

```
.OPTIONS WireTable=filename
```
where *filename* is the path of the wire table file.

# **10.6 Digital Model Libraries**

#### **10.6.1 Using Third Party Libraries**

The SIMetrix digital simulator is based on XSPICE and all the XSPICE digital devices have been implemented. Virtually all of these have been enhanced in a number of ways but all remain backward compatible with the original XSPICE. Consequently any 100% XSPICE compatible digital model will work with SIMetrix.

# **10.7 Arbitrary Logic Block - User Defined Models**

#### **10.7.1 Overview**

The arbitrary logic block is an internal component that can be defined to perform any logic function. Using a simple descriptive language it is possible to define combinational logic elements, synchronous and asynchronous registers as well as look-up table (ROMs) and arrays (RAMs).

Each ALB device is defined as a normal .MODEL statement which refers to a separate file containing the logic description. This section is mostly concerned with the descriptive language used in the definition file.

#### **10.7.2 An Example**

We start with a simple example. The following is a description of a simple 8 bit synchronous counter. (This definition would be put into a file referred to in a .MODEL statement. This is described later). A circuit using this model is supplied as an example. See EXAMPLES/ALB\_Examples/count.sch

```
PORT (DELAY = 10n) CountOut out [0:7] ;
EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;
Count = Count + 1;
CountOut = count;
```
We will go through this line by line.

The first line:

PORT (DELAY = 10n) CountOut out  $[0:7]$ ;

is a PORT statement and in this case defines the characteristics of an output.

 $(DELAY = 10n)$ 

says that the output delay is 10nS that is the actual output pins will change state 10nS after the output is assigned.

CountOut

names the output CountOut.

out[0:7]

defines the port as an output and specifies the actual pins used on the device. This specifies the first 8 pins on the output port. There are two sets of pins on an ALB one assigned for inputs and referred to as "in[a:b]" and the other assigned for outputs and referred to as "out[a:b]". The line ends in a semi-colon which terminates the statement. All statements must end in a semi-colon.

The next line:

EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;

defines an edge triggered register.

CLOCK=in[0]

specifies the pin used for the clock (it must always be an input pin). This is always positive edge triggered.

DELAY=5n

This is the clock to output delay. (See illustration below)

WIDTH=8

This specifies the width of the register i.e. 8 bits

The next line:

Count =  $Count + 1$ ;

defines the operation to be performed at each clock edge. In this case the value in the register is simply incremented by one. When it reaches 255 it will reset to 0.

The final line

CountOut =  $count$ ;

defines what appears at the output. This says that the output equals the count register.

The following diagram illustrates the internal structure of the counter.



#### **Reset Count at 200**

We will now make a small modification to the counter so that the counter only counts up to 199 before resetting back to zero. Change the line:

```
Count = Count + 1;
```
to:

```
Count = Count == 199 ? 0 : Count + 1;
```
This says 'If the count equals 199 set to zero otherwise increment by one'. As before, this will happen on each clock edge.

### **Add an Asynchronous Reset**

The logic definition language supports the addition of asynchronous controls to synchronous registers. Here we will add an asynchronous reset. The complete definition becomes:

```
PORT (DELAY = 10n) CountOut out [0:7];
PORT Reset in[1] ;
EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;
Count := !Reset ? 0 ;
Count = Count == 199 ? 0 : Count + 1;CountOut = count ;
```
To add the reset signal we have to add two lines to the definition. The first:

PORT Reset in[1];

defines the signal pin to be used for the reset and the second:

Count  $:=$  !Reset ? 0 ;

defines the action to be taken. This is an asynchronous action statement. The '!' means NOT so the line says 'If Reset is NOT TRUE (i.e. low) set the count to zero otherwise do nothing'. Asynchronous action statements are always of the form:

```
register_name := condition ? action ;
```
The ':' signifies that the statement is asynchronous and that the action should happen immediately.

### **10.7.3 Example 2 - A Simple Multiplier**

```
PORT (DELAY=10n) MultOut out [0:7] ;
PORT in1 in[0:3] ;
PORT in2 in[4:7];
MultOut = in1*in2;
```
The above defines a simple combinational circuit, that of a 4X4 digital multiplier. The inputs in1 and in2 are treated as 4 bit unsigned values so if both are zero the output will be zero and if both are 1111 (i.e. 15) the result will be 11100001 (i.e. 225). See the circuit EXAMPLES/ALB\_Examples/Mult.sch.

#### **10.7.4 Example 3 - A ROM Lookup Table**

The following definition is that of a lookup table to define a sine wave:

```
PORT (DELAY=10n) ROMout out[0:7] ;
PORT input in[0:7] ;
READONLY (WIDTH=8) ROM[256] =
128, 131, 134, 137, 140, 143, 146, 149, 152, 156, 159, 162,
165, 168, 171, 174, 176, 179, 182, 185, 188, 191, 193, 196,
199, 201, 204, 206, 209, 211, 213, 216, 218, 220, 222, 224,
226, 228, 230, 232, 234, 236, 237, 239, 240, 242, 243, 245,
246, 247, 248, 249, 250, 251, 252, 252, 253, 254, 254, 255,
255, 255, 255, 255, 255, 255, 255, 255, 255, 255, 254, 254,
253, 252, 252, 251, 250, 249, 248, 247, 246, 245, 243, 242,
240, 239, 237, 236, 234, 232, 230, 228, 226, 224, 222, 220,
218, 216, 213, 211, 209, 206, 204, 201, 199, 196, 193, 191,
188, 185, 182, 179, 176, 174, 171, 168, 165, 162, 159, 156,
152, 149, 146, 143, 140, 137, 134, 131, 128, 124, 121, 118,
115, 112, 109, 106, 103, 99, 96, 93, 90, 87, 84, 81, 79, 76,
73, 70, 67, 64, 62, 59, 56, 54, 51, 49, 46, 44, 42, 39, 37,
35, 33, 31, 29, 27, 25, 23, 21, 19, 18, 16, 15, 13, 12, 10,
9, 8, 7, 6, 5, 4, 3, 3, 2, 1, 1, 0, 0, 0, 0, 0, 0, 0, 0, 0,
0, 0, 1, 1, 2, 3, 3, 4, 5, 6, 7, 8, 9, 10, 12, 13, 15, 16,
18, 19, 21, 23, 25, 27, 29, 31, 33, 35, 37, 39, 42, 44, 46,
49, 51, 54, 56, 59, 62, 64, 67, 70, 73, 76, 79, 81, 84, 87,
90, 93, 96, 99, 103, 106, 109, 112, 115, 118, 121, 124 ;
```

```
ROMout = ROM[input] ;
```
See the example circuit EXAMPLES/ALB\_Examples/SineLookUp.sch

#### **10.7.5 Example 4 - D Type Flip Flop**

The following is the definition for the 74X74 Dtype flip flop supplied with the standard SIMetrix model library. This model is somewhat more complicated as it models a number of timing artefacts such as setup time and minimum clock width. Each line below has been annotated to describe its function. Full details are explained in the following sections.

```
// Input port definitions
PORT D in[0] ; // D input
PORT CK in[1] ; // Clock
PORT SR in[2:3] ; // Set/reset inputs. r bit 3 s bit 2
PORT out out [0:1] ; // Outputs Q and !Q
// Edge triggered register.
// HOLD is hold time i.e. time after clock edge that data
// must remain stable. Setup time is implemented by
// delaying the D input
// MINCLOCK is minimum clock width.
// USER[n] references values supplied in the .MODEL statement
// The final '=2' initialise the register with the value 2
// i.e. Q=0 and Q!=1EDGE (WIDTH=2, DELAY=USER[4], HOLD=USER[2], MINCLOCK=USER[3],
CLOCK=in[1]) DTYPE=2;
// COMB defines a combinational register. This is effectively
// a delay element. These delay the D input (to implement
// setup time) and the set/reset inputs to implement minimum
// set and reset times
COMB (DELAY=USER[0], WIDTH=1) D_DEL ;
COMB (DELAY=USER[1], WIDTH=2) SR_DEL ;
// These assign the combinational registers
SR DEL = SR ;
D_DEL = D;
// asynchronous action
DTYPE := SR_DEL==1||SR_DEL==2 ? (SR_DEL==2 ? 1 : 2) ;
// synchronous action
DTYPE = DDEL ? 1 : 2 ;
// Both outputs are forced high if S and R are both active
// Output will be restored to previous value when one of
// S and R becomes inactive
out = SR_DEL==0 ? 3 : DTYPE ;
```
### **10.7.6 Device Definition - Netlist Entry and .MODEL Parameters**

#### **Netlist entry**

Axxxx [ in\_0 in\_1 .. in\_n ] [ out\_0 out\_1 .. out\_n ] model\_name + : parameters

#### **Connection details**





# **Instance parameters**



# **Model format**

**.MODEL** model\_name d\_logic\_block parameters

# **Model parameters**





#### **Notes**

Usually the logic block definition would be placed in a file referred in the FILE parameter. Alternatively the definition may be placed directly in the .MODEL statement as the value of the DEF parameter. In this case the definition must be enclosed in quotation marks (").

The USER\_SCALE parameter scales all values found in the USER parameter.

### **10.7.7 Language Definition - Overview**

The following sections describe the full details of the arbitrary logic block language.

All logic definitions are divided into two sections. The first contains the ports and register definitions and the second section consists of the assignment statements. (The first section can be empty in very simple cases).

#### **10.7.8 Language Definition - Constants and Names**

Constants follow the usual rules. Any decimal number with optional sign and exponent or engineering suffix is permitted. In addition, numbers in hexadecimal are also allowed. The format is the same as for the 'C' programming language i.e. prefixed with '0X'. E.g.:

 $0x10 = 10$  hex = 16.

Identifiers used for register, port and variable names must begin with an alphabetic character or underscore and consist of alphanumeric characters and underscores.

#### **10.7.9 Language Definition - Ports**

Port statements define the inputs and outputs to the logic device. They are of the form

```
PORT ( DELAY=output_delay) port_name OUT [ pin1| pin1:pin2 ]
```
OR

```
PORT port_name IN|OUT [ pin1| pin1:pin2 ]
```
Ports define a label to a single pin or sequence of pins so that they can be treated as a single entity in the remainder of the logic definition. In the case of outputs they can optionally also define an output delay. (If this is not specified a default output delay defined in the devices .MODEL statement is used).



#### <span id="page-351-0"></span>**Relationship between ports, netlist entry and symbol definition**

The netlist entry for an arbitrary logic block is of the form:

Axxx [ input\_node\_list ] [ output\_node\_list ] model\_name

The pin numbers in the port statements above, i.e. *pin1* and *pin2* are the positions within the *input\_node\_list* for input ports and *output\_node\_list* for output ports.

So if the netlist entry is:

A12 [ 1 2 3 4 ] [ A B C D ] ARB1

the port definition:

PORT output OUT[0:3] ;

assigns the label output to the netlist pins A B C and D. If, for example, the value 7 is evaluated and assigned to  $\text{output}$ , pins A B and C would be set to a logic '1' and pin D would be set to a logic '0'. Pins 1 2 3 & 4 would be used for input ports in a similar way.

The netlist entry relates directly to a symbol definition for an arbitrary logic block. When defining a symbol to be used with an ALB you should observe the following rules

- The first input pin's name and the first output pin's name should both be prefixed with a '['.
- The last input pin's name and the last output pin's name should both be suffixed with a ']'.
- Use **Property/Pin | Edit Pin Order...** to define the pin order with input pins first then output pins.
- You should assign a MODEL property with the value 'A'.

#### **10.7.10 Language Definition - Registers and Variables**

Registers are the main working elements of the arbitrary logic block. There are four main types. These are:

- Edge triggered. The value of these change on the rising edge of an assigned clock.
- Level triggered. The value of these change when an assigned enable is at a logic '1' level.
- Combinational. The value of these change after a specified delay.
- Read-only. These are given a fixed value which cannot be changed. These would usually be arranged in indexable arrays to implement a read only memory.

Edge and level triggered registers may be arranged in indexable arrays. Level or edge triggered arrays form a read-write memory or RAM.

In addition to registers there are also local variables. These can be assigned a value that can later be used in a register assignment.

All registers must be declared. Local variables are declared by simply assigning a value to them.

The syntax for register declarations follow:

### **Edge Triggered Register Declaration**

EDGE ( CLOCK=input\_pin\_spec

```
[, DELAY=reg_delay]
[, WIDTH=reg_width]
[, MINCLOCK=reg_minclock]
[, HOLD=reg_hold_time]
[, ASYNCDELAY=reg_asyncdelay]
[, BITWISE=0|1 ] ) name [[array_size]]
[ = initial_condition \star [, initial_condition] ] ;
```


*initial\_condition* Value assigned to register when simulation starts.

Default: 0

Notes: To implement register setup time, assign a value to *reg\_hold\_time* equal to the sum of the register setup and hold times then delay the input data by a period equal to the setup time.

### **Level Triggered Register Declaration**

```
LEVEL (CLOCK=input_pin_spec
[, DELAY=reg_delay]
[, WIDTH=reg_width]
[, SETUP=reg_setup_time]
[, ASYNCDELAY=reg_asyncdelay]
[, BITWISE=0|1 ] name [[array_size]]
[ = initial_condition \star [, initial_condition]] ;
```


# **Combinational Register Declaration**

```
COMB ( [, DELAY=reg_delay]
[, WIDTH=reg_width]
```
 $[$ , BITWISE=0|1 ] ) name  $[$  = initial\_condition  $]$ ;



#### **Read-only Register Declaration**

```
READONLY ([, WIDTH=reg_width] name[[array_size]]
[ = initial_condition \star [, initial_condition]] ;
```


Read-only registers are usually arranged as an addressable array. When reading a read-only register, the value returned is the value defined by the initial conditions. As the name implies it is not possible to assign read-only registers.

# **10.7.11 Language Definition - Assignments**

Registers and output ports can be assigned using the assignment operator '='. Assignment values can be constants, input ports, other registers, local variables or expressions of any or all of these. Assignments are of the form:

```
register | output_port | OUT[pin1:pin2] | OUT[pin1] | local_var = expr ;
```
OR

clocked\_register[index] = expr ;





# <span id="page-355-0"></span>**Expression operators**

The following table lists all operators available. These are listed in order of precedence. Precedence determines the order of evaluation. For example in the expression:

var1<var2 && var3<var4

The sub-expressions var1<var2 and var3<var4 are evaluated first and the result of that those evaluations combined using && to yield the final result. This is because < has higher precedence than &&. The precedence can be altered using parentheses in the usual way.





Note that the operators and their precedence are a subset of those used in the 'C' programming language with the exception of  $\leq$ .

# **Controlling Output Enables**

An output can be set into a high impedance state using a modification to an output port variable. Use the suffix .EN after the output port or port identifier to signify that the result of the expression should control the output enable. E.g. the following is extracted from the 74XX244 definition:

```
PORT (DELAY=USER[0]) Output out[0:3] ;
Output.En = Out_En_Del ? 0 : 0xf ;
```
#### **Examples**

 $Y = ! \text{Enable ? A Del} != B Del : 1 ;$ 

If Enable is 0 then Y will be the result of A\_Del != B\_Del otherwise the result will be 1.

Shift = !Par\_En\_Del ? Par\_Data\_Del :(Shift<<1) | Ser\_Data\_Del;

This describes the action of a parallel loadable shift register.

out[0]= !in[1]&!in[2] | in[1]&!in[2]&in[0] | !in[1]&in[2]&in[0]

An example of referencing inputs and outputs directly without needing PORT statements.

#### **10.7.12 Language Definition - User and Device Values**

Sometimes it is convenient to use the logic description to define the functionality of a block but have the timing and other specifications specified separately. This is achieved by USER and DEVICE values. USER values are specified in the .MODEL statement while DEVICE values are specified on the device at the netlist (or schematic device) level. The values are referenced in the logic definition in the form:

USER[index]

and

DEVICE[index]

These can replace any constant value in an expression, register qualifier or port qualifier. (Register and port qualifiers are the values in parentheses after the register/port keyword. E.g. DELAY, HOLD, SETUP etc.).

To set USER values in a .MODEL statement, assign the parameter USER. This is a *vector* parameter, that is it can have any number of values and these must be enclosed in square brackets '[' and ']'. For example:

```
.MODEL Counter8 d_logic_block file=counter_8.ldf
+ user=[10n, 5n]
```
The logic definition to which this model refers - counter\_8.ldf - can use USER[0] and USER[1] to refer to the values 10n and 5n respectively.

To set DEVICE values in a netlist, the netlist entry for the device must be appended with:

: USER=[ values ]

For example:

```
A$U3 [clock] [Q0 Q1 Q2 Q3 Q4 Q5 Q6 Q7] Counter8 :
+ USER=[10n, 5n]
```
The logic definition for this device can use DEVICE[0] and DEVICE[1] to access the USER values in the netlist i.e. 10n and 5n respectively. Always remember to include the colon. This acts as a separator between the device name and any parameters.

#### **10.7.13 Diagnostics: Trace File**

In order to debug models, a tracing facility is provided. If the .MODEL TRACE\_FILE parameter or instance parameter of the same name is specified, a file will be created which lists the values of all internal registers at each time point.

The file will usually have a number of lines of the form: Roll back to  $\langle$ time>

For example the following is an extract from an actual trace file

```
5.00022e-05 2696 9 2696 0
5.09397e-05 2696 9 2696 0
5.09407e-05 2692 10 2692 0
Roll back to 5.08599e-05
5.09397e-05 2696 9 2696 0
5.09407e-05 2692 10 2692 0
5.09657e-05 2692 10 2692 0
```
Roll-back occurs when an analog time step is rejected but the digital simulation has already advanced past the new analog time. In this case the digital simulator has to back-track events. This mechanism is central to the operation of the mixed-mode system and is explained in more detail in [Mixed-mode Simulator -](#page-357-0) [How it Works.](#page-357-0)

# <span id="page-357-0"></span>**10.8 Mixed-mode Simulator - How it Works**

#### **10.8.1 Event Driven Digital Simulator**

The digital simulator is said to be *Event Driven*. An event is essentially a change of state e.g. a gate output changing from logic '0' to logic '1'. When an event occurs on an output, all devices with inputs connected to that output are notified of the event and can respond appropriately by generating new events.

For example, consider the following circuit fragment.



U1 receives an event, a rising edge at its input at time  $= T. U1$  has a propagation delay of 5.5nS, so on receipt of the event at its input, U1 posts an event at its output with a time T+5.5nS. At that time this event is received by U2 and U3. U3 does not respond to this event because one of its inputs is permanently at logic '1' so its output will always be low. U2, however, does respond and creates a low-high event at a time delayed by its propagation delay of 6.5nS i.e. T+5.5nS+6.5nS. Any device with an input connected to the output of U2 will process this new event and so the process continues.

In addition to the propagation delays described above, there are also additional delays caused by loading effects. Each input has an effective input capacitance and each output a resistance. For each event, an additional delay is added equal to the sum of all capacitances on the node multiplied by the driving output's resistance.

### **10.8.2 Interfacing to the Analog Simulator**

Connections between the analog and digital system are made via special interfaces bridges. (As described in [Analog to Digital Interfaces](#page-338-0) these bridges are implicitly included by the simulator and it isn't necessary for the user to wire them in.) The digital to analog interface has an output that looks like - to a first approximation - an analog representation of a digital gate. This output changes voltage at a specified rise and fall time when the digital input changes state. More importantly, the analog system is notified when an event occurs at the input to a D-A interface bridge and a timestep is forced at that time. This is known as a *breakpoint* and is the analog equivalent of an event. The analog system is only notified of events that occur at the input of D-A bridges. It knows nothing of events that are internal to the digital system.

Analog to digital interface bridges are much like a comparator. When the analog input passes a threshold, the output state changes appropriately and a digital event is generated.

#### **Time Step Control**

With two simulators running largely independently, something is needed to synchronise the timesteps. Basically the analog system is in control. It tells the digital system to process events up to a certain time, that time being the analog system's next anticipated time point. A problem arises, however in that the next analog timestep is not guaranteed to be accepted. The analog system frequently rejects timesteps either

because of slow convergence or because a shorter timestep is needed to maintain the required accuracy. If the analog system has to cut back the timestep to a point prior to the most recent digital event, then the digital system has to back-track. This process is known as roll-back and the need for the digital simulator to be able to perform it substantially increases its complexity. In order to roll-back the digital simulator has to store its past history back to the most recent accepted analog timepoint

# <span id="page-359-0"></span>**10.9 Enhancements over XSPICE**

- Gate delays in XSPICE are *stored* i.e. like a transmission line not like a real gate. SIMetrix gate delays are *inertial* so if a pulse shorter than the propagation delay is received, it is swallowed not transmitted.
- Automatic interface creation. In XSPICE you have to explicitly join digital and analog nodes via interface bridges. In SIMetrix this is done automatically.
- Fan out implemented. The underlying mechanism for load dependent delay was there but none of the models supported it. Static loading effects (as in bipolar logic) was not supported at all. In SIMetrix it is.
- Input load reflected in analog to digital interfaces. The AD interfaces in XSPICE have infinite input impedance regardless of what the digital output is driving. SIMetrix AD interfaces reflect the digital capacitative and static load at their inputs.
- Output strength reflected in digital to analog interfaces. The DA interfaces in XSPICE have zero output impedance regardless of what is driving them. SIMetrix DA interfaces reflect the strength of the digital output driving the input. A hi-z logic state will look like a hi-z logic state when transferred to the analog domain. This is not the case with XSPICE.
- AD interface threshold detection. All AD interfaces switch at a particular input threshold. In the XSPICE system the output switched at the first analog timepoint that exceeded the threshold. This could be a long way passed the threshold if the analog time steps are large. In SIMetrix a mechanism has been implemented that cuts back the time step so that the threshold is hit within a specified time tolerance.
- Arbitrary logic block device. This allows the definition of any logic device using a simple descriptive language. The language accommodates combinational logic, synchronous and asynchronous registers as well as look up tables (i.e. ROMS) and arrays (i.e. RAMs).
- Arbitrary analog to digital converter. Up to 32 bits with specified input range and offset, conversion time and maximum conversion rate. Output may be in two's complement or offset binary.
- Arbitrary digital to analogue converter. Up to 32 bit with specified input range and offset and output slew time. Input may be in two's complement or offset binary.
- Voltage controlled oscillator (analog in digital out). There was one of these in the original XSPICE code but it suffered a number of problems and was scrapped. The SIMetrix version is all new.
Copyright © SIMetrix Technologies Ltd. 1992-2024 SIMetrix 9.2 Simulator Reference Manual